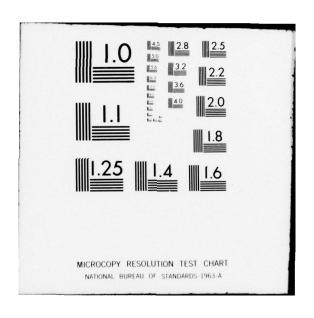
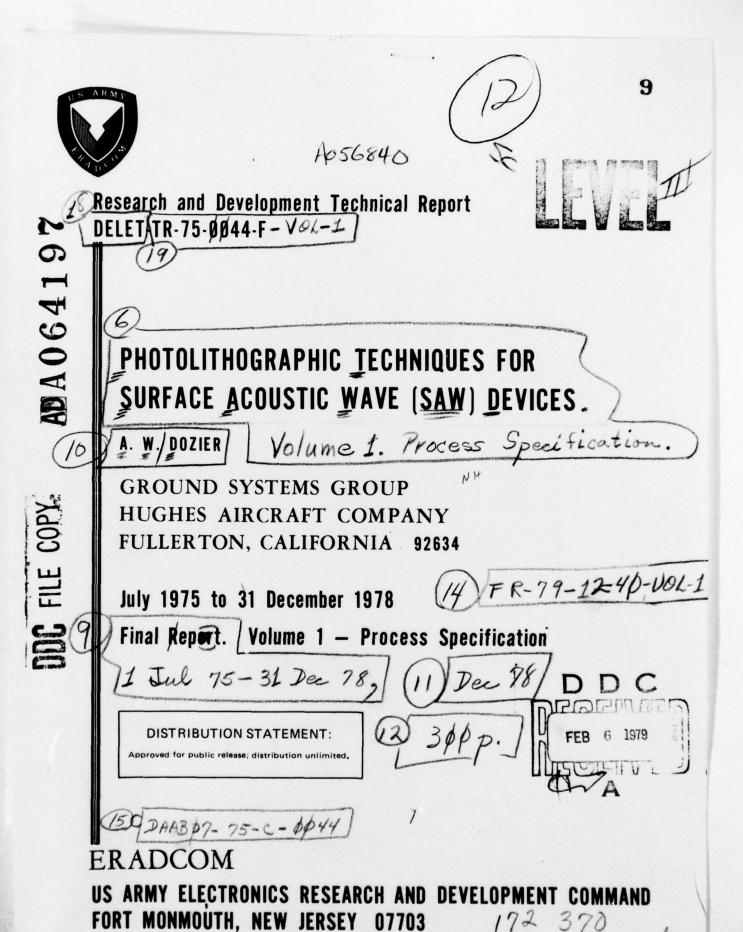
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#### NOTICES

#### Acknowledgements

This project has been accomplished as part of the US Army Manufacturing and Technology Program, which has as its objective the timely establishment of manufacturing processes, techniques or equipment to insure the efficient production of current or future defense programs.

#### Disclaimers

The findings in this report are not to be construed as an official Department of the Army position, unless so designated by other authorized documents.

The citation of trade names and names of manufacturers in this report is not to be construed as official Government endorsement or approval of commercial products or services referenced herein.

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14. SUPPLEMENTARY HOTES

19. KEY BORDS (Continue on reverse side if necessary and identify by block number)

Surface Acoustic Wave Devices Bandpass Filters Tapped Delay Line Filters Pulse Compression Filters

SAW Processing SAW Packaging

20. ABSTRACT (Continue on reverse side if necessary and identify by block number)

The object of the program was the establishment of a production capability for surface acoustic wave devices of varied design and material for the purpose of meeting estimated military needs for a period of two years after the completion of the contract, and to establish a base and plans which may be used to meet expanded requirements. The primary requirement was the pilot line production of devices that are reliable, reproducible, and low cost.~

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The first phase of this program required the design, fabrication and testing of a total of 60 prototype bandpass, tapped delay line and pulse compression SAW filters on both lithium niobate and ST-quartz. The First Engineering Phase (Phase I) electrical testing demonstrated that the device designs generally met the specifications imposed by the program. Deviations from specification, which required additional test to optimize the levels of padding and/or shunt resistance and capacitance, were resolved during the Second Engineering Phase (Phase II) for the PC-Q, PC-LN and TDL-200. Deviations from the insertion loss specification occurred with the BP-LN and TDL-100 designs. In the former case, a redesign excluding the program-specified multi-strip coupler, was theoretically evaluated. In the latter case, as pointed out in the Hughes proposal, a theoretical analysis precluded the possibility of a specification accommodation. It was necessary to revise the specification for both designs since the customer insisted on utilization of the multistrip coupler in the BP-LN.

Testing of modified semiconductor pin packages during Phase II demonstrated these to be suitable, cost-effective replacements for the machined chassis employed for Phase I. A quartz orientation problem was highlighted in Phase I and negotiated during Phase II. The quartz vendor implemented an effective screening procedure for the off-orientation problem. However, problems with this vendor continued in the form of substrate surface defects. Other major yield problems encountered during these portions of the program resulted from the dicing and mask making operations. The Phase I and Phase II efforts resulted in a finalized layout, electrical specification and test procedure for the Third Engineering Phase (Phase III).

Phase III involved fabrication of a larger quantity (50 ea.) of confirmatory devices which were sampled at a high rate and subjected to rigorous life and environmental testing. Phase III was successfully completed with delivery and acceptance of the confirmatory samples. The device configuration is detailed as it existed for Phase III along with assembly details, results and conclusions from the Confirmatory Sample production run (Phase III).

The Fourth Engineering Phase (Phase IV) of the program was pilot line production effort of 150 each of the devices scheduled to be delivered. Solder sealing was identified as a problem area during Phase IV for SAW devices in Phase III packages. New solder seal screening and processing procedures were investigated. In addition, alternative sealing approaches were evaluated. These procedures, Tungsten Inert Gas (TIG) and projection and seam welding were demonstrated to be more compatible with SAW processing. They are especially suitable for high volume production.

Phase IV pilot line production was completed with the delivery of approximately 150 of each of the device types. Some devices were shipped short due to the inability to locate a second source for projection welding, and the extended lead time in reprocurement of packages capable of being sealed by alternate procedures.

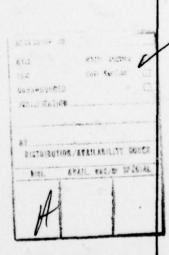
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Data from Phases I through IV are presented in the Technical and Operational volume of the Final Report. Pilot Line process flow and related documentation are presented in the Process Specification Volume of the Final Report. All inspection positions, pilot run yields, and quality control procedures for Phase IV are presented in the Quality Control Volume of the Final Report. Cost analysis and labor distribution for all facets of the program are covered in a non-distributable volume of the final report.

The Program will include preparation of a General Report, which will consist of an analysis of equipment and facilities required to produce SAW devices of the type produced in the Pilot Run at a rate of 500 per month. In addition, an Industry Demonstration was prepared which verbally and visually presented all facets of the MMT program through the Pilot Run.



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Note: The numerical sequence of the PEI section is not continuous due to the fact that processing documents not utilized on this program were not included.

#### **PURPOSE**

This report presents the results of the three year effort in satisfying the requirements of a Manufacturing Methods and Technology Program devoted to a representative range of surface acoustic wave (SAW) device designs.

The objective of this program was to establish a production capability for the purpose of meeting estimated military needs for a period of two years after the completion of the contract, and to establish a base and plans which may be used to meet expanded requirements. The manufacturing method emphasized the photolithographic fabrication of SAW devices that are reliable and reproducible at low cost.

Specific tasks included establishing and demonstrating a capability to manufacture the six SAW device designs on a pilot line basis using methods and processes suitable for a production rate of 150 devices per month for each type. In addition, engineering analysis and planning remains to be accomplished for expansion of the manufacturing capability which could accommodate the production of such devices at a rate of 500 each per month. This analysis and planning will be delivered in the General Report.

The program was divided into four phases. The first (Phase I First Engineering Sample) addressed the design, fabrication and analytical testing of six prototype SAW devices that are representative of the major current and potential application of the technology. While these device requirements did not represent the state-of-the-art in an R & D sense, they were of such complexity as to require a serious design effort in each case.

The second phase (Phase II – Second Engineering Samples) was performed to redesign those devices that failed the intended design specification. The net result of this effort was to be functional electrical specification adherence, based on a cost effective packaging commitment.

The third (Phase II – Confirmatory Samples) was to test and conform to specification for both the electrical and environmental commitment of the various devices. The final phase (Phase IV – Pilot Run) was to test the reproducibility of those predetermined electrical and environmental requirements in a high volume (500 per month) production environment. A key result of this phase was the establishment of meaningful manufacturing cost data on each device as well as a comparison of this data to the prior low volume efforts of the earlier phases. These data will then be extrapolated to a production rate of 500 per month with assumptions regarding facilities and equipment in the General Report.

#### **GLOSSARY**

SAW - Surface Acoustic Wave

BP-Q - Bandpass Filter - ST Quartz Substrate

BP-LN - Bandpass Filter - Lithium Niobate Substrate

TDL-100 - Tapped Delay Line Filter - 100 MHz - ST Quartz Substrate

TDL-200 - Tapped Delay Line - 200 MHz - ST Quartz Substrate

PC-Q - Pulse Compression Filter - ST Quartz Substrate

PE-Q - Pulse Expansion Filter - ST Quartz Substrate

PC-LN - Pulse Compression Filter - Lithium Niobate Substrate

PE-LN - Pulse Expansion Filter - Lithium Niobate Substrate

ST - Quartz orientation, ST cut (42° 45'), X propagating

YZ - Lithium Niobate orientation, Y cut Z propagating

TIG - Tungsten Inert Gas Welding

MSC - Multistrip Coupler

K<sup>2</sup> - Electromechanical Coupling Constant

fo - Center frequency

B - Bandwidth

T - Time Delay

TXB - Time Bandwidth Product

VSWR - Voltage Standing Wave Ratio

DUT - Device Under Test

LINS - Insertion Loss

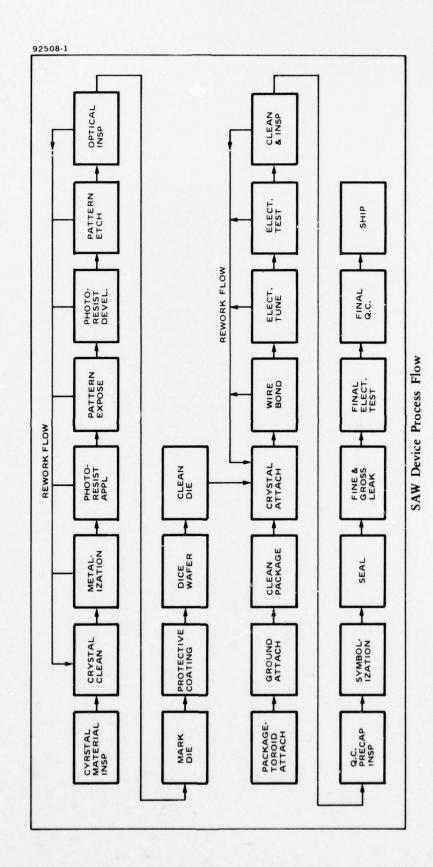
Ss. L. - Sidelobe Suppression

Sf. t. - Feedthrough Suppression

Spur - Spurious Suppression

TTS - Triple Transit Signal

PROCESS ENGINEERING INSTRUCTIONS (PEI)



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## HUGHES

HUGHES AIRCRAFT COMPANY

ENGINEERING PROCESS ENGINEERING INSTRUCTION MICROFLECTRONICS

instruction

Subject

ACOUSTIC SURFACE WAVE DEVICE PROCESS CRYSTAL INSPECTION

Pag e

Number 7.18.01

Date 19 December 1973

Revision

Approved

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#### 1.0 SCOPE

This instruction covers the inspection of a crystal to assure a surface suitable for fabrication of acceptable acoustic surface wave devices.

#### 2.0 EQUIPMENT AND MATERIAL

- 2.1 Equipment.
  - Microscope, Reichert Zetopan, with XY stage, incident oblique lighting and approximately 55X capability.
  - 2.1.2 Log or record book.
- 2.2 Material.
  - Crystal substrate, of the material required, cut and polished, and marked with individual identification.
  - 2.2.2 Finger cots.

#### 3.0 GENERAL REQUIREMENTS

- There shall be no scratches or pits with a depth greater than one-half 3.1 micron. There shall be no residual patterns, or other defects in the surface area visible at 50X magnification.
- 3.2 There shall be no chips into the crystal edges which extend to within 1 milimeter of the active part of the device.
- Any questionable imperfections will be brought to the attention of the process engineer or supervisor.

#### 4.0 PROCEDURE

Start-up. 4.1

- 4.2 Process instructions.
  - 4.2.1 Place finger cots on all fingers which may touch the crystal.

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#### ACOUSTIC SURFACE WAVE DEVICE PROCESS CRYSTAL INSPECTION

- 4.2.2 Record the crystal identification in the log book that is maintained in the Acoustic Laboratory.
- 4.2.3 Set up the optics of the microscope for approximately 55X magnification.
- 4.2.4 Carefully lift the crystal from it's carrier container and position it on the stage of the microscope with the surface to receive the processing on top.
- 4.2.5 Locate the incident light so that it illuminates the crystal surface under the microscope at a 45° angle maximum from the horizontal.
- 4.2.6 Slowly scan the crystal surface taking care to maintain good focus.
- 4.2.7 Note all imperfections in the log. Items to be noted are the following:
  - 4.2.7.1 Scratches.
  - 4.2.7.2 Pits.
  - 4.2.7.3 Residual pattern from previous processing.
  - 4.2.7.4 Edge defects.
  - 4.2.7.5 Other irregularities.
- 4.2.8 If there is a residual pattern from previous processing which may be removed by etching, clean up the crystal per PEI 7.18.07. Then reinspect per this instruction.
- 4.2.9 If the surface condition is uncertain due to dirt or contamination, clean the crystal per PEI 7.18.02. Then reinspect per this instruction.
- 4.2.10 If during the inspection a condition is found which would prevent obtaining a good acoustic surface wave device, further inspection may be discontinued and the crystal returned for rework.
- 4.2.11 An entry will be noted in the log as to whether the crystal is acceptable for processing or to be returned for rework.
- 4.2.12 When the scanning is completed, the illumination will be relocated so as to originate from a direction 45° from the original direction, and the crystal shall be rescanned per 4.2.6 through 4.2.11 above.

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- 4.2.13 A crystal which has been deemed suitable for making an acceptable device will be forwarded to the next operation, or properly stored to await its use. In the latter case, a label shall be attached to its container noting that it has been inspected.
- 4.3 Shut-down.

Not applicable.

### 5.0 REFERENCES

#### HUGHES AIRCRAFT COMPANY GROUND SYSTEMS GROUP

ENGINEERING DIVISION
PROCESS ENGINEERING INSTRUCTION
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Subject

ACOUSTIC SURFACE WAVE DEVICE PROCESS CRYSTAL SURFACE CLEANING

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Number 7.18.02

Date 19 December 1973

Revision A

Approved

#### 1.0 SCOPE

1.1 This instruction covers the cleaning of a crystal surface to obtain a surface suitable for obtaining satisfactory adhesion to photoresist and vacuum deposited metal films.

#### 2.0 EQUIPMENT AND MATERIAL REQUIRED

- 2.1 Equipment.
  - 2.1.1 Laminar flow work station with fume removal.
  - 2.1.2 Oven, vacuum, 200°C and Nitrogen gas purge capability, capable of operation at 25 inches of mercury.
  - 2.1.3 Resistivity meter, Balsbaugh Model 900, or equivalent.
- 2.2 Material.
  - 2.2.1 Crystal, cut and polished, and inspected per PEI 7.18.01.
  - 2.2.2 Deionized water, 12 18 m<sup>2</sup> gohm-cm resistivity and 0.45 micron filtered.
  - 2.2.3 Nitrogen gas, dry, 0.45 micron filtered.
  - 2.2.4 150 mm Petri Dish.
  - 2.2.5 Polyfoam-tipped swabs.
  - 2.2.6 Finger cots.
  - 2.2.7 Rubber-tipped tweezers.
  - 2.2.8 Alconox detergent powder.

#### 3.0 GENERAL REQUIREMENTS

3.1 The cleaned crystal, immediately after cleaning and rinsing and prior to drying, must pass the "water-break" test described in 4.2.8.

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- 3.2 The cleaned crystal must not be touched with bare fingers or be allowed to leave the clean laminar flow work station environment without adequate protection.
- 3.3 The total time elapsed between removal from the cooled vacuumnitrogen oven and initiation of the next process (photoresist or metallization) shall be held to a minimum and shall in no case exceed one-half hour. If this time is exceeded, the crystal shall be recleaned starting with 4.2.7.

#### 4.0 PROCEDURE

- 4.1 Start-up.
  - 4.1.1 Verify D.I. water resistivity with resistivity meter and the flow of the deionized water.
  - 4.1.2 Verify the condition of the final nitrogen gas filter at least weekly.
  - 4.1.3 Adjust the oven temperature to 160° + 2°C.
  - 4.1.4 Verify adequacy of nitrogen gas supply.
  - 4.1.5 Verify that the vacuum to the oven is operational and level is adequate. Set vacuum to  $20 \pm 4$  inches of mercury.
- 4.2 Process Instructions.
  - 4.2.1 Start deionized water flowing.
  - 4.2.2 Cover at least the thumb and first two fingers of each hand with finger cots.
  - 4.2.3 Place about 50 ml of Alconox into the 150 mm petri dish.
  - 4.2.4 Carefully place the crystal to be cleaned into the petri dish.
  - 4.2.5 Moisten a polyfoam swab with deionized water and dip it into the Alconox.
  - 4.2.6 Hold the crystal against a flat surface with one hand while executing a light scrubbing motion across its surface using the swab in the other hand.
  - 4.2.7 Lift the crystal and hold it under the running deionized water so that it flows from one end, across the entire crystal, and leaves at the other end. Allow the water to flow across the crystal for not less than one minute.

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ACOUSTIC SURFACE WAVE DEVICE PROCESS CRYSTAL SURFACE CLEANING

- 4.2.8 Criterion: After removal in a horizontal position from the flow of water, orient the crystal so that the surface supports a volume of water sufficient to distribute itself over the entire crystal. When there is No interruption in the uniform distribution of this water film it may be assumed that the crystal surface is practically clean for the acceptance of continued processing (i.e., photoresist and metallization).
- 4.2.9 If the above "water-break" test fails, return to step 4.2.6 and repeat the remaining cleaning steps.
- 4.2.10 When the crystal surface satisfies the "water-break" test, blow it dry with filtered dry nitrogen gas and place it in a clean dry petri dish.
- 4.2.11 Without leaving the protection of the laminar flow hood place the uncovered petri dish containing the crystal into the vacuum/nitrogen gas oven for an overnight bake @ 160°C 5°C. A sufficient volume of nitrogen gas is "leaked" into the oven to give a partial pressure of 20 inches 4 inches of Hg during the bake.
- 4.2.12 At the end of the bake period, the oven is shut off and allowed to cool to room temperature, while maintaining the vacuum and nitrogen flow.
- 4.2.13 The crystal must be forwarded immediately to the next process step.
- 4.3 Shut-down.
  - 4.3.1 Turn off D.I. water flow.

#### 5.0 REFERENCES

Not applicable

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## ENGINEERING DIVISION PROCESS ENGINEERING INSTRUCTION MICROELECTRONICS

### instruction

Subject

ACOUSTIC SURFACE WAVE DEVICE PROCESS PHOTO RESIST PROCESS

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Number

7.18.03

Date 19 December 1973

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Revision

1.0 SCOPE

This process covers the application of photoresist images on metallized or unmetallized single crystal substrates for acoustic surface wave devices.

### 2.0 EQUIPMENT AND MATERIAL REQUIRED

- 2.1 Equipment.
  - 2.1.1 Aligner and holder (HAC design).
  - 2.1.2 Microscope, 7X to 40X zoom with vertical lighting.
  - 2.1.3 U.V. exposure box (HAC design).
  - 2.1.4 Photo resist dipper (HAC design).
  - 2.1.5 Spray gun.
  - 2.1.6 Laminar flow work stations.
  - 2.1.7 Oven (set at 85°C).
  - 2.1.8 Laminar flow work station with fume removal.
  - 2.1.9 Resistivity meter, Balsbaugh Model 900, or equivalent.

#### 2.2 Material.

- 2.2.1 Crystal, processed per PEI 7.18.02, crystal surface cleaning. If the etch process is to be used, the crystal shall also have been processed per PEI 7.18.04, vacuum deposition.
- 2.2.2 Finger cots.
- 2.2.3 Dry nitrogen gas 0.45 micron filtered.
- 2.2.4 Deionized water, 12 18 megohm resistivity, 0.45 micron filtered.
- 2.2.5 Photo resist, Shipley or equivalent.
- 2.2.6 Photo resist developer, Shipley or equivalent.

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ACOUSTIC SURFACE WAVE DEVICE PROCESS PHOTO RESIST PROCESS

#### 3.0 GENERAL REQUIREMENTS

- 3.1 The photo resist pattern shall conform to the following.
  - 3.1.1 It shall be completely developed.
  - 3.1.2 It shall have no defects that are not also in the photomask.
  - 3.1.3 There shall be no contaminants which will interfere with the formation or delineation of the metal pattern.
  - 3.1.4 The photo resist pattern shall be positioned and aligned on the crystal surface as required.

#### 4.0 PROCEDURE

- 4.1 Start-up.
  - 4.1.1 Make certain the photo resist dipper reservoir is full.
  - 4.1.2 Verify that the oven temperature is 85°C + 5°C.
  - 4.1.3 The crystal clamp should be raised to allow clamping the crystal.
  - 4.1.4 Set motor control to "lower" and speed control to "6".
  - 4.1.5 Prepare the photo resist developer.
  - 4.1.6 Verify D.I. water resistivity with resistivity meter.
- 4.2 Process Instructions.
  - 4.2.1 Attach the crystal at one of its ends to the support wire by means of the clamp of the photo resist dipper.
  - 4.2.2 Remove the cover from the photo resist reservoir.
  - 4.2.3 Set motor control speed at "6" and lower crystal into photo resist solution so that all of the crystal is immersed except that portion held by the clamp.
  - 4.2.4 Set motor control mode on "raise" and motor control speed on 2-1/2 (approximately 1 inch per minute).
  - 4.2.5 Turn on motor control to initiate withdrawal.

CAUTION: Prior to and during the withdrawal, care must be exercised to prevent any vibrations to the coating equipment.

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- 4.2.6 When the crystal has emerged entirely from the photo resist solution the motor control is switched off and the cover immediately placed over the photo resist solution.
- 4.2.7 Allow the crystal to air dry 5 minutes minimum.
- 4.2.8 Remove the crystal from the photo resist dipping apparatus and place in 85°C oven for 6 minutes 30 seconds.
- 4.2.9 Remove the crystal from the oven and allow it to cool to room temperature.
- 4.2.10 Position crystal and mask into aligner-holder.
- 4.2.11 Position crystal, mask, and aligner-holder beneath ultra violet lamp and expose for the required time.
- 4.2.12 Remove crystal from aligner-holder and spray develop for approximately 1 minute.
- 4.2.13 Spray rinse in deionized water (ambient temperature).
- 4.2.14 Blow dry with filtered dry nitrogen.
- 4.2.15 Inspect for acceptable photo resist pattern.
- 4.2.16 Postbake.
  - 4.2.16.1 If the etch process is to follow, postbake at 85°C for 10 minutes 1 minute.
  - 4.2.16.2 If the lift-off process is to be used, do not postbake.

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- 4.2.16.3 Postbake may be done prior to the inspection step (4.2.15).
- 4.3 Shut-down.

Not applicable.

#### 5.0 REFEREICES

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Subject

ACOUSTIC SURFACE WAVE DEVICE PROCESS

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Number 7.18.04

Date 19 December 1973

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#### SCOPE 1.0

This procedure provides a thin film of metallization to be deposited on the crystal surface to satisfy device requirements.

#### 2.0 EQUIPMENT AND MATERIALS REQUIRED

- 2.1 Equipment.
  - Vacuum evaporation system, capable of 5 x 10<sup>-6</sup> torr.. 2.1.1 minimum. vacuum.
  - 2.1.2 Electron gun (E-gun), Airco Temescal, or an alternate energy source, to evaporate source metal.
  - 2.1.3 Necessary tooling to support crystals during evaporation.
  - 2.1.4 Sloan thickness monitor.

#### 2.2 Material.

- Crystal, cut and polished, of the material specified, cleaned per PEI 7.18.02. If the "lift-off" process is to be used, 2.2.1 photoresist coat per PEI 7.18.03.
- 2.2.2 Finger cots.
- 2.2.3 Argon gas.
- 2.2.4 Liquid nitrogen.
- 2.2.5 Source material, as required.

#### 3.0 REQUIREMENTS

- Metal film shall be of the thickness required. Thickness shall be 3.1 determined by use of the Sloan thickness monitor.
- The metal film must be bright (reflective and specular), and not 3.2 matte or cloudy in appearance.
- The metal film must be free of pinholes when viewed at 350X.

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#### **Subject**

#### ACOUSTIC SURFACE WAVE DEVICE PROCESS VACUUM DEPOSITION

- The monitor slide shall pass the "tape test" for metal adhesion. 3.4
- The monitor slide shall be etched for metalization thickness check. 3.5

#### 4.0 PROCEDURE

- 4.1 Start-up.
  - Select proper scale on the Sloan thickness monitor and zero 4.1.1 the instrument.
  - 4.1.2 The vacuum system cleanliness should comply with Class 10,000 of FED-STD-209.
  - 4.1.3 Use 5 grams of source material to perform the deposition.
- Process Instructions.
  - 4.2.1 Caution: The parts or materials to be placed into the vacuum evaporation system and the internal surfaces of the vacuum evaporation system must never be touched by bare hands or fingers. Always wear clean finger cots or appropriate gloves.
  - 4.2.2 Close the high vacuum valve.
  - 4.2.3 Fill the bell jar chamber with argon gas to ambient pressure.
  - 4.2.4 Raise bell jar.
  - 4.2.5 Remove tooling from top of chamber that will support crystals during evaporation.
  - 4.2.6 Load crystals onto holders so that the surface to be patterned to will "see" the evaporant material. Blow off crystals with argon or nitrogen gas. Return holders to position in vacuum system.
  - 4.2.7 Observe evaporant material to make certain there is a sufficient volume to perform the evaporation.
  - 4.2.8 Lower bell jar.
  - 4.2.9 Close foreline valve.
  - 4.2.10 Open roughing valve.
  - 4.2.11 Press "ON" power button to control console.
  - 4.2.12 Admit liquid nitrogen to cold trap until full.

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#### ACOUSTIC SURFACE WAVE DEVICE PROCESS VACUUM DEPOSITION

- 4.2.13 When bell jar chamber pressure is reduced to 50 ± 5 torr, close the roughing valve and open foreline valve.
- 4.2.14 Open high vacuum valve.
- 4.2.15 Turn on Ion gage and degas for approximately 1 minute.
- 4.2.16 Make sure high voltage button is OFF, then turn ON E-gun.
- 4.2.17 Rotate E-gun power control rheostat to minimum (counter-clockwise).
- 4.2.18 When pressure reaches 5 x 10<sup>-6</sup> torr, proceed to 4.2.19.
- 4.2.19 After power warmup, push "ON" E-gun high voltage button.
- 4.2.20 Set E-gun power meter to indicate 100 ma for prebake.
- 4.2.21 Set Sloan meter at frequency relative to desired thickness.
- 4.2.22 Make sure shutter is between the evaporant source and crystals.
- 4.2.23 Increase E-gun power setting to 300 ma.
- 4.2.24 After 5-7 seconds, open shutter to expose crystal to evaporant material.
- 4.2.25 When desired deposition thickness is achieved (as indicated by the Sloan meter), close shutter.
- 4.2.26 Reduce E-gun power control to its minimum position and push switch to off position. Shut off Sloan meter.
- 4.2.27 Shut off Ion gage.
- 4.2.28 Switch therm egage to foreline sensor.
- 4.2.29 Close high vacuum valve.
- 4.2.30 Cool chamber tooling to less than 100°C and then backfill with argon gas.
- 4.2.31 Raise bell jar.
- 4.2.32 If tooling is cool enough, the crystal holders may be removed.
- 4.2.33 With extreme care, the crystals are placed into their protective containers.

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#### ACOUSTIC SURFACE WAVE DEVICE PROCESS VACUUM DEPOSITION

- 4.3 Shut-down.
  - 4.3.1 Lower bell jar.
  - 4.3.2 Close foreline valve
  - 4.3.3 Open roughing valve.
  - 4.3.4 Switch thermocouple gage from foreline sensor to bell jar chamber sensor.
  - 4.3.5 Allow pressure to reach 50 + 5 torr, and close roughing valve.
  - 4.3.6 Open foreline valve.
  - 4.3.7 Return thermocouple gage to foreline sensor.
  - 4.3.8 Shut off main power on console

### 5.0 REFERENCES

5.1 Government Standards and Specifications

Federal Standards

FED-STD-209

Clean Room and Work Station Requirements, Controlled Environment.

5.2 Internal Specifications and Instructions.

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**Subject** 

ACOUSTIC SURFACE WAVE DEVICE PROCESS ETCH PROCESS og e

of

Number

7-18.06

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Approved William F. Can

#### 1.0 SCOPE

This procedure provides for the formation and definition of the metal pattern through the utilization of etch solution.

#### 2.0 EQUIPMENT AND MATERIAL REQUIRED

- 2.1 Equipment.
  - 2.1.1 Container, Etch.
  - 2.1.2 Microscopes, stereozoom and Reichert Zetopan, or equivalent.
  - 2.1.3 Petri dish (dimensions depend on crystal size).
  - 2.1.4 Tweezers
  - 2.1.5 Resistivity meter, Balsbaugh Model 900, or equivalent.
  - 2.1.6 Hot plate with magnetic stirrer.

#### 2.2 Material.

- 2.2.1 Crystal, with the required processes having been performed (PEI 7.18.01, PEI 7.18.02, PEI 7.18.03 and PEI 7.18.04).
- 2.2.2 Aluminum etchant per 4.1.4.
- 2.2.3 Deionized water, 12-18 megohm--cm resistivity, 0.45 micron filtered.
- 2.2.4 Dry nitrogen, 0.45 micron filtered.
- 2.2.5 Phosphoric acid, electronic grade, Baker and Adamson or equivalent.
- 2.2.6 Nitric acid, electronic grade, Baker and Adamson or equivalent.
- 2.2.7 Acetone, electronic grade, Baker and Adamson or equivalent.

#### 3.0 GENERAL REQUIREMENTS

The completed pattern of aluminum on the crystal shall meet the following:

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#### ACOUSTIC SURFACE WAVE DEVICE PROCESS ETCH PROCESS

- 3.1 Metallization must be attached to crystal throughout entire pattern (no lifting).
- 3.2 Any observable shorts or discontinuities shall be brought to the attention of the supervisor or responsible engineer.
- 3.3 If additional cleaning is required clean per PEI 4.18.07.

#### 4.0 PROCEDURE

- 4.1 Start-up.
  - 4.1.1 Verify D.I. water resistivity with resistivity meter.
  - 4.1.2 Aluminum etchant Preparation. Into 180ml ±5ml of deionized water add 800ml ±5ml of phosphoric acid and 40ml ±2ml of nitric acid. Mix thoroughly. Store in a clean, capped polyethylene bottle.
  - 4.1.3 Initiate a flow of deionized water in the sink.
  - 4.1.4 Pour a sufficient volume of aluminum etchant into the etch container to cover crystal. Do not treat more than 150 square inches of metalized crystal surface in each 200ml of solution.

#### 4.2 Process Instructions

- 4.2.1 Hold crystal by edges with tweezers and immerse into aluminum etchant solution.
- 4.2.2 Gently agitate the dish to insure that the crystal "sees" fresh etchant uniformly for 2 to 3 minutes.
- 4.2.3 Remove crystal from alumium etchant and rinse with running deionized water.
- 4.2.4 Observe metallization to see if additional etching is required.
- 4.2.5 If additional etching is necessary, usually 30 secs is sufficient, return to 4.2.1 and go to 4.2.4.
  - NOTE: If the etching is not proceeding satisfactorily, it may be necessary to warm the etchant about 5°C or prepare fresh etchant.

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- 4.2.6 Rinse crystal in deionized water.
- 4.2.7 Blow dry with filtered dry nitrogen.

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#### ACOUSTIC SURFACE WAVE DEVICE PROCESS ETCH PROCESS

- 4.2.8 Inspect the crystal with the aid of a microscope (zoom or Reichert, as required).
- 4.2.9 Strip the photo resist by immersing the crystal in acetone for approximately three minutes.
- 4.2.10 Rinse the crystal with a stream of fresh acetone from a squirt bottle.
- 4.2.11 Blow dry with filtered nitrogen.
- 4.2.12 Inspect under a microscope for completeness of photo resist removal.
- 4.3 Shut-down.

Not applicable.

#### 5.0 REFERENCES

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ACOUSTIC SURFACE WAVE DEVICE PROCESS CLEAN-UP PROCESS

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1.0 SCOPE

> The following procedure is performed to insure that there will be no residual metallization extraneous to the desired pattern.

- 2.0 EQUIPMENT AND MATERIAL REQUIRED
  - 2.1 Equipment.
    - 2.1.1 Microscope, 7X 40X zoom.
  - 2.2 Material.
    - Crystal, with metal pattern etched on its surface as per 2.2.1 PEI 7.18.06 etch process.
    - 2.2.2 Wooden sticks (i.e., polyfoam swabs).
    - 2.2.3 50 or 100 ml beaker.
    - 2.2.4 Aluminum etchant.

#### 3.0 GENERAL REQUIREMENTS

- The crystal must be free of all extraneous metallization either 3.1 within the pattern or outside of it on the top surface of the crystal.
- The completed crystal with metal pattern must comply with the general 3.2 requirements of PEI 7.18.06.

#### 4.0 PROCEDURE

- 4.1 Start-up.
  - Pour small volume of aluminum etchant into 50 or 100 ml beaker. 4.1.1
  - Sharpen polyfoam swab sticks to sharp point.
- 4.2 Process instructions.
  - 4.2.1 Carefully place crystal on the microscope stage, focus for maximum clarity and scan for extraneous metallization.

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### ACOUSTIC SURFACE WAVE DEVICE PROCESS CLEAN-UP PROCESS

- 4.2.2 When an area is discovered that requires additional cleaning, dip the wooden stick into the aluminum etchant and bring the saturated point gently to the material to be eliminated.
  - NOTE: If an area in need of clean-up is part of or adjacent to pattern, use the stick to deliver the etchant but do not physically make contact between stick and metallization.
- 4.2.3 Move the stick so as to agitate the etchant over the area to be eliminated.
- 4.2.4 When the undersireable metal has been removed place the crystal in the flow of running deionized water.
- 4.2.5 Remove the crystal from the running water and rinse with isopropyl alcohol.
- 4.2.6 Blow dry with dry filtered nitrogen.
- 4.2.7 Repeat steps 4.2.2 through 4.2.6 until all undersireable metal is removed from the crystal.
- 4.3 Shut-down.

Not applicable.

#### 5.0 REFERENCES

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Number 7.18.08

ACOUSTIC SURFACE WAVE DEVICE FINAL IN-PROCESS INSPECTION

Date 19 December 1973

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1.0 SCOPE

This instruction provides assurance that device quality is as required.

#### 2.0 EQUIPMENT AND MATERIAL REQUIRED

- 2.1 Equipment.
  - 2.1.1 Reichert Zetopan microscope, or equivalent, with XY stage, incident lighting, and 55X, 110X, 220X magnification capability.
- 2.2 Material.
  - 2.2.1 Crystal processed according to PEI 7.18.05, PEI 7.18.06 and PEI 7.18.07 as applicable.
  - 2.2.2 Finger Cots.
  - 2.2.3 Tweezers.
  - 2.2.4 Process follower sheet.

#### 3.0 GENERAL REQUIREMENTS

- 3.1 There shall be no opens or shorts in the electrode fingers beyond that allowed for the particular device.
- 3.2 There must not be any contamination such as photoresist, finger prints or dirt etc.
- 3.3 The pattern shall be parallel with the long axis of the crystal to the extent it can be determined with the unaided eye.
- 3.4 The pattern shall be centered between the ends of the crystal, unless otherwise indicated by the engineering drawing.

#### 4.0 PROCEDURE

- 4.1 Start-up.
  - 4.1.1 Place finger cots on those fingers that may touch the crystal.
  - 4.1.2 Select the microscope objective that will offer the desirable magnification and insert it into the microscope.

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### ACOUSTIC SURFACE WAVE DEVICE FINAL IN-PROCESS INSPECTION

- 4.1.3 Switch on the microscope illuminator.
- 4.1.4 Rotate the stage control knob so as to bring the stage forward towards the observer.
- 4.1.5 Cautiously position the crystal on the stage so that the surface with the pattern is up and focus for maximum clarity.
- 4.2 Process Instructions.
  - 4.2.1 Scan the entire surface of the crystal making observations as outlined in section 3.0, Process Requirements, and noting same on the process follower sheet.
  - 4.2.2 If there is any metal extraneous to the pattern reprocess the crystal per PEI 7.18.07.
  - 4.2.3 All irregularities, either defined by section 3.0 or not, must be brought to the attention of the supervisor or responsible engineer.
  - 4.2.4 Disposition.
    - 4.2.4.1 Acceptable devices shall be forwarded to the next process step.
    - 4.2.4.2 Unacceptable devices will be dispositioned per the instructions of the supervisor or process engineer.
- 4.3 Shut-down.

Not applicable.

#### 5.0 REFERENCES

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SURFACE ACOUSTIC WAVE (SAW) SUBSTRATE CLEANING	Issue 2 - 13 - 1 =	Revision -
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	Approved 11 Laur	Date 2-3-77

#### 1.0 SCOPE

1.1 This instruction covers surface acoustic wave (SAW) substrate cleaning.

#### 2.0 EQUIPMENT AND MATERIAL REQUIRED

- 2.1 Equipment.
  - 2.1.1 Sink with D.I. water, 14 meg ohm resistivity or greater.
  - 2.1.2 Beakers, size as required.
  - 2.1.3 Tweezers, size 5 or equavalent.
  - 2.1.4 Substrate carrier.
  - 2.1.5 N<sub>2</sub> blow gun.
  - 2.1.6 Wash bottle.
  - 2.1.7 Petri dishes.
  - 2.1.8 Swabs (foam, cotton).
  - 2.1.9 Spinner (optional).
  - 2.1.10 Measuring flask, 100 ml or equivalent.

#### 2.2 Material.

- 2.2.1 Chromium oxide (cro,) reagent grade or equivalent.
- 2.2.2 Sulfuric acid (H2SO4) reagent grade or equivalent.
- 2.2.3 Detergent (Turco Sudz or equivalent).
- 2.2.4 Acetone, reagent grade or equivalent.
- 2.2.5 Dry Nitrogen; 99.9% Purity
- 2.2.6 Isopropanol, reagent grade or equivalent.

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SURFACE ACOUSTIC WAVE (SAW) SUBSTRATE CLEANING

#### 3.0 GENERAL REQUIREMENTS OR INSTRUCTIONS

- 3.1 When cleaned using these processes substrate should exhibit no evidence of undesirable foreign material or contamination when viewed at 30% magnification.
- 3.2 If the substrates are to be subjected to thin film deposition as the next step in device processing then evidence of adequate cleaning will be a successful adhesion test.

#### 4.0 PROCEDURE

- 4.1 As received, SAW substrates can be cleaned using individual or a combination of the following procedures:
  - 4.1.1 Detergent cleaning.
    - 4.1.1.1 Prepare detergent solution by pouring one part of Turco Sudz to 20 parts D.I. water.
    - 4.1.1.2 Hold substrate with tweezers or by other suitable means.
    - 4.1.1.3 Scrub wafer with a diluted detergent solution using a foam swab.
    - 4.1.1.4 Rinse wafer in D.I. water a minimum of 5 seconds making sure to also rinse the tweezers and the area under the tweezers.
    - 4.1.1.5 Blow dry with  $N_2$  using spinner if appropriate.  $N_2$  should be directed toward top of substrate while the back of the substrate may be blotted dry.
  - 4.1.2 Solvent cleaning. Cognizant engineer will specify solvent.
    - 4.1.2.1 Immerse substrate in solvent briefly or until visibly clear of such foreign material as photoresist. Scrub if necessary with foam or cotton swab.
    - 4.1.2.2 Remove from solvent while rinsing part with wash bottle of same solvent (do not let part dry) and transfer to water rinse.

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4.1.2.3 Proceed as in 4.1.1.4 through 4.1.1.5.

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SURFACE ACOUSTIC WAVE (SAW) SUBSTRATE CLEANING

- 4.1.3 Acid cleaning.
  - 4.1.3.1 Prepare chromic acid:
    - 4.1.3.1.1 Pour 10 ±1 grams of chromium oxide (CrO<sub>3</sub>) into a 1,000 ml beaker. Add 10 ml of D.I. water. Stir solution until all chromium oxide is dissolved. Add 600 ml ±200 ml of sulphuric acid and stir carefully.
  - 4.1.3.2 Slowly immerse parts into chromic acid using a suitable holder (Teflon or other material inert to the acid) and leave in acid from 5 to 20 minutes or as necessary to remove residue.
  - 4.1.3.3 Rinse parts by slowly immersing in running D.I. water.
  - 4.1.3.4 Proceed as in 4.1.1.2 through 4.1.1.5.

#### 5.0 REFERENCE

- 5.1 Government standards and specifications.
  - 5.1.1 Not applicable.
- 5.2 Internal specifications.
  - 5.2.1 Not applicable.

## **HUGHES**

HUGHES AIRCRAFT COMPANY GROUND SYSTEMS GROUP

## ENGINEERING DIVISION PROCESS ENGINEERING INSTRUCTION MICROFLECTRONICS

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VACUUM SYSTEM OPERATION

Page 1 of 3 Number 7.18.15

Issue 2-13-78 Revision -

Approved 1 L. T. Date 2.

Approved Date 2.3-78

### 1.0 SCOPE

1.1 This instruction covers the operating procedure for obtaining a vacuum of 10<sup>-5</sup> torr or better using a conventional diffusion pumped vacuum system.

### 2.0 EQUIPMENT AND MATERIALS REQUIRED

- 2.1 Equipment.
  - 2.1.1 Vacuum system Vecco VE-400 or similar.
  - 2.1.2 High voltage power supply.
- 2.2 Materials.
  - 2.2.1 Industrial water.
  - 2.2.2 Argon, 99.999 percent pure.
  - 2.2.3 Nitrogen gas, 99.9% pure
  - 2.2.4 Liquid Nitrogen.

### 3.0 GENERAL REQUIREMENTS OR INSTRUCTIONS

3.1 The bell jar should always be down and system under vacuum except when loading or unloading.

## 4.0 PROCEDURE

- 4.1 Startup.
  - 4.1.1 Open the water valve behind the vacuum system to turn on the cooling water for the diffusion pump and the E-gun.
  - 4.1.2 Close the roughing, foreline, gate and vent valves. They are located on the front panel. These valves are normally closed at this time. Notify the supervisor if any were found to be open. Turn the valves clock wise to close.
  - 4.1.3 Turn on the roughing and diffusion pumps using the marked electrical switches.

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#### VACUUM SYSTEM OPERATION

4.1.4 After 3 -0 minutes, open the foreline valve, by turning the valve counter clock wise.

#### 4.2 Process instructions.

- 4.2.1 Rotating counter clockwise open vent valve until backfill is complete. Then close.
- 4.2.2 Raise belljar by pressing belljar raise button.
- 4.2.3 Perform substrate loading functions.
- 4.2.4 Lower belljar, by pressing belljar and safety switches. Close foreline valve by turning it clockwise.
- 4.2.5 Slowly open roughing valve by turning it counterclockwise.
- 4.2.6 When the pressure drops to 100 μM or less open argon (Ar) bleed valve (toggle) and stabilize pressure at around 100 μm (with micrometer valve).
- 4.2.7 Turn on high voltage supply and increase voltage to initiate a glow discharge and until a current of 400 ma is indicated.

  Maintain the glow discharge from 5 to 20 minutes then turn off H.V. supply.
- 4.2.8 Close Argon bleed valve (toggle).
- 4.2.9 Fill cold trap with liquid No.
- 4.2.10 With pressure below 100 µm, close roughing valve, open foreline valve and slowly open the gate valve.
- 4.2.11 With pressure indicating less than 20 µm, turn on ionization guage (10<sup>-4</sup> range).
- 4.2.12 When ionization guage indicates  $1 \times 10^{-5}$  or less as required, proceed with deposition as described in separate PEI 7.18.16.
- 4.2.13 Turn off ionization guage.
- 4.2.14 Close gate valve.
- 4.2.15 Open (slowly) vent valve until backfill is complete. Then close
- 4.2.16 Raise belljar.
- 4.2.17 Unload chamber.

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#### VACUUM SYSTEM OPERATION

- 4.2.18 Lower belljar.
- 4.2.19 Perform 4.2.5.
- 4.2.20 When roughing pressure drops to 100 µm close the roughing valve.
- 4.2.21 Open foreline valve.
- 4.3 Shutdown.
  - 4.3.1 With foreline valve open and all others closed, turn off diffusion pump.
  - 4.3.2 After 1/2-hour close foreline valve and turn off mechanical pump.

## 5.0 REFERENCE

- 5.1 Government standard and specification.
  - 5.1.1 Not applicable.
- 5.1 Internal specifications and instructions.
  - 5.2.1 PEI 7.18.16 Then Film E-Beam Evaporation.

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## instruction

Subject

THIN FILM E-BEAM EVAPORATION

Page 1 of 2 Number 7.18.16

Issue 2-8-78 Revision —

Approved Date 2-8-78

Approved Date 2-8-78

### 1.0 SCOPE

1.1 This instruction covers thin film deposition using an electron beam evaporator.

### 2.0 EQUIPMENT AND MATERIAL REQUIRED

- 2.1 Equipment.
  - 2.1.1 Vacuum system (VE-400 or similar).
  - 2.1.2 High voltage power supply (CVC Mod. LC031 or similar).
  - 2.1.3 Electron beam equipment (Airco Temescal STIH 270-2M, qun and CV-8, power supply or similar).
  - 2.1.4 Evaporation controller (Inficon XMS-3 or similar).
- 2.2 Material.
  - 2.2.1 Source material as required.

### 3.0 GENERAL REQUIREMENTS OR INSTRUCTIONS

3.1 This process should yield thin evaporated films with a thickness, uniformity and adhesion necessary to fabricate thin film devices.

### 4.0 PROCESS INSTRUCTION

- 4.1 Startup.
  - 4.1.1 Open the vacuum chamber, remove the holder plate and load the substrates on the plate, using button magnets to hold them in place. Carefully replace the holder plate into the chamber by inverting and sliding it onto the support structure.
  - 4.1.2 Evacuate the chamber for evaporation as delineated in Steps 4.2.4 through 4.2.12 in PEI 7.18.15.

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#### THIN FILM E-BEAM EVAPORATION

#### 4.2 Process instruction.

- 4.2.1 Turn on E-beam power supply (main power) and controller (key switch, H.V. on, gun #1 fil. on) assuring that all interlock lights are on.
- 4.2.2 Determine that evaporation controller is appropriately programmed according to the process being used and those listed in the evaporation log book.
- 4.2.3 Press start button on the controller.
- 4.2.4 Manually open shutter by rotating shutter knob C.W. when "thickness 1" lights.
- 4.2.5 Close shutter by reversing 4.2.4 when "thickness 2" light illuminates.
- 4.2.6 Turn off controller and supply.
- 4.2.7 Wait approximately 5 minutes to cool gun before opening chamber.

### 4.3 Shutdown.

4.3.1 To remove substrates, proceed with PEI 7.18.15 - Steps 4.2.13 through 4.2.17.

### 5.0 REFERENCES

- 5.1 Government standards and specifications.
  - 5.1.1 Not applicable.
- 5.2 Internal specifications and instructions.
  - 5.2.1 PEI 7.18.15 Vacuum System Operation.

## HUGHES

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	PHOTORESIST APPLICATION (SPINNING)	Issue 2-13-78	Revision
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### 1.0 SCOPE

1.1 This instruction covers the application of photoresist to a substrate by using the spinning technique.

### 2.0 EQUIPMENT AND MATERIALS REQUIRED

- 2.1 Equipment.
  - 2.1.1 Photoresist spinner (Solid State Equipment Model 103 or equivalent).
  - 2.1.2 No blow gum.
  - 2.1.3 Tweezers.
  - 2.1.4 Oven capable of 125 C.
- 2.2 Materials.
  - 2.2.1 Photoresist Shipley AZ1350B2 or AZ1350J or equivalent as specified by Process Engineer.
  - 2.2.2 Vacuum 20" or better, house vacuum.
  - 2.2.3 No, 99.9% purity.
  - 2.2.4 Finger cots.
  - 2.2.5 Acetone, reagent grade

## 3.0 GENERAL REQUIREMENTS

3.1 Thin uniform photoresist coatings are necessary for high resolution photolithography.

## 4.0 PROCEDURE

- 4.1 Startup.
  - 4.1.1 Provide external facilities hookup to the photoresist spinner as required in the equipment instruction manual.
  - 4.1.2 Turn on electrical power.

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## PHOTORESIST APPLICATION (SPINNING)

- 4.1.3 Rotate speed control fully CCW (minimum speed).
- 4.1.4 Fast/slow switch position in slow position unless otherwise instructed on flow sheet.
- 4.1.5 Place wafer chuck on spindle.
- 4.1.6 Set timer as required, approximately 20 seconds.
- 4.1.7 Place wafer on wafer chuck (centered).
- 4.1.8 Turn on vacuum switch. Vacuum gauge should indicate in excess of 12" and yellow "Low vacuum" light must extinguish.
- 4.1.9 Press start switch.
- 4.1.10 Rotate speed control CW until desired speed is indicated on gauge, approximately 5K RPM or per Cognizant Engineer's instructions.
- 4.1.11 When spinner stops, turn off vacuum and remove wafer.

### 4.2 Procedure.

- 4.2.1 Place wafer on chuck (centered).
- 4.2.2 Turn on vacuum and satisfy 4.1.8.
- 4.2.3 Blow possible foreign material from top of wafer with N<sub>2</sub> blow gun.
- 4.2.4 Apply adequate amount of photoresist to top of wafer with eyedropper or other suitable means.
- 4.2.5 Press start button.
- 4.2.6 When spinner stops, turn off vacuum and remove wafer.
- 4.2.7 Place coated wafers in an oven set to 95 ±5°C for 20 minutes or as specified by the Cognizant Engineer.

### 4.3 Shutdown.

- 4.3.1 Turn off vacuum and electrical power.
- 4.3.2 Clean up using acetone to remove resist residue.

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### PHOTORESIST APPLICATION (SPINNING)

## 5.0 REFERENCES

5.1 Government standards and specifications.

5.1.1 Not applicable

5.2 Internal specifications and instructions.

5.2.1 Not applicable

## **HUGHES**

PROCESS ENGINEERING INSTRUCTION
MATERIAL & PROCESSES

HUGHES AIRCRAFT COMPANY

## instruction

Subject

PHOTORESIST EXPOSURE USING KASPAR 1800
ALIGNMENT/EXPOSURE EQUIPMENT

e age		of 4	Number 7	.18.18
ssue	100	10-112	Revision	-
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### 1.0 SCOPE

1.1 This instruction covers the exposure of a pattern on a photoresist coated substrate using an alignment/exposure machine equipped with a ultraviolet light source.

## 2.0 EQUIPMENT AND MATERIAL REQUIRED

- 2.1 Equipment.
  - 2.1.1 Alignment/exposure machine (Kaspar 1800 or equialent).
  - 2.1.2 Photo mask, as specified.
  - 2.1.3 Filtered and dry pressurized nitrogen source.
  - 2.1.4 Tweezers, 86BSA (Technitool or equivalent).
  - 2.1.5 Petri dish and cover 4 inch diameter.
  - 2.1.6 Vacuum source, 21 inches of mercury, minimum.
- 2.2 Materials.
  - 2.2.1 Wafer, as specified on the applicable drawing.

### 3.0 GENERAL REQUIREMENTS

3.1 The pattern exposed on the photoresist coated substrate shall exactly duplicate the pattern on the photo mask. Lines shall be sharp and clear.

### 4.0 PROCEDURE

- 4.1 Start-up.
  - 4.1.1 Turn on power by depressing "Power" button located on the right side of the console (light illuminator).
  - 4.1.2 Turn on the exposure light by depressing the "Power On" button located on the lamp control power supply to the left of the console (light illuminator).

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## PHOTORESIST EXPOSURE USING KASPAR 1800 ALIGNMENT/EXPOSURE EQUIPMENT

4.1.3 Depress and quickly release (approximately 1 second) the "Starter" button next to the power button on the lamp control power supply to illuminate the exposure light.

NOTE: Allow a minimum of 10 minutes warm up time of the exposure lamp prior to use.

- 4.1.4 Set the exposure time on the timer to that which is specified on the Standard Flow Sheet (SFS).
- 4.1.5 Verify that the turret is rotated to the "Split Field High Power" position.
- 4.1.6 Depress the "Load Mask" and the "Visual Align" buttons on the right side on the console to the left of the exposure head (lights will illuminate).
- 4.1.7 Lift the mask holder table, by hand, to the extreme back position and bring it forward slightly to the stop upright position.
- 4.1.8 Turn on the vacuum to the holder plate by turning the vacuum valve to the right of the console.
- 4.1.9 Locate the mask on the holder plate using the three alignment stops on the plate.

NOTE: Place the emulsion side of the mask toward the front and the mirrored chrome surface away from you.

CAUTION: With the mask holder setting just forward of the extreme back position, the vacuum will hold the mask securely in place. Pushing the mask holder to the extreme back position releases the vacuum to remove the mask.

### 4.2 Procedure.

- 4.2.1 With the mask holder plate in the up position, center the wafer on the chuck. Orient the wafer so that the cut corners are at the top and bottom of the right hand side.
- 4.2.2 Lower the mask holder.
- 4.2.3 Push the mask load button to secure the mask holder table in the down position. (The light will go out.)

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PHOTORESIST EXPOSURE USING KASPAR 1800 ALIGNMENT/EXPOSURE EQUIPMENT .

- 4.2.4 Push the "Load Manual" button to raise the wafer chuck to contact the mask. (The light will illuminate and then go off.)
- 4.2.5 Visually determine the alignment of the wafer edge to the mask. If adjustment is necessary, push the "Mask Load" button. (The light will illuminate.) Raise the mask holder slightly and adjust the alignment by using the rotation adjustment, the alignment disk, and the rotary mask adjustment knobs.
- 4.2.6 When the mask and wafer are properly aligned, push the "Mask Load" button (light out) and the "Contact" button (light on).
- 4.2.7 Center the scanner disk on its pad.
- 4.2.8 Push the "Visual Alignment" button (light out) to lower the exposure head.
- 4.2.9 Set timer per instructions on flow sheet.
- 4.2.10 Turn the turret to the "Expose" position and wait for the exposure light to go off.
- 4.2.11 Return the turret to the "Split Field High Power" position.
- 4.2.12 Push the "Mask Load" and "Visual Align" buttons to raise the exposure head.
- 4.2.13 Raise the mask holder table, and using a pair of tweezers, remove the wafer to a petri dish and cover the wafer.
- 4.2.14 If another wafer is to be processed, repeat steps 4.2.1 through 4.2.13.

#### 4.3 Shut-down.

- 4.3.1 Remove the mask by lifting the mask holder table to the extreme back position to cut off the vacuum. Lift the mask from the locating stops and lower the table.
- 4.3.2 Lower the exposure head by pushing the "Mask Load" and "Visual Align" buttons. (Lights off.)
- 4.3.3 Push the lower button (light off). Close the vacuum valve and turn off the exposure lamp by switching the power off.

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## 5.0 REFERENCES

5.1 Not applicable.

## **HUGHES**

HUGHES AIRCRAFT COMPANY GROUND SYSTEMS GROUP

## ENGINEERING DIVISION PROCESS ENGINEERING INSTRUCTION MICROELECTRONICS

## instruction

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PHOTORESIST DEVELOPMENT	Issue 2-7-72	Revision
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	Approved /	ans Date 2-8-77

## 1.0 SCOPE

1.1 This instruction covers the use of certain developer materials and techniques necessary to produce high resolution images on exposed photoresist coated substrates.

## 2.0 EQUIPMENT AND MATERIALS REQUIRED

- 2.1 Equipment.
  - 2.1.1 Petri dishes or other suitable container for chemical solutions.
  - 2.1.2 Photoresist spinner; Solid State Equipment Model 103 or Equivalent.
  - 2.1.3 N<sub>2</sub> Blow gun.
  - 2.1.4 Sink.
- 2.2 Materials.
  - 2.2.1 D. I. water, 14 meg ohm resistivity or greater.
  - 2.2.2 Developer solution, Shipley AZ developer.
  - 2.2.3 Tweezers, size 5 or equivalent.
  - 2.2.4 Fingers cots.
  - 2.2.5 Dry nitrogen.

## 3.0 GENERAL REQUIREMENTS

3.1 Once a sensitized photoresist coated substrate has been exposed it must be developed (selective removal of certain portions of this resist) yielding an image identical to the mask through which it was exposed.

### 4.0 PROCEDURE

- 4.1 Start up.
  - 4.1.1 Prepare the developer by mixing 50 ml of AZ developer with 50 ml of D. I. water.

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### PHOTORESIST DEVELOPMENT

- 4.2 Procedure.
  - 4.2.1 Immerse exposed substrate for a specified time (10 to 60 seconds) or until visual indication of complete development and remove.
  - 4.2.2 Rinse under running D. I. water for a minimum of 5 seconds.
  - 4.2.3 Proceed with etching process as described in PEI 7.18.20 Step 4.2.1 OR continue with 4.2.4 of this PEI.
  - 4.2.4 After complete rinsing spin wafer dry or blow dry with N2.
- 4.3 Shutdown.
  - 4.3.1 Dispose of chemicals properly.

## 5.0 REFERENCES

- 5.1 Government standard and specifications.
  - 5.1.1 Not applicable.
- 5.2 Internal specification and instructions.
  - 5.2.1 PEI 7.18.20 Thin Film Pattern Definition (Etch).

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## HUGHES

HUGHES AIRCRAFT COMPANY GROUND SYSTEMS GROUP

## ENGINEERING DIVISION PROCESS ENGINEERING INSTRUCTION MICROELECTRONICS

## instruction

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THIN FILM PATTERN DEFINITION (ETCH)

Page 1 of 2 Number 7.18.20

Issue 2-8-78 Revision —

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Date 2-2-78

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1.0 SCOPE

1.1 This instruction describes the etch process by which a pattern that has been previously defined in photoesist coating is etched into an underlying thin film.

## 2.0 EQUIPMENT AND MATERIAL REQUIRED

- 2.1 Equipment.
  - 2.1.1 Petri dishes or other suitable containers for chemical solutions.
  - 2.1.2 Photoresist spinner, Solid State Equipment Model 103 or equivalent.
  - 2.1.3 No blow gun.
  - 2.1.4 Sink
- 2.2 Material.
  - 2.2.1 D. I. water, 14 meg ohm resistivity minimum.
  - 2.2.2 Tweezers, style 5 or equivalent.
  - 2.2.3 Dry nitrogen, 99.9% purity.
  - 2.2.4 Nitric acid reagent grade.
  - 2.2.5 Phosphoric acid reagent grade.
  - 2.2.6 Acetic acid Reagent grade.
  - 2.2.7 Finger cots.

### 3.0 GENERAL REQUIREMENTS

3.1 After a thin film coated substrate has had a photoresist pattern defined on it, the pattern must be etched into the thin film forming the actual circuit pattern in the thin film. This pattern should very closely approximate the mask geometry exhibiting no shorts or opens or variations in line to space ratios.

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## THIN FILM PATTERN DEFINITION (EICH)

## 4.0 PROCEDURE

- 4.1 Startup.
  - 4.1.1 Prepare the aluminum etchant by mixing 60 ml D.I. water, 1,600 ml phosphoric acid, 100 ml acetic acid and 100 ml nitric acid.
- 4.2 Process instructions.
  - 4.2.1 Immerse substrate into etch. Remove when there is visual indication that etching is complete, such as when the field appears clear.
  - 4.2.2 Rinse in running D. I. water for 2 minutes minimum.
  - 4.2.3 After complete rinse, spin dry or blow dry with No.
  - 4.2.4 Inspect and repeat 4.2.1 through 4.2.3, if necessary.
- 4.3 Shutdown.
  - 4.3.1 Dispose of etchant.
  - 4.3.2 Turn off D. I. water.

## 5.0 REFERENCES

- 5.1 Government standards and specifications.
  - 5.1.1 Not applicable.
- 5.2 Internal specifications and instructions.
  - 5.2.1 Not applicable

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## PROCESS ENGINEERING INSTRUCTION MICROELECTRONICS

## instruction

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## 1.0 SCOPE

1.1 This instruction describes the dicing of substrates into individual die.

## 2.0 EQUIPMENT AND MATERIAL REQUIRED

SUBSTRATE DICING

- 2.1 Equipment.
  - 2.1.1 Dicing saw with accessory tools; Electroglass Model 106; or equivalent.
  - 2.1.2 Hot plate, 100°-300°F temperature range.
  - 2.1.3 Petri dishes, 4 to 5 inch diameter.
  - 2.1.4 Vacuum system capable of maintaining 26 inches of mercury.
  - 2.1.5 Photoresist spinner.

### 2.2 Materials.

- 2.2.1 Deionized water.
- 2.2.2 Dry nitrogen gas.
- 2.2.3 Optical mounting pitch; R. Howard Strausberg; or equivalent.
- 2.2.4 Double back tape; 3M; or equivalent.
- 2.2.5 Detergent; Dynatex KERF-AID; or equivalent.
- 2.2.6 Acetone; reagent grade or better.
- 2.2.7 Lubricant; KERF-AID 101, 102; or equivalent.
- 2.2.8 Photoresist; AZ1350J; or equivalent.

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#### DICING

## 3.0 GENERAL REQUIREMENTS OR INSTRUCTIONS

- 3.1 Wafers with multiple circuit patterns are to be cut to yield individual die of single circuit patterns.
- 3.2 The operator shall receive a minimum of 4 hours training from Supervision or Process Engineering in the operation of this equipment and the operational process in accordance with this document.
- 3.3 If the machine malfunctions, notify the supervisor immediately.

### 4.0 PROCEDURE

- 4.1 Start-up
  - 4.1.1 Saw blade replacement and installation.
    - 4.1.1.1 The following tools (supplied with the dicing saw) are required to replace the saw blade.

1. Spindle Nut Wrench Part No. 106122

2. Blade Handler Part No. 106123

3. Blade Stand Part No. 106418

4. Guard Removal Tool Part No. 060952

- 4.1.1.2 Remove the two plastic covers from the front of the spindle housing.
- 4.1.1.3 Turn the nozzle retractor screw full clockwise to retract the nozzle away from the blade area.
- 4.1.1.4 Remove the spindle nut with the Spindle Nut Wrench.
  Hold the exterior knurled tube, and rotate the handle
  clockwise.
- 4.1.1.5 Connect the Blade Handler tool to the VACUUM outlet on the right front cover of the machine.
- 4.1.1.6 Place the Blade Handler over the front of the spindle, firmly against the face of the saw blade to form a vacuum seal.
- 4.1.1.7 Slowly pull the blade from the spindle.

NOTE: If blade is tight on the spindle, rock the handler up and down or to the side while removing the blade from the spindle.

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#### DICING

- 4.1.1.8 Place the blade on the Blade Stand and release the vacuum by pressing the vacuum release button on the end of the handler.
- 4.1.1.9 If the blade is to be saved, place a plastic guard ring on it and remove it from the stand. Damaged blades should be discarded.
- 4.1.1.10 Clean the flange face and spindle shaft surfaces of all debris. These surfaces must be clean to insure proper alignment of the blade with the shaft.
- 4.1.1.11 Place a new blade on the Blade Stand with the white guard ring facing up.
- 4.1.1.12 Remove the guard ring by firmly holding the blade hub against the stand and gradually prying the ring off by working the Guard Removal Tool around the outside edge of the ring.

CAUTION: Do not touch the blade. It is very fragile and can be easily damaged.

- 4.1.1.13 Lower the Blade Handler over the Blade Stand against the blade hub to make a vacuum seal.
- 4.1.1.14 Remove the blade from the Blade Stand.
- 4.1.1.15 Place the blade on the spindle shaft. Make sure it is seated against the spindle flange.
- 4.1.1.16 Release the vacuum by holding the Vacuum Switch button and remove Blade Handler.
- 4.1.1.17 Make sure the face of the spindle nut is free of debris. Place it on the end of the spindle with the large-diameter face against the blade.
- 4.1.1.18 Tighten the spindle nut with the Spindle Nut Wrench.
- 4.1.1.19 Turn the nozzle retractor screw counterclockwise until the nozzle strikes the adjustment setscrew.
- 4.1.1.20 Turn the spindle on and check for correct water flow.
- 4.1.1.21 Readjust the height indicator as described in Section 4.1.5.
- 4.1.1.22 Replace the plastic covers.

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#### DICING

- 4.1.2 Fill lubricant tank with KERF-AID as required.
- 4.1.3 Apply a protective coating of AZ1350J photoresist to wafer per PEI 7.18.17.
- 4.1.4 Mounting substrates to glass mounting plate.
  - 4.1.4.1 Mount quartz substrates using optical mounting pitch as described below:
    - a. Preheat hot plate to 125 ± 5°C.
    - b. Place the glass mounting plate on the hot plate and allow 3-5 minutes for temperature stabilization.
    - c. Apply the mounting pitch to the mounting plate and spread with the rod end of a Q-tip.
    - d. Place the quartz substrate on the mounting pitch and press the substrate with a wooden probe in circuit free areas for intimate contact.
    - e. Remove and allow to cool to room temperature.
  - 4.1.4.2 Mount lithium niobate substrates to a glass mounting plate using double back masking tape.
- 4.1.5 Perform blade height adjustment as described below after approximately 5 hours of cutting time, dressing the blade or changing the blade.
  - **4.1.5.1** Rotate the HEIGHT ADJUST knob clockwise to maximum height.
  - 4.1.5.2 Set BLADE to ON and set HEIGHT ADJUST/RUN switch to HEIGHT ADJUST. This will allow the blade to come down without the water being on.
  - 4.1.5.3 Set AUTO/MAN switch to AUTO.

CAUTION: Do not cut fast or deep while in HEIGHT ADJUST or the blade will be damaged due to the lack of cooling water. Do not cut deeper than 0.001 inch or faster than 0.3 inches per second without water.

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#### DICING

- 4.1.5.4 Place the MODE selector in CUT and turn the SPEED ADJUST valve fully clockwise (closed).
- 4.1.5.5 Press the START/STOP button. Slowly turn the SPEED ADJUST VALVE counterclockwise (open) until the wafer is under the saw blade. Close the SPEED ADJUST valve, stopping the X-axis carriage.
- 4.1.5.6 Slowly lower the blade by turning the HEIGHT ADJUST knob counterclockwise while observing the distance between the blade and the wafer.
- 4.1.5.7 Lower the blade until it just clears the wafer.
- 4.1.5.8 Open the SPEED ADJUST valve slightly so that X-axis will cycle slowly back and forth. Lower the blade in 0.0005-inch steps per pass until a scratch is made across the wafer. If necessary, use the microscope to determine when contact has been made.
- 4.1.5.9 Turn the MODE selector to LOAD. Press the START/STOP botton.
- 4.1.5.10 Lower the blade height to the desired depth of cut.
- 4.1.5.11 Set the HEIGHT ADJUST/RUN switch to RUN.

NOTE: These processes are to be performed only with the concurrence of your supervisor or a process engineer.

An alternate visual method is to use the above procedure but contact the top of the chuck. Do not put a wafer on the chuck. Once contact is made, adjust the height up a distance equal to thickness of the material that is to remain below the cut.

A third visual method is to make contact with a shim equal in thickness to the material that is to remain below the cut.

- 4.1.6 Final setup adjustments.
  - 4.1.6.1 Prior to making a production run, the following adjustments should be made. They are used to set up a programmed sequence for a particular wafer geometry. New adjustments must be made for each new wafer geometry.

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#### DICING

- 4.1.6.2 Wafer size: Three wafer size limits are selected by the WAFER SIZE switch. Use Wafer Size 2 for wafers up to 2 1/4 inches in diameter. Size 3 is for wafers between 2 1/2 and 3 1/4 inches in diameter. Size 4 is for wafers between 3 1/4 and 4 1/4 inches. Select the proper setting as specified on the Standard Flow Sheet and dial it in on the WAFER SIZE switch.
- 4.1.6.3 Speed: Adjust the speed as specified on the Standard Flow Sheet. Speed in the cutting direction (left-to-right) is controlled by the SPEED ADJUST knob and displayed in inches per second. Speed is only sampled once per X-axis cycle; therefore, it must be adjusted while the X-axis is cycling back and forth. For a correct reading do not adjust speed during the cutting pass. The speed indication is a timed pulse rate from a linear encoder and it latches the readouts to results of the last pass. The reading remains until another X-axis pass is completed.
- 4.1.6.4 Index settings: Index settings are determined by following the procedure outlined below.
  - Select an identifiable mark on the wafers so they can always be palced on the chuck in the same direction.
  - Set the chuck to the Phase A position and place a wafer on it.
  - Dial in the A index distance as specified on the Standard Flow Sheet for the horizontal streets.
  - Dial in the B index distance as specified on the Standard Flow Sheet for the vertical streets.
  - Verify index settings by first jogging the center of a street to the microscope reticle and then make one index. It should index to the center of the next street.
  - 6. To check the B index settings, release the chuck lock and rotate the chuck to Phase B position. The wafer should index from the center of one street to the next as it did in Phase A.
  - 7. If the street spacing in unknown, dial in .0100 inch (0.100 mm) on the Phase A index switch.

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DICING

## 4.1.6.4 Index settings: (Continued)

- 8. Align a wafer street center with the microscope reticle in Phase A. Continually index, counting the number of indexes until the reticle crosses the center of the next street. Jog back to realign the reticle with the original street. Dial the number of counted indexes times 0.0100 into the INDEX DISTANCE digitswitch.
- Make a single index and observe the relationship to the next street.
- 10. Return one index to the center of the original street and add a few mils (less than 10) to the index setting and repeat Step 9.
- Readjust the index settings until one index moves the wafer exactly one street.

NOTE: Always return to the original street before changing the index setting in order to eliminate jogging each time.

12. Rotate the chuck to the Phase B position and repeat the above procedure. (Steps 7-11).

This method is recommended over the simple trial and error method which may easily result in index settings that are hard-to-detect multiples of the true street spacing.

### 4.2 Process instructions.

- 4.2.1 Place a wafer on the vacuum chuck.
- 4.2.2 While observing through the microscope, rotate the wafer until a street is roughly aligned with the cross hair. Set the CHUCK VACUUM to ON.
- 4.2.3 Set the MODE selector to ALIGN and press the START/STOP button. The chuck will cycle from side-to-side under the microscope.
- 4.2.4 Observe the relation of the street to the crosshair and adjust the Theta knob until the street runs parallel to the crosshair.
- 4.2.5 Jog the Y-axis until the crosshair is in the center of a street.

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#### DICING

- 4.2.6 Turn the MODE selector to CUT. The blade will automatically go to the rear of the wafer, the blade will lower, the cooling water will start flowing, and the X-axis will travel to the right, cutting the wafer. When the blade reaches the end of the wafer, it will lift and the Y-axis will index to the next street while the X-axis returns to the left at high speed. This entire cycle will repeat until the wafer is completely scribed in one axis. When the entire cycle is complete, the blade will then return to its Home position. To vefify alignment, the cycle can be stopped at any time by pressing the START/STOP button. The cycle can be restarted by pressing the START/STOP button a second time and the cycle will continue. Each time it is restarted, however, the chuck will go the the Home position, at the far left, before completing the previous cut. The operator can, therefore, stop the cutting at any time, then restart to move the chuck to the far left and then stop it a second time as desired under the microscope to observe the cut. By repeatedly starting and stopping, the operator can observe any desired location on the street. stopped in the Auto-Cut mode, the manual controls are reactivated to allow jogging or indexing as required. Always return the Y-axis to the street that it was stopped on in order to ensure cutting of all streets.
- 4.2.7 Press and hold the CHUCK RELEASE button while rotating the chuck to the 90° detent. Release the button and the chuck will lock in place. The system's electronic circuitry will atuomatically switch to the Phase B index switch.
- 4.2.8 Set the MODE selector to ALIGN and press the START/STOP button.
- 4.2.9 Check the Theta alignment and readjust if necessary.
- 4.2.10 Scan or jog the crosshair to the center of a street.
- 4.2.11 Turn the MODE selector to CUT. The saw will automatically cut all the streets at the Phase B index spacing in the same manner as it cut during Phase A.
- 4.2.12 Press and hold the CHUCK RELEASE button while rotating the chuck back to its original position. Release the button to lock the chuck in the starting position (Phase A) for the next wafer.

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4.2.13 Turn the CHUCK VACUUM OFF and remove the wafer.

NOTE: If vacuum is removed while Theta is still in Phase B cut position, an alarm will sound to warn that the chuck is not in the correct starting position for the next wafer.

- 4.2.14 If the wafer cannot be removed easily because of suction caused by the wafer under it, then press the WAFER AIR button to inject air pressure into the chuck, thus, lifting the wafer and releasing the suction.
- 4.3 Shut-down.
  - 4.3.1 Not applicable.

### 5.0 REFERENCES

- 5.1 Government standards and specifications.
  - 5.1.1 Not applicable.
- 5.2 Internal specifications and instructions.
  - 5.2.1 PEI 7.18.17, Photoresist Application (Spinning).

## HUGHES

ENGINEERING DIVISION
PROCESS ENGINEERING INSTRUCTION
MICROELECTRONICS

HUGHES AIRCRAFT COMPANY GROUND SYSTEMS GROUP

## instruction

TOROID ATTACH TO SAW HYBRIDS

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Issue 3-9-78 Revision 
Approved Santa Date 1-30-74

Approved Date 2-7-79

### 1.0 SCOPE

1.1 This instruction describes the internal connection of a tuning coil (toroid) to package leads.

## 2.0 EQUIPMENT AND MATERIAL REQUIRED

- 2.1 Equipment.
  - 2.1.1 Low Power Microscope ~ 40 X.
  - 2.1.2 Temperature controlled soldering iron (2 each)
  - 2.1.3 Tweezers.
  - 2.1.4 Wire cutters.
  - 2.1.5 No blow gum.
- 2.2 Materials.
  - 2.2.1 Platform package (as specified).
  - 2.2.2 Toroids (as specified).
  - 2.2.3 Rosin core solder (Sn 60/Pb 40, 63/37 or as specified) per QQ-S-571 and MIL-F-14256.
  - 2.2.4 Isopropanol, reagent grade or equivalent.
  - 2.2.5 Dry Nitrogen, 99.9% purity.

### 3.0 GENERAL REQUIREMENTS OR INSTRUCTIONS

3.1 When SAW devices are to be packaged with internal tuning, the tuning elements must be interconnected in a manner that is compatible with subsequent processing such as themo-compression bonding.

## 4.0 PROCEDURE

4.1 Startup.

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#### TOROID ATTACH TO SAW HYBRIDS

- 4.1.1 Set temperature of one soldering iron so that it is hot enough to flow solder around package pin, but not hot enough to cause the solder to "wick" up the pin and over the top.
- 4.1.2 (Optional) Set temperature of other soldering iron to solder toroid lead properly to the package itself.
- 4.2 Process Instructions.
  - 4.2.1 Wrap pre-timed toroid lead around package lead, at least 1 but less than 2 full turns.
  - 4.2.2 Apply heat to wire and pin with the iron described in 4.1.1 and apply solder to wire-pin junction.
  - 4.2.3 Remove heat when solder has been observed to flow forming a smooth fillet between the pin and the wire.
  - 4.2.4 If required, solder one lead to the package by applying solder and heating the wire against the package using the soldering iron described in 4.1.2.
  - 4.2.5 Remove heat when solder has been observed to flow forming a smooth fillet between the wire and the package.
  - 4.2.6 Clip excess lead lengths.
  - 4.2.7 Clean flux residue from package with isopropanol. Blow dry with dry nitrogen.
  - 4.2.8 Check that bare toroid wire does not short against package unless the assembly drawing shows it to be grounded.
- 4.3 Shutdown.
  - 4.3.1 Turn off soldering iron(s).

### 5.0 REFERENCE

- 5.1 Government standards and specifications.
  - 5.1.1 Not applicable.
- 5.2 Internal specifications and instructions.
  - 5.2.1 Not applicable.

## HUGHES

HUGHES AIRCRAFT COMPANY

#### ENGINEERING DIVISION PROCESS ENGINEERING INSTRUCTION MTCROFLECTRONTCS

## instruction

Subject

SURFACE ACOUSTIC WAVE DIE MOUNT

Number 7.18.24 . of

Revision Issue

Date 2.2.78 Approved Date 2-3-78

#### 1.0 SCOPE

1.1 This instruction describes the mounting of the SAW die to a package or substrate.

Approved

#### 2.0 EQUIPMENT AND MATERIALS REQUIRED

- 2.1 Equipment.
  - 2.1.1 Dispenser (Hughes RTV dispenser or equivalent).
  - 2.1.2 Tweezers, style 5 or equivalent.
  - 2.1.3 Syringe.
- 2.2 Materials.
  - Dow Corning 3140 or 3144 RTV or equivalent per MII-A-46146. 2.2.1

#### GENERAL REQUIREMENTS OR INSTRUCTIONS 3.0

The SAW die is to be securely attached to a package or a substrate 3.1 in such a way as to provide minimal mechanical stress to the crystal and absorb excess acoustic energy at ends of crystal.

#### 4.0 PROCEDURE

- 4.1 Startup.
  - Determine that dispenser and/or syringe has adequate RTV 4.1.1 and that it is not plugged.
  - Assure that the RTV is being dispensed in the quantity and 4.1.2 location required. Adjust per Process Engineer's instructions, if necessary.
- 4.2 Process Instruction.
  - 4.2.1 Hughes dispenser operation.
    - Place package or substrate on dispenser stage. 4.2.1.1

4.2.1.2 Raise stage to uppermost position.

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## SURFACE ACOUSTIC WAGE DIE MOUNT

- 4.2.1.3 To dispense RTV, slide stage away from the operator to the stop.
- 4.2.1.4 Partially lower stage, approximately .1 inches.
- 4.2.1.5 Slide stage toward the operator to the stop.
- 4.2.1.6 Lower stage to lowest position.
- 4.2.1.7 Remove package or substrate.
- 4.2.2 Hand dispense.
  - 4.2.2.1 Using syringe or other suitable applicator dispense material by hand CAREFULLY.
- 4.2.3 Place crystal on top of RTV bead and press into place making sure there are no air gaps between crystal and package or substrate.
- 4.2.4 Apply RTV to the ends of the crystal, wrapping it up over the end to cover the top surface a distance roughly equal to half the total distance from the end of the transducer pattern to the end of the crystal.
- 4.2.5 Place parts in an open area under luminar flow for RTV to cure (24 to 72 hours).
- 4.3 Shutdown.
  - 4.3.1 Seat RTV dispenser tube.

#### 5.0 REFERENCES

- 5.1 Government standards and spcifications.
  - 5.1.1 MIL-A-46146 Adhesive-Sealants, Silicone, RTV, Non-Corrosive (For use with sensitive metals and equipment).
- 5.2 Internal specifications and instructions.
  - 5.2.1 Not applicable.

# HUGHES HUGHES AIRCRAFT COMPANY GROUND SYSTEMS GROUP

ENGINEERING DIVISION
PROCESS ENGINEERING INSTRUCTION
MICROELECTRONICS

## instruction

Subject

PULSED TIP THERMO-COMPRESSION WIRE BONDING

Page 1 of 17 Number 7.18.25

Issue 2-2-78 Revision 
Approved Date 1-30-78

Approved Date 2-2-78

## 1.0 SCOPE

This instruction covers the attachment of gold wires between microelectronic devices and header, flatpack, or substrate using pulsed tip thermo-compression techniques.

### 2.0 EQUIPMENT AND/OR MATERIAL REQUIRED

- 2.1 Equipment.
  - 2.1.1 Hughes pulse tip thermo-compression wire bonder Model 360, with microscope and light capable of 30X magnification, or equivalent.
  - 2.1.2 Hughes MA-16-10 Heater and Gas Controller.
  - 2.1.3 Hughes MA-16-02B Temperature Calibrator.
  - 2.1.4 Appropriate header adapters.
  - 2.1.5 Gram gauge, 25-150 gram. Haldex AB or equivalent.
  - 2.1.6 Tweezers.
  - 2.1.7 Hughes bonding tools:
    - 2.1.7.1 EBB-07-3 for .0007" wire.
    - 2.1.7.2 EBB-1-15 for .001" wire.
    - 2.1.7.3 EBB-15-15 for .0015" wire.
    - 2.1.7.4 EBB-2-15 for .002" wire.
    - 2.1.7.5 EBB-5-15 for .005" wire.
  - 2.1.8 Hydrogen Flame Orifice.
    - 2.1.8.1 5000-2 for .0007" wire.
    - 2.1.8.2 5000-3 for .001-.0015" wire.
    - 2.1.8.3 5000-4 for .002" wire and larger.

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PULSED TIP THERMO-COMPRESSION WIRE BONDING

### 2.2 Material.

- 2.2.1 Gold wire; 2 5 percent elongation; 99.99 percent purity wound on TC-1 copper light spun wire spool. Single winding required per 760660, or equivalent. Size as required.
- 2.2.2 H<sub>z</sub> gas supply, 5 psi minimum.
- 2.2.3 N<sub>2</sub> gas supply, 3 psi minimum.
- 2.2.4 Die header or die-flat pack assemblies.
- 2.2.5 Finger cots.

### 3.0 GENERAL REQUIREMENTS OR INSTRUCTIONS

- 3.1 Pulsed tip thermo-compression bonded gold wire is used to interconnect microelectronic parts to package or hybrid leads or to other internal components within the same package or hybrid.
- 3.2 All bonds shall meet the requirements of MIL-STD-883, PEI 7.15.22, PEI 7.16.14, 780335 and Tables I and II of this document.
- 3.3 The process is to be performed only by qualified operators per PEI 7.16.03.
- 3.4 The work station must be kept clean and free of contaminants.

### 4.0 PROCEDURE

- 4.1 Setup.
  - 4.1.1 Install the bonding tip in the holding clamps. Make sure that the screw used in clamping holds the bonding tip assembly securely and that the top of the shank is positioned against the stop provided for it. The shanks must be pressed firmly to the back of the holding clamps, otherwise the bonding surface of the capillary will not be parallel to the working surface and inconsistent bonds and pulloffs may result. During this mounting make certain that the power is turned off because any movement of the tip may activate the heating cycle.

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PULSED TIP THERMO-COMPRESSION WIRE BONDING

- 4.1.2 Temperature Calibration (With MA-16-02B)
  - 4.1.2.1 Set up HPB-360 bonder as follows:

- 4.1.2.2 Connect thermocouple to Model MA-16-02 CALIBRATOR via front panel jack.
- 4.1.2.3 Install thermocouple in top of capillary after removing the gold bonding wire. Arrange thermocouple lead wire so that base of thermocouple holder is approximately level.
- 4.1.2.4 Lift bonder flexure assembly to initiate bond heating pulse and observe temperature indication. Bonder must be in AUTOMATIC and one of the three channel lights must be on.
- 4.1.2.5 Increase TEMP CALIBRATE thumbwheel a few steps at a time until 450°C temperature indication is reached.
- 4.1.2.6 If temperature indication is above 450°C. with TEMP CALIBRATE set at .5 it will be necessary to use a lower TEMPERATURE thumbwheel setting for the capillary.
- 4.1.2.7 If 450°C cannot be reached with TEMP CALIBRATE at maximum (3.6), TEMPERATURE at 20 and TIME AT TEMP at 3.0, then check capillary tip for defective connections.
- 4.1.3 Install wire spool. Facilities for both a large spool or a small spool are provided. If a large spool is to be used, remove the glass cover from the spool holder. Install the spool on the foam plastic cylinder. Thread the wire through the hole in the glass cover and replace the glass cover on the spool holder. Be careful that the glass cover does not make contact with the spool of wire during installation. Position the fabric-lined clip onto the small spool mounting cylinder above the tail puller. Remove small spool dust cover when the large spool is used.

If a small spool is to be incorporated it will not be necessary to mount the large reel holder. Instead remove the feltlined clip-on from the Teflon cylinder, install the wire spool on the Teflon cylinder, and cover the wire with the plastic dust tube provided.

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PULSED TIP THERMO-COMPRESSION WIRE BONDING

4.1.4 CAUTION! TURN THE POWER SWITCH OFF WHILE THREADING CAPILLARY.

If the two-inch spool of wire is to be used, thread the wire from the glass cover over the Teflon guide and under the clip that mounts on the guide. Thread the wire through the wire guide near the jaws of the wire puller and then through the capillary tip.

Turn the machine on. This will open the clamps so that the wire will locate itself between the jaws of the wire clamp.

- 4.1.5 Turn on the hydrogen pressure and set the regulator to 5 psi.
  - 4.1.5.1 Bleed the hydrogen line to the unit and connect the hose to the hose connector located on rear of cabinet.

    Make sure the hydrogen hose is free of contamination.
  - 4.1.5.2 Ignite hydrogen pilot with a match and adjust flame size to about .10 diameter ball with the needle valve located on the front face of the flame-off head.
- 4.1.6 Move the Z-motion handle to the right. The bonding sheet will go up to the flame-off position, hesitate for as long as the timer requires, and then return to the search height position. At initial startup, it will probably be necessary to operate the valve several times before the hydrogen fills the tube and ignites at the tip.
  - 4.1.6.1 If the Z-lever is held in the "PULL & BALL" position and not released, the bonding tip will move to the flame-off position and remain there until the handle is released. The flame will still be controlled by gas timer. This action allows accurate positioning of the flame-off tip.
- 4.1.7 Search Height Adjustment.
  - 4.1.7.1 Turn the power supply on. Place a sample substrate in the work chuck and set the #3 search height to the lowest level desired. If a second search height and/or bonding schedule is required, set the #2 search height by adjustment of the search height knob. The search height in which the Z-lever is positioned will be indicated by a light on the left hand front panel. If a third height or bonding cycle is required, another search height (#1) is available.

PULSED TIP THERMO-COMPRESSION WIRE BONDING

- 4.1.7.2 Turn the manual-automatic selector switch to automatic. CAUTION: NEVER operate the unit when the search level lights are off. When in automatic, all three lights operate separately, but only the one that indicates the selected search height will be lighted. Should more than one search height indicator light be on, the search height detents are not accurately adjusted.
- 4.1.7.3 Position the Z-motion lever so that the appropriate search height light is on. It is usually best to start with #3 and the search height about .020 above the bonding area. The unit will operate with a search height from 0 to .100 inches.

#### 4.2 Process.

- 4.2.1 Set Capillary Time, Temperature and Weight as prescribed by the cognizant engineer.
- 4.2.2 Adjust the search heights as in paragraph 4.1.7.
- 4.2.3 Set work stage temperature as prescribed by cognizant engineer and allow 10 minutes warm up.
- 4.2.4 Put the Automatic/Manual Switch in Automatic Mode.
- 4.2.5 Load substrate onto heat column.
- 4.2.6 Manipulate chessman handle and Z-lever to place capillary over bonding point on die. Select the appropriate search height.

NOTE: Refer to assembly diagram for bond location and termination point of each wire to be bonded.

- 4.2.7 Actuate the Z-lever to the left and produce a ball bond.
- 4.2.8 Raise the Z-lever to the appropriate search position and locate the area for bond termination. Actuate the Z-lever to the left and produce a wedge bond.
- 4.2.9 Actuate the Z-lever to the right to flame-off.
- 4.2.10 If the wire clamp is not used, wire tails must be pulled off with tweezers.
- 4.2.11 Repeat Steps 4.2.6 through 4.2.10 for all bonds required.
- 4.2.12 Remove substrate from work stage.

## PROCESS ENGINEERING INSTRUCTION MICROELECTRONICS

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## PULSED TIP THERMO-COMPRESSION WIRE BONDING

- 4.3 Shutdown.
  - 4.3.1 Turn off machine microscope light.
  - 4.3.2 Turn off machine power supply.
  - 4.3.3 Turn off hydrogen and extinguish flame.

## 5.0 REFERENCES

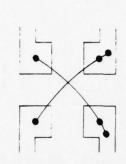
- 5.1 Government Standards and Specifications.
  - 5.1.1 Not applicable.
- 5.2 Internal Specifications and Instructions.
  - 5.2.1 760660 Wire, Gold, for Microelectronic Circuits
  - 5.2.2 PEI 7.15.22 Bonding Wire Acceptance Inspection
  - 5.2.3 PEI 7.16.14 Non-Destruction Pull Test of Wire Bonds

## PROCESS ENGINEERING INSTRUCTIONS MICROELECTRONICS

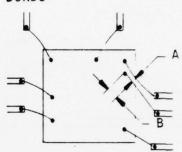
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## THERMOSONIC GOLD BALL BONDING

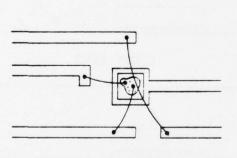
### TABLE I : UNACCEPTABLE BONDS



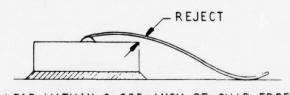
LEAD WIRE CROSSOVER



LEAD WIRES TOO CLOSE WHERE A IS LESS THAN 0.005 INCH AFTER A DISTANCE OF 0.010 INCH FROM THE WIRE TO SUB-STRATE BOND (B)



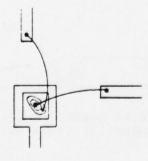
WIRE CROSSES OVER CHIP



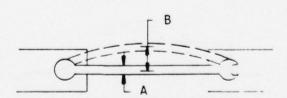
LEAD WITHIN 0.005 INCH OF CHIP EDGE



LEAD WIRE BONDED TO GLAZE OR COATING RATHER THAN PAD



LEAD WIRES CROSS



LEAD DISPLACEMENT B MORE THAN 3 TIMES DIAMETER OF A WHEN VIEWED FROM ABOVE

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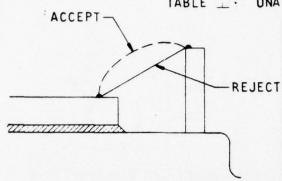
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#### THERMOSONIC GOLD BALL BONDING

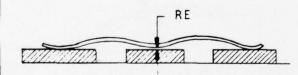


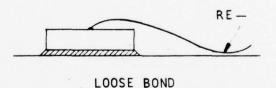


B

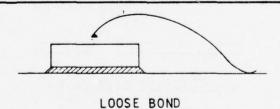
STRESS RELIEF IN LEAD WIRE LESS
THAN 3 WIRE DIAMETERS WHEN WIRE
IS MORE THAN 0.00 INCH IN LENGTH

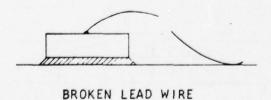
NICKS, CUTS, CRIMPS OR SCORING IN LEAD WIRE WHERE B IS LESS THAN 75 PERCENT OF A

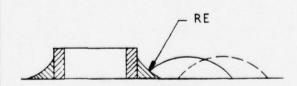




LEAD WIRE LESS THAN 0.005 INCH ABOVE UNINSULATED CONDUCTOR, RESISTOR OR CHIP







LEAD WIRE BONDED TO SOLDER JOINT OR CONDUCTIVE EPOXY RATHER THAN PAD

10

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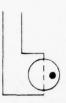
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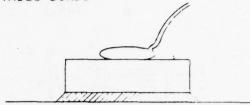
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#### THERMOSONIC GOLD BALL BONDING

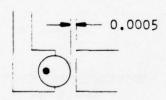
TABLE I: UNACCEPTABLE BONDS



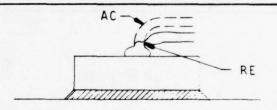
BASE OF LEAD WIRE ON BALL BOND NOT WITHIN PAD AREA



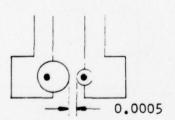
LEAD WIRE DISPLACED TO SIDE OF BALL



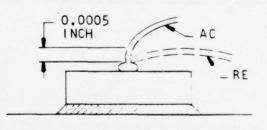
BOND WITHIN 0.0005 INCH OF ADJACENT METALLIZED AREA



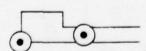
LEAD NECKING EXCEEDS 25 PERCENT OF LEAD DIAMETER



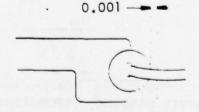
LEAD BONDS LESS THAN 0.0005 INCH DISTANT



BEND TO CLOSE TO BALL



LESS THAN 50 PERCENT OF BALL WITHIN SUBSTRATE PAD AREA



LESS THAN 1 MIL OF OXIDE SEPARATING BOND AND DIE EDGE

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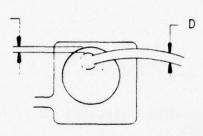
Date

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#### THERMOSONIC GOLD BALL BONDING

TABLE I : UNACCEPTABLE BONDS



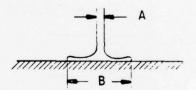
WIRE EXIT LESS THAN 1/2 D FROM PERIPHERY (BALL BONDS ONLY)



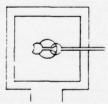
BOND SHORTS ADJACENT METALLIZED AREA



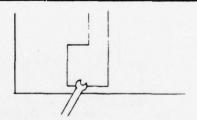
BALL BOND MORE THAN 50 PERCENT OFF CONTACT AND/OR TOUCHING CHIP SURFACE



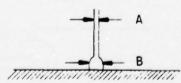
AFTER BONDING, BALL DEFORMED MORE THAN 5 TIMES THE DIAMETER OF THE WIRE; B IS GREATER THAN 5 TIMES A



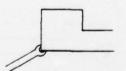
SINGLE WEDGE BOND OR THE FIRST OF TWO WEDGE (STITCH) BONDS MORE THAN 50 PERCENT OFF CONTACT AND/OR TOUCHING CHIP SURFACE



BOND ON EDGE OF BONDING PAD OF CHIP OR SUBSTRATE



AFTER BONDING, DEFORMATION OF BALL IS LESS THAN 2 TIMES THE DIAMETER OF THE WIRE; B IS LESS THAN 2 TIMES A

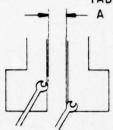


LESS THAN 50 PERCENT OF FIRST WEDGE (STITCH) BOND WITHIN PAD AREA

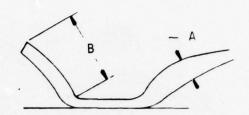
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#### THERMOSONIC GOLD BALL BONDING

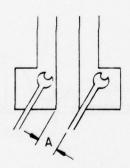
TABLE I: UNACCEPTABLE BONDS



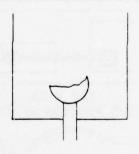
BONDS TOO CLOSE WHEN A IS LESS THAN 0.0005 INCH



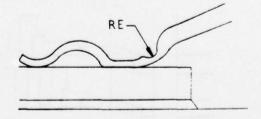
TAIL ON BOND IS LONGER THAN 0.003



ADJACENT PAD AND CONDUCTOR ARE TOO CLOSE WHEN A IS LESS THAN 0.0005 INCH



PORTION OF SINGLE WEDGE BOND MISSING WHERE LESS THAN 0.75 DESIGN SIZE REMAINS



LEAD NECKING EXCEEDS 25 PERCENT OF WIRE DIAMETER

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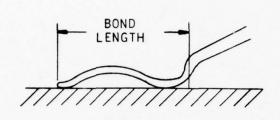
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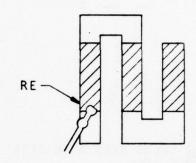
Date 2-2-78

THERMOSONIC GOLD BALL BONDING

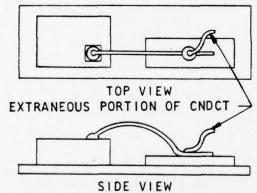
TABLE I: UNACCEPTABLE BONDS



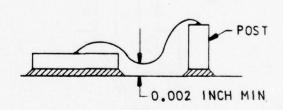
LESS THAN 25 PERCENT OF A SINGLE WEDGE BOND CONTACTS PAD



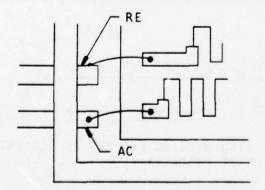
WIRE BOND ON RESISTOR



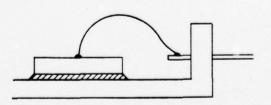
THERE IS NO EVIDENCE OF ELECTRICAL CONNECTION AT THE END OF WIRE



LEAD LESS THAN 0.002 INCH ABOVE SURFACE OF SUBSTRATE



BOND NOT COMPLETELY WITHIN CONFINES OF PACKAGE LAND FLAT



LEAD WIRE EXCEEDS TOP OF FLAT PACK FRAME

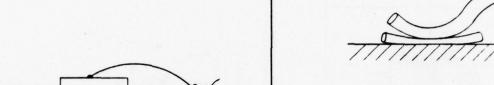
## PROCESS ENGINEERING INSTRUCTION MICROELECTRONICS

Page 13 of 17 Number 7.18.25

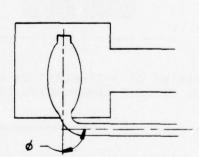
Date 2-2-78 Revision —

#### THERMOSONIC GOLD BALL BONDING

TABLE I : UNACCEPTABLE BONDS

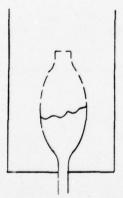


EXCESSIVE LEAD TAIL

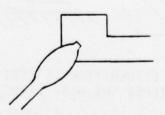


NEW BOND FORMED OVER OLD BOND

BONDWIRE BENT AT MORE THAN 45 DEGREES. Ø IS GREATER THAN 45 DEGREES



PORTION OF LEAD BOND MISSING WHERE LESS THAN 0.75 DESIGN SIZE REMAINS. THIS APPLIES ONLY TO ALUMINUM WIRE BONDED ULTRASONICALLY



LESS THAN 50 PERCENT OF BOND WITHIN PAD AREA

Page 14 of 17

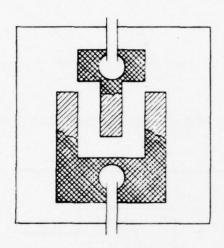
7.18.25

Date 2-2-78

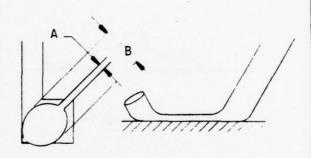
Revision -

### THERMOSONIC GOLD BALL BONDING

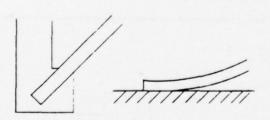
TABLE I: UNACCEPTABLE BONDS



DARKENING OR DISCOLORATION ON ACTIVE AREAS OF CHIP SURROUNDING LEAD BONDS



EXCESSIVE BOND DEFORMATION WHERE B IS MORE THAN 3 TIMES DIAMETER A



BOND DEFORMATION IS LESS THAN 1.2 TIMES THE WIRE DIAMETER

# PROCESS ENGINEERING INSTRUCTION MICROELECTRONICS

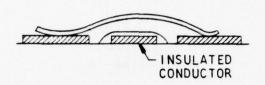
Page of 17 15 2-2-78

Number 7.18.25 Revision -

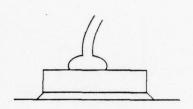
#### THERMOSONIC GOLD BALL BONDING

Date

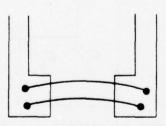
TABLE I : ACCEPTABLE BONDS



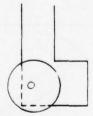
CROSSOVER CONDUCTOR INSULATED OR GLAZED



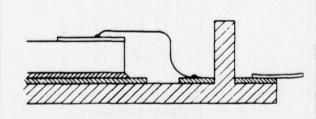
OPTIMUM BALL BOND



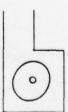
REDUNDANT LEAD BONDS



SLIGHTLY MISALIGNED BALL



GOOD BOND AND LEAD DRESS



SLIGHTLY DEFORMED BALL

Page 16 17

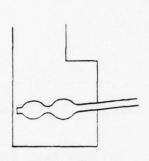
Number 7.18.25

Date 2-2-78

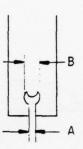
Revision

#### THERMOSONIC GOLD BALL BONDING

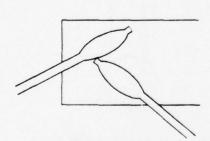
TABLE I : ACCEPTABLE BONDS



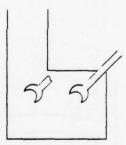
SINGLE OR DOUBLE IMPRESSION ON BOND FOOT



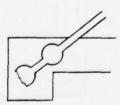
GOOD WEDGE BOND B IS 1.2 TO 3.0 TIMES A



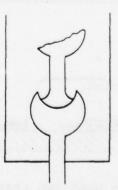
TWO BONDS ON SAME PAD TOUCH



ANY NUMBER OF REBONDS PER PAD, AS L LONG AS THE INTERCONNECTING CONDUC-TIVE PATH IS NOT REDUCED BY MORE THAN THE MINIMUM LINE WIDTH



SLIGHTLY MISALIGNED WEDGE



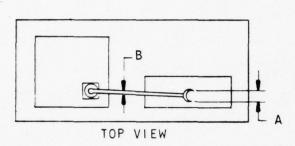
ANY PORTION OF SECOND WEDGE (STITCH) BOND MISSING

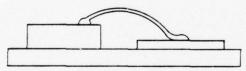
Page 17 of 17 Number 7.18.25

Date 2-2-78 Revision —

#### THERMOSONIC GOLD BALL BONDING

TABLE I : ACCEPTABLE BONDS





SIDE VIEW

GOOD BOND. IF THE WIDTH OF A DOES NOT EXCEED 5 TIMES B TO HALF-MOON TYPE OF BOND OBTAINED WITH GOLD WIRE, ULTRASONICALLY BONDED, IS ACCEPTABLE.

MATERIAL SPECIFICATIONS

. 1

HUGHES

HUGHES AIRCRAFT COMPANY GROUND SYSTEMS GROUP FULLERTON, CALIFORNIA CODE IDENT NO. 05869

MATERIALS AND PROCESSES

CHANGE NOTICE

						CT A THE	ACTIVE	X
SPEC	760781	REV	A_[	MEND	1	STATUS	INACTIVE	

### SINGLE CRYSTAL QUARTZ FOR SURFACE ACOUSTIC WAVE DEVICES

Specification 760781 is amended as follows: 1. Page 3, Table  $\coprod$ . Revise as follows:

Table Ⅲ: Eulerian Angles for Orientation of Crystalline Structure

Identifying		Euleria	n Angles	(degrees)
Number	Orientation	ø	Ð	W
		<u>+</u> 0.25°	<u>+</u> 0.25°	<u>+</u> 0.5°
760781-10	ST-X	0	132.75	0
760781-11	YX	0	90	0
760781-100	ST-X	0	132.75	0
760781-110	YX	0	90	0

STANDARD S RELEASE

DATE:	28 July 1978	ENGINEER: 6.91. Nowell	
DATE.	0 3	APPROVED: 90 Carlement	
0 0 00			_

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### GROUND SYSTEMS MATERIAL SPECIFICATION

APPROVED - MATERIALS & PROCESSES	HUGHES AIRCRAFT COMPANY	76078	1	REV:
APPROVED UKOK	GROUND SYSTEMS GROUP FULLERTON, CALIF. 92634	185UE DATE 78-04-04	REV. DATE	17
APPROVED Wardenut		PRE PARED BY:	curkl.	
			METRI	С

### SINGLE CRYSTAL QUARTZ FOR SURFACE ACQUISTIC WAVE DEVICES

- 1. SCOPE
- T.l This specification establishes the requirements for quartz materials to be used in the fabrication of surface acoustic wave devices.
  - 1.2 <u>Classification</u>. Quartz covered by this specification shall be of the forms and orientation shown in Table I.

Table I: Forms and Orientations of Quartz Crystal.

Identifying Number	Form	Orientation (See 3.2)
760781	Boule	As grown (See 3.2.1)
760781-10	Plate	ST-X
760781-11	Plate	YX
760781-100	Substrate	ST-X
760781-110	Substrate	YX

- 2. APPLICABLE DOCUMENTS
- 2.1 There are no applicable government documents

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2.2 Other. The following document, of the issue in effect on date of invitation for bids, forms a part of this specification to the extent specified herein. In the event of a conflict between the referenced document and this specification, the contents of this specification shall govern.

#### Hughes Aircraft Company (GSG)

P81

Eulerian Angles

(Copies of GSG documents may be obtained from the Hughes Aircraft Company, P. O. Box 3310, Fullerton, CA. 92634.)

#### 3. REQUIREMENTS

3.1 The quartz shall be a single, polarized crystal in the form of a boule, plate, or substrate that has been oriented, cut, and finished in accordance with the requirements herein (See 6.1).

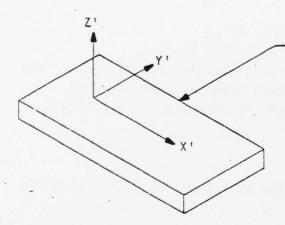
#### 3.2 Orientation.

- 3.2.1 Boules. The specified axis shall be within 2° of the major axis of the boule (see 6.1.1).
- 3.2.2 <u>Plates and substrates</u>. The crystalline axes (X Y Z) shall be oriented to the surface axes (X' Y' Z') of the plate or substrate (Figure 1) as determined by the applicable Eulerian angles ( $\delta + \Psi$ ) specified in Table II. Eulerian angles are defined in Standard Design Drawing P81 (summary of the description given in Classical Mechanics by Herbert Goldstein).
- 3.2.2.1 Orientation identification. When the standard surface acoustic wave propagation direction is not the longest axis of the plate or substrate, the orientation shall be clearly identified on each plate or substrate.

-	HUGHES AIRCRAFT CO. FULLERTON, CALIFORNIA	GROUND SYSTEMS MATERIAL SPECIFICATION	760781	А
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Table  $\coprod$ : Eulerian Angles for Orientation of Crystalline Structure

Orientation	Tolerance ±0.1°
ST-X	0, 132.75, 0
YX	0, 90, 0
ST-X	0, 132.75, 0
YX	0, 90, 0
	YX ST-X



Indexing edge establishes X' axis of plate or substrate.

Y' and Z' axes are related, as shown.

For (0, 0, 0), X', Y', and Z' coincide with X, Y, and Z, respectively.

# FIGURE 1: IDENTIFICATION OF SURFACE AXES FOR PLATES AND SUBSTRATES

### 3.3 Dimensions.

3.3.1 <u>Boules</u>. The length and diameter specified in the applicable purchase document for the boule are minimum dimensions. When the boule is ordered by weight, the weight specified on the applicable purchase document is the minimum acceptable net weight.

HUGHES AIRCRAFT CO. FULLERTON, CALIFORNIA	GROUND SYSTEMS MATERIAL SPECIFICATION	760781	Д

- 3.3.2 <u>Plates</u>. Plate dimensions are as specified in the applicable purchase document. Tolerances are as follows:
  - (a) Length and width or diameter values are minimum dimensions.
  - (b) Thickness is +0.5, -0 mm (+0.020, 0.000 inches).
  - (c) Top and bottom surfaces shall be parallel within 0.25 mm (.01 inch).
- 3.3.3 <u>Substrates</u>. Substrate dimensions are as specified in the applicable purchase document. Tolerances are as follows:
  - (a) Length and width or diameter values are minimum dimensions.
  - (b) Thickness is  $\pm 0.05$  mm ( $\pm 0.002$  inch).
  - (c) Top and bottom surfaces shall be parallel within 0.002 mm per mm (0.002 inch per inch).
- (d) The polished surface shall be flat within 0.08 wave per millimeter (2 waves per inch).
  - 3.4 <u>Surface Finish</u>. Surface finish shall be as specified in Table <u>TII</u> and as defined herein. 120 grit surface shall exhibit a finish at least equivalent to that obtained from a lapping operation using 120 grit carborundum. Polished surfaces shall be such that examination at 250 diameter magnification does not reveal scratches nicks, pits, or other blemishes that will adversely affect the intended application.

Table III: Quartz Crystal Surface Finish

Ident Number	Material Form	Surface Finish
760781	Boule	As grown; if cut to rough shape, not to exceed surface roughness height of 6.3 µm (250 microinches).
760781-1X	Plate	As cut; not to exceed surface roughness height of 6.3 um (250 microinches).
760781-1XX	Substrate	Top surface surface - polished Opposite surface - 120 Grit

3.5 Workmanship. The material shall be free of gross impurity, high strains or optical inhomogeneities. There shall be no cracks, blisters, bubbles, pits, inclusions or unspecified holes or notches as viewed in ordinary white light using the unaided eye. Evidence of chipping or protrusions on any edge or surface shall not extend more than 0.25 mm (0.010 inch) from the outside edges or surface nor more than 0.13 mm (0.005 inch) from a hole, notch, slot or other specified topographical feature.

#### 4. QUALITY ASSURANCE PROVISIONS

- 4.1 Responsibility for inspection. Unless otherwise specified in the contract or purchase order, the supplier is responsible for the performance of all inspection requirements as specified herein. Except as otherwise specified, the supplier may utilize his own facilities or any commercial laboratory acceptable to the contracting activity. The contracting activity reserves the right to perform any of the inspections set forth in this specification where such inspections are deemed necessary to assure supplies and services conform to prescribed requirements.
- 4.2 Acceptance tests. Acceptance tests shall consist of the following:

Determination of quantity of pieces.

NOTE: Receiving inspection activity is prohibited from opening packages as material is easily contaminated by handling.

4.3 Test procedures. The following procedures shall be used by the procuring agency to ascertain compliance with the requirements of this specification. Failure to meet the requirements when tested by these methods will constitute failure to qualify and be cause for rejection of the shipment.

- 4.3.1 <u>Dimensions</u>. Compliance to dimensional requirements specified in the purchase document and tolerances specified herein shall be established using standard measuring devices of the appropriate precision.
- 4.3.2 Until the technical details of measuring the parameters associated with the requirements of section 3.2 are suitably developed, compliance with these requirements will be established by engineering.
- 4.3.3 <u>Workmanship</u>. The pieces shall be examined visually up to 250X magnification to determine compliance to the requirements of 3.4 and 3.5.

#### 5. PREPARATION FOR DELIVERY

- 5.1 Packaging and packing. Packaging and packing shall conform to good commercial practice and shall be such as to protect the material from contamination and mechanical damage or any change of composition and form during shipment and prolonged storage. Packing shall be so arranged as to facilitate inventory audit by weighing or counting.
- 5.2 <u>Package marking</u>. Marking shall include but not necessarily be limited to the following:

760781 (and applicable dash numbers, if any)
Manufacturer's name or code
Manufacturer's material designation
Lot or batch identification
Quantity
Contract or procurement number
A prominent statement on outer packaging:

"Do Not Open For Inspection Unless Ultimate User Is Present."

5.3 All marking shall be clearly legibly, contrasting in color and shall not be obliterated by normal handling and storage.

2-7

PAGE

HUGHES AIRCRAFT CO. FULL ERTON, CALIFORNIA	GROUND SYSTEMS MATERIAL SPECIFICATION	760781	А
	GROUND SYSTEMS MATERIAL SPECIFICATION	760781	А

- 6. NOTES
- 6.1 Ordering data.
- 6.1.1 Boule. Procurement documents shall specify:
- (a) Boule
- (b) 760781
- (c) Minimum length and diameter, or weight of boule.
- (d) Major axis of the boule.
- (e) Title, number, and date of this specification.
- (f) Special instructions for packaging (See 5.).
- (g) Location of reference flat, if required.
- 6.1.2 <u>Plates and substrates</u>. Procurement documents shall specify:
  - (a) Title, number, and date of this specification.
  - (b) Material identification number, including applicable dash number.
  - (c) Plate or substrate.
  - (d) Material thickness.
  - (e) Minimum diameter or length and width of plate or substrate.
  - (f) Special instructions for packaging (See 5.).

HUGHES AIRCRAFT CO. FULLERTON, CALIFORNIA GROUND SYSTEMS MATERIAL SPECIFICATION	760781	A
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### 7. QUALIFIED SOURCE

7.1 Procurement under this specification is limited to the product shown below:

	Manufacturer's	
Material	Designation	Manufacturer's Name and Address
760781	Single Crystal Quartz, Boule	Valpey-Fisher 75 South Street Hopkinton, MA. 01748 Phone: (617) 435-6831 FSCM: 21821
.760781-10	Single Crystal Quartz, Plate ST-X	Local Source
760781-11	Single Crystal Quartz, Plate YX	Wolf Engineering P. O. Box 2311 Newport Beach, CA. 92663 Phone: (714) 646-7214
760781-100	Single Crystal Quartz, Substrate ST-X	Toyo Communication Equipment Co., Ltd. Toyo Bldg., Jingumae 6-12-20 Shibuya-ku, Tokyo, Japan Telex: 02423001 T0Y0C0 J
		Local Source
760781-110	Single Crystal Quartz, Substrate YX	IHP, Inc. 16871 Noyes Avenue Irvine, CA. 92714 Phone: (714) 546-4651



#### HUGHES AIRCRAFT COMPANY GROUND SYSTEMS GROUP FULLERTON, CALIFORNIA

CODE IDENT NO. 05869

MATERIALS AND PROCESSES

CHANGE NOTICE

			STATUS
SPEC	760716	REV C X AMEND	STATUS

### LITHIUM NIOBATE FOR SURFACE ACOUSTIC WAVE DEVICES

Specification 760716, Revision B, has been revised as follows:

### Revision C

- 1. Document designated METRIC.
- 2. Corrected designation of orientation from 41.5  $\times$  to 41.5  $\times$  X.
- 3. Added 41.5 Z', X plate and substrate to approved sources.
- 4. Minor editorial and typographical errors corrected.

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### GROUND SYSTEMS MATERIAL SPECIFICATION

APPROVED - MATERIALS & PROCESSES	HUGHES AIRCRAFT COMPANY	76071	6	REV:
APPROVED: DWKN by	GROUND SYSTEMS GROUP	155UE DATE 76-04-03	78-04-	-,
APPROVED Markins.	CODE IDENT. NO. 05869	PRE PARES BY:	vell	
		, , , ,	METRIC	

## ACOUSTIC WAVE DEVICES

- 1. SCOPE.
- 1.1 This specification establishes the requirements for Lithium Niobate materials to be used in the fabrication of surface acoustic wave devices.
- 1.2 <u>Classification</u>. Lithium Niobate covered by this specification shall be of the forms and orientation shown in Table I.

Table I: Forms and Orientations of Lithium Niobate

	Identifying Number	Form	Orientation (See 3.2)
	760716	Boule	As grown (See 3.2.1)
	760716-10	Plate	YZ
	760716-11	Plate	41.5 Z', X
i	760716-100	Substrate	YZ
	760716-110	Substrate	41.5 Z', X

- 2. APPLICABLE DOCUMENTS
- 2.1 There are no applicable government documents.

2.2 Other. The following document, of the issue in effect on date of invitation for bids, forms a part of this specification to the extent specified herein. In the event of a conflict between the referenced document and this specification, the contents of this specification shall govern.

### Hughes Aircraft Company (GSG)

P8

Eulerian Angles

(Copies of GSG documents may be obtained from the Hughes Aircraft Company, P. O. Box 3310, Fullerton, CA. 92634.)

#### 3. REQUIREMENTS

3.1 The Lithium Niobate shall be a single, polarized crystal in the form of a boule, plate, or substrate that has been oriented, cut, and finished in accordance with the requirements herein (See 6.1)

#### 3.2 Orientation.

- 3.2.1 Boules. The specified axis shall be within  $2^{\circ}$  of the major axis of the boule (See 6.1.1).
- 3.2.2 <u>Plates and substrates</u>. The crystaline axes (X Y Z) shall be oriented to the surface axes (X' Y' Z') of the plate or substrate (Figure 1) as determined by the applicable Eulerian angles ( $\phi \psi$ ) specified in Table  $\Pi$ . Eulerian angles are defined in Standard Design Drawing P81 (summary of the description given in Classical Mechanics by Herbert Goldstein).
- 3.2.2.1 Orientation identification. When the standard surface acoustic wave propagation direction is not the longest axis of the plate or substrate, the orientation shall be clearly identified on each plate or substrate.

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FULL	ERT	ON,	CAL	IFC	RNIA

GROUND SYSTEMS MATERIAL SPECIFICATION

760716

Table  $\coprod$ : Eulerian Angles for Orientation of Crystaline Structure

Identifying <b>N</b> umber	Orientation	Eulerian Angles $\phi \in \Psi$ (degrees) Tolerance $\pm 0.1^{\circ}$
760716-10	ΥZ	0, 90, 90
760716-11	41.5 Z', X	0, 41.5, 0
760716-100	ΥZ	0, 90, 90
760716-110	41.5 Z', X	0, 41.5, 0



 Indexing edge establishes X' axis of plate or substrate.

Y' and Z' axes are related, as shown. For (0, 0, 0) the X', Y' and Z' axes coincide with the X, Y, and Z axes respectively.

## FIGURE 1. IDENTIFICATION OF SURFACE AXES FOR PLATES AND SUBSTRATES

### 3.3 Dimensions.

3.3.1 <u>Boules</u>. The length and diameter specified in the applicable purchase document for the boule are minimum dimensions. When the boule is ordered by weight, the weight specified on the applicable purchase document is the minimum acceptable net weight.

1 6

- 3.3.2 <u>Plates</u>. Plate dimensions are as specified in the applicable purchase document. Tolerances are as follows:
  - (a) Length and width or diameter values are minimum dimensions.
  - (b) Thickness is +0.5, -0 mm (+0.020, -0.000 inches).
  - (c) Top and bottom surfaces shall be parallel within 1.25 mm (.01 inch).
- 3.3.3 <u>Substrates</u>. Substrate dimensions are as specified in the applicable purchase document. Tolerances are as follows:
  - (a) Length and width or diameter values are minimum dimensions.
  - (b) Thickness is  $\pm 0.05$  mm ( $\pm 0.002$  inch).
  - (c) Top and bottom surfaces shall be parallel within 0.002 per mm (0.002 inch per inch).
  - (d) The polished surface shall be flat within 0.08 wave per millimeter (2 waves per inch).
- 3.4 <u>Surface finish</u>. Surface finish shall be as specified in Table TII and as defined herein. 120 grit surface shall exhibit a finish at least equivalent to that obtained from a lapping operation using 120 grit carborundum. Polished surfaces shall be such that examination at 250 diameter magnification does not reveal scratches. nicks, pits, or other blemishes that will adversely affect the intended application.

Table III: Lithium Niobate Crystal Surface Finish

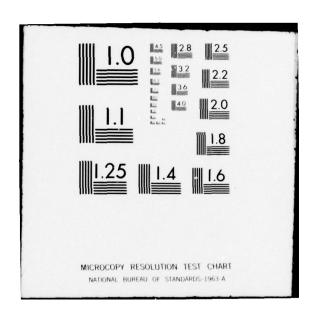
-	makes as seen a seen of		
	Identifying Number	Material Form	Surface Finish
	760716	Boule	As grown; if cut to rough shape, not to exceed surface roughness height of 6.3 am (250 microinches).
	760716-1X	Plate	As cut; not to exceed surface roughness height of 6.3 am (250 microinches).
	760716-1XX	Substrate	Top surface -polished Opposite surface - 120 Grit

- 3.5 <u>Poling</u>. The boule shall be electrically poled to the extent that an iso-gyre inspection shall clearly show a cross pattern.
- 3.6 <u>Workmanship</u>. The material shall be free of gross impurity, high strains or optical inhomogeneities. There shall be no cracks, blisters, bubbles, pits, inclusions or unspecified holes or notches as viewed in ordinary white light using the unaided eye. Evidence of chipping or protrusions on any edge or surface shall not extend more than 0.25 mm (0.010 inch) from the outside edges or surface nor more than 0.13 mm (0.005 inch) from a hole, notch, slot or other specified topographical feature.
  - 4. QUALITY ASSURANCE PROVISIONS
- 4.1 Responsibility for inspection. Unless otherwise specified in the contract or purchase order, the supplier is responsible for the performance of all inspection requirements as specified herein. Except as otherwise specified, the supplier may utilize his own facilities or any commercial laboratory acceptable to the contracting activity. The contracting activity reserves the right to perform any of the inspections set forth in this specification where such inspections are deemed necessary to assure supplies and services conform to prescribed requirements.
- 4.2 <u>Acceptance tests</u>. Acceptance tests shall consist of the following:

Determination of quantity of pieces.

- NOTE: Receiving inspection activity is prohibited from opening packages as material is easily contaminated by handling.
- 4.3 Test procedures. The following procedures shall be by the procuring agency to ascertain compliance with the requirements by these methods will constitute failure to qualify and be rejection of the shipment.

HUGHES AIRCRAFT CO FULLERTON CALIF GROUND SYSTEMS GROUP F/6 9/5
PHOTOLITHOGRAPHIC TECHNIQUES FOR SURFACE ACOUSTIC WAVE (SAW) DE--ETC(U) AD-A064 197 DEC 78 A W DOZIER FR-79-12-40-VOL-1 DAAB07-75-C-0044 DELET-TR-75-0044-F-VOL-1 UNCLASSIFIED NL 2 OF 4 



- 4.3.1 <u>Dimensions</u>. Compliance to dimensional requirements specified in the purchase document and tolerances specified herein shall be established using standard measuring devices of the appropriate precision.
- 4.3.2 Until the technical details of measuring the parameters associated with the requirements of sections 3.2 and 3.5 are suitably developed, compliance with these requirements will be established by engineering.
- 4.3.3 <u>Workmanship</u>. The pieces shall be examined visually up to 250X magnification to determine compliance to the requirements of 3.4 and 3.6.

#### 5. PREPARATION FOR DELIVERY

- 5.1 <u>Packaging and packing</u>. Packaging and packing shall conform to good commercial practice and shall be such as to protect the material from contamination and mechanical damage or any change of composition and form during shipment and prolonged storage. Packing shall be so arranged as to facilitate inventory audit by weighing or counting.
- 5.2 <u>Package marking</u>. Marking shall include but not necessarily be limited to the following:

760716 (and applicable dash numbers, if any)
Manufacturer's name or code
Manufacturer's material designation
Lot or batch identification
Quantity
Contract or procurement number
A prominent statement on outer packaging:

"Do Not Open For Inspection Unless Ultimate User Is Present."
An explanation of orientation indicators (See 3.2.2.1).

- 5.3 All marking shall be clearly legible, contrasting in color and shall not be obliterated by normal handling and storage.
  - 6. NOTES
  - 6.1 Ordering data.
  - 6.1.1 Boule. Procurement documents shall specify:
  - (a) Boule
  - (b) 760716
  - (c) Minimum length and diameter, or weight of boule.
  - (d) Major axis of the boule.
  - (e) Title, number, and date of this specification.
  - (f) Special instructions for packaging (See 5.).
  - (g) Location of reference flat, if required.
- 6.1.2 <u>Plates and substrates</u>. Procurement documents shall specify:
  - (a) Title, number and date of this specification.
  - (b) Material identification number, including applicable dash number.
  - (c) Plate or substrate.
  - (d) Material thickness.
  - (e) Minimum diameter or length and width of plate or substrate.
  - (f) Special instructions for packaging (See 5.).

HUGHES AIRCRAFT CO. FULLERTON, CALIFORNIA	GROUND SYSTEMS MATERIAL SPECIFICATION	760716	(

### 7. QUALIFIED SOURCE

7.1 Procurement under this specification is limited to the product shown below:

Material	Manufacturer's Designation	Manufacturer's Name and Address
760716	Lithium Niobate Boule, transducer grade.	Crystal Technology, Inc. 2510 Old Middlefield Way Mountain View, CA. 94043
760716-1 <b>0</b>	Lithium Niobate Plate, transducer grade. YZ	Phone (415) 961-9311 FSCM: 50559
760716-11	Lithium Niobate Plate, 41.5 Z', X	
760716-100	Lithium Niobate Substrate, YZ	Union Carbide Corporation Electronics Division
760716-110	Lithium Niobate Substrate, 41.5 Z',X	3615 Del Amo Blvd. Torrance, CA. Phone: (213) 371-5521

DRAWING (DWG) AND PARTS LIST (PL)

	REVISIONS		
LTR	DESCRIPTION	DATE	APPROVED

EULERIAN ANGLES ARE THREE SUCCESSIVE ANGLES OF ROTATION USED TO ORIENT CRYSTALINE STRUCTURES RELATIVE TO PLATE AND SUBSTRATE SURFACES. THEY ARE APPLIED AS FOLLOWS:

2

(A) FIRST THE INITIAL SYSTEM OF AXES XYZ ARE ROTATED COUNTER-CLOCKWISE ABOUT THE Z AXIS BY AN ANGLE & (FIGURE 1). THE RESULTING COORDINATE SYSTEM IS LABELLED THE 694 AXES.

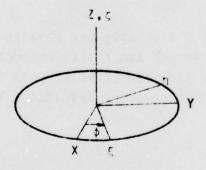


FIGURE 1. FIRST ROTATION

#### STANDARD DESIGN DRAWING 10 SHEET 11 12 13 **REV STATUS** OF SHEETS REV CONTRACT: HUGHES AIRCRAFT COMPANY UNLESS OTHERWISE NONE FULLERTON, CALIFORNIA SPECIFIED DIMENSIONS ARE IN INCHES AND EULERIAN ANGLES PER ANSI Y14.5 .xxx +.010 FSCM NO. SIZE DWG NO. REV P81 05869 $.xx \pm .03$ C ANGLES +0.5° SCALE NONE SHEET 1 OF 2

(B) NEXT, THE INTERMEDIATE AXES ARE ROTATED COUNTERCLOCKWISE ABOUT THE & AXIS BY AN ANGLE & (FIGURE 2). THIS NEW SET OF AXES IS LABELLED & 'n'C'.

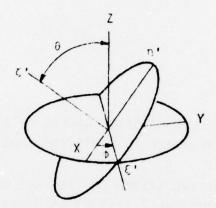


FIGURE 2. SECOND ROTATION

(C) FINALLY, THE E'n'S' AXES ARE ROTATED COUNTERCLOCKWISE ABOUT THE 5' AXIS BY THE ANGLE "TO PRODUCE THE DESIRED X'Y'Z' AXES (FIGURE 3) WHICH COINCIDE WITH THE PLATE OR SUBSTRATE SURFACES AS SHOWN IN THE APPLICABLE MATERIAL SPECIFICATION.

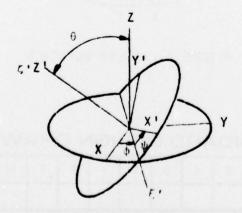


FIGURE 3. THIRD ROTATION

HUGHES AIRCRAFT COMPANY	CONTRACT:			
DR W. Schus 78-05-30	A 0586	P81	REV	
100.150	SCALE 3-2	SHEET 2		

14-338 1 GS 11 76

	REVISIO	NS	
LTR	DESCRIPTION	DATE	APPROVED
-	PRODUCTION RELEASE	77-11-10	LRIS

REV STATUS	SHEE	Т	1	1 2	3	4	5	6	7 1	8	9	10	11	12	13	14	15	16
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UNLESS OTHERWISE SPECIFIED DIMENSIONS ARE IN INCHES AND PER ANSI Y14.5		CONTRACT: DAAB07-75-C-0044					1	HUGHES HUGHES AIRCRAFT COMPANY FULLERTON, CALIFORNIA										
		OR Burns 77-09-28					28	DELAY LINE, SURFACE ACOUSTIC WAVE - DESIGN/PERFORMANCE SPECIFICATION										
.xxx .xx		APE		all last	77	7-11-0	9	SIZE	0	58	69		G NO. 1950	512-	600		T	REV
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#### **UPDATED 7/1/76**

### ELECTRONICS COMMAND TECHNICAL REQUIREMENTS

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#### PHOTOLITHOGRAPHICALLY PRODUCED ACOUSTIC SURFACE WAVE PULSE COMPRESSION, BAND-PASS AND PHASE-CODED FILTERS

#### 1. SCOPE

1. 1 Scope. This specification covers the requirements for photolithographic and batch fabrication techniques necessary for the low-cost production of acoustic, surface-wave pulse compression, band-pass, and phase-coded filters.

#### 2. APPLICABLE DOCUMENTS

2.1 The following documents, of the issue in effect on date of invitation for bids or request for proposal, form a part of this specification to the extent specified herein.

#### SPECIFICATIONS

#### MILITARY

MIL-C-39012 Connector, Coaxial, Radio Frequency, General Specification For.

#### STANDARDS

#### MILITARY

MIL-STD-105	Sampling Procedures and Tables for Inspection by Attributes.
MIL-STD-130	Identification Marking of US Military Property.
MIL-STD-202	Test Methods for Electronic and Electrical Component Parts.
MIL-STD-883	Test Methods and Procedures for Microelectronics.

(Copies of specifications, standards, drawings, and publications required by suppliers in connection with specific procurement functions should be obtained from the procuring activity or as directed by the contracting officer. Both title and identifying number or symbol should be stipulated when requesting copies.)

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## REQUIREMENTS

3.1 General Description. The filters shall be photolithographically fabricated on lithium niobate or ST quartz substrates.

## 3.2 Processing.

- 3.2.1 Metallization. An aluminum film shall be deposited on the piezo-electric substrates using high vacuum or radio frequency sputtering systems. The resistivity shall be less than 0.5 ohms per square.
- 3.2.1.1 Uniformity of metallization. The absolute thickness of the aluminum film may vary between 1000 and 2000 angstrom (A<sup>O</sup>); the uniformity of the thickness shall be controlled to ± 5 percent.
- 3.2.1.2 Adhesion of metallic film. The adhesion of the aluminum film to the substrate shall remain intact on the surface of the substrate (see 4.6.2).
- 3.2.2 Photoresist application. Photoresist shall be applied to the lithium niobate and ST quartz substrates resulting in a thin uniform coating capable of resolving 2 micron lines.
- 3.2.3 Photolithographic processing. Contact printing (etching), "lift-off" or "wet contact" printing techniques shall be used, whereby photomasks are applied over the photoresist.

## 3.2.4 Visual inspection.

- 3.2.4.1 Wafer. Circuits on the undiced wafer shall be checked using an approved prototype comparison standard to check the sameness of each circuit pattern using a minimum 250X magnification. A minimum of one circuit per wafer or substrate should be examined. A comparison standard is a wafer whose devices meet the specified design and have passed all the electrical tests. This comparison standard will be used as a reference model in order to cull devices with obvious defects in the geometry.
- 3.2.4.2 Filter package (device). The circuit chip shall be examined after placement in package (without cover) for broken wire bonds, dirt, scratches or other circuit imperfections under 20X magnification.
- 3.2.5 Dicing of wafer into circuit chips. When required to separate the multiple identical circuits fabricated on the same wafer, a diamond-tipped precision cutting tool shall be used.
- 3.2.6 Wire bonding. Wire bonding techniques shall be performed so that reliable electrical connections between the surface acoustic wave circuit and the package connectors are made.
- 3.2.7 Device packaging. Packaging and sealing techniques shall be used so that the resultant hermetically sealed filters shall be capable of meeting all the environmental requirements as specified herein.

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3.3 Classes of devices. The required filter type devices are identified as follows:

Devices		Substrate Materials	Center Frequency	
a.	Linear FM Pulse	ST Quartz	150 MHz	
	Compression Filter	Lithium Niobate	150 MHz	
ъ.	Linear Phase Band-Pass	ST Quartz	100 MHz	
	Filter	Lithium Niobate	150 MHz	
c.	Biphase-Coded Tapped	ST Quartz	100 MHz	
	Delay Line Filter	ST Quartz	200 MHz	

- 3.3.1 <u>Linear FM pulse compression filters</u>. In-line configuration shall be used with internal weighting for sidelobe suppression. Conjugate matched filter pairs shall be fabricated from each substrate material and used to demonstrate pulse compression in each case.
- 3.3.2 <u>Linear-phase band-pass filters</u>. Multistrip couplers shall be used on lithium niobate to couple the two apodized transducers which effect the weighted filter response.
- 3.3.3 Biphase-coded tapped delay line filters. Phase-coded tapped delay line filters with center frequencies of 100 and 200 MHz shall use uniform aperture for the phase-coded array. Conjugate matched filter pairs shall be fabricated and used to demonstrate autocorrelation.
  - 3.4 Number of circuit chips per wafer.
  - 3.4.1 Linear-FM pulse compression filters.
- 3.4.1.1 ST quartz. At least 10 circuit chips shall be fabricated on a single piezoelectric wafer.
- 3.4.1.2 Lithium niobate. At least 10 circuit chips shall be fabricated on a single piezoelectric wafer.
  - 3.4.2 Linear-phase band-pass filters.
- 3.4.2.1 ST quartz. At least 15 circuit chips shall be fabricated on a single piezoelectric wafer.
- 3.4.2.2 Lithium niobate. At least 15 circuit chips shall be fabricated on a single piezoelectric wafer
  - 3.4.3 Biphase-coded tapped delay line filters.
- 3.4.3.1 At least 7 circuit chips shall be fabricated on a single piezo-electric ST quartz wafer.

## 3.5 Construction.

- 3.5.1 <u>Connections (external)</u>. The basic filter shall employ two or three parts, depending on the type of filter device with connectors or strip leads. (The precise location should be finalized prior to the confirmatory sample phase.)
- 3.5.1.1 Connectors. When connectors are used with these filter devices, they shall be series SMA and shall conform to the requirements of MIL-C-39012.
- 3.5.1.2 Strip leads (lead integrity). When strip leads are used, they shall show no physical or mechanical damage when tested (see 4.6.4.2).
- 3.5.2 Connections (internal), wire bonding (lead integrity). Gold wire connections of two mil diameter and minimum length, shall show no evidence of loosening or rupturing from the wire bond connection (see 4.6.4.1).
- 3.5.3 <u>Dimensions</u>. The crystal and package size shall meet the maximum dimensions in inches specified in Table I (see 4.6.3).

Table I. Dimensions.

Classes of Devices	Substrate Material	Max. Circuit Chip Size Substrate (Inches) L W T	Max. Filter Package Size (Inches) L W T
Linear-FM Pulse Type Compression Filters	ST Quartz Lithium Niobate	1.00 x 0.200 x 0.050	2.0 x 1.0 x 0.50
Linear Phase Band Pass Filters	ST Quartz Lithium Niobate	1.00 x 0.200 x 0.050	2.0 x 1.0 x 0.50
Biphase-coded Tapped Delay Lines		2.20 x 0.200 x 0.050 2.2 x 0.200 x 0.050	3.0 x 1.0 x 0.50 3.0 x 1.0 x 0.50

- 3.6 Hermetic seal. Each filter shall be back-filled with an inert gas and shall show no evidence of leakage (see 4.6.5).
- 3.7 Thermal shock. Each filter shall show no evidence of mechanical or physical damage and shall exhibit no short circuits (see 4.6.6).
- 3.8 Solderability (strip leads) (when applicable). Strip leads shall be solderable (see 4.6.7).

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- 3.9 Short circuit and open circuit tests. All chips and filter circuit devices, as applicable, shall be checked for no shorted circuits. A continuity check shall be made to determine that no open circuits exist between the external connection and the surface wave circuit.
- 3.10 Electrical characteristics. Filters shall meet the electrical characteristics and tolerances as specified (see 4.6.9).
  - 3. 10. 1 Center frequency of operation.
  - 3. 10. 1. 1 Linear FM pulse compression filters.
    - a. ST Quartz: 150 MHz + 3 MHz,
    - b. Lithium Niobate: 150 MHz + 3 MHz.
  - 3. 10. 1. 2 Linear-phase band-pass filters.
    - a. ST Quartz: 100 MHz + 2 MHz.
    - b. Lithium Niobate: 150 MHz + 3 MHz.
  - 3. 10. 1. 3 Biphase-coded tapped delay line filters.
    - a. ST Quartz: 100 MHz + 2 MHz.
    - b. ST Quartz: 200 MHz + 4 MHz.
  - 3.10.2 Bandwidth (3db).
  - 3.10.2.1 Linear FM pulse compression filters.
    - a. ST Quartz: 50 MHz + 1 MHz.
    - b. Lithium Niobate: 50 MHz + 1 MHz.
  - 3. 10. 2. 2 Linear-phase band-pass filters.
    - a. ST Quartz: 2 MHz + 40 MHz.
    - b. Lithium Niobate: 30 MHz + 0.6 MHz.
  - 3. 10. 2. 3 Biphase-coded tapped delay line filters.
    - a. ST Quartz: 10 MHz + 0.2 MHz (100 MHz) center frequency.
    - b. ST Quartz: 10 MHz + 0.2 MHz (200 MHz) center frequency.
  - 3. 10. 3 Time-delay.
  - 3. 10. 3. 1 Linear FM pulse compression filters (dispersive delay).
    - a. ST Quartz: 2 microsec + 0.02 microsec.
    - b. Lithium Niobate: 2 microsec + 0.01 microsec.

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- 3, 10, 3, 2 Linear-phase band-pass filters (nondispersive delay).
  - ST Quartz: 2 microsec + 0.01 microsec.
  - Lithium Niobate: 2 microsec + 0.01 microsec.
- 3. 10. 3. 3 Biphase-coded tapped delay line filters.
  - ST Quartz: 12.7 microsec (100 MHz)

center frequency.

- ST Quartz: 12.7 microsec (200 MHz) center frequency.
- 3. 10. 4 Time-bandwidth product.
- 3. 10. 4. 1 Linear FM pulse compression filters.
  - ST Quartz: 100:1
  - Lithium Niobate: 100:1
- 3. 10. 4. 2 Linear-phase band-pass filters.
  - ST Quartz: 4:1
  - Lithium Niobate: 60:1
- 3. 10. 4. 3 Biphase-coded tapped delay line filters.
  - a. ST Quartz: 127:1 (100 MHz) center frequency.
  - ST Quartz: 127:1 (200 MHz) center frequency.
- 3. 10.5 Insertion loss. (Insertion loss is to be measured by CW)
- 3. 10. 5. 1 Linear FM pulse compression filters.
  - ST Quartz: 55db + 5 db.
  - Lithium Niobate: 30db + 3db.
- 3. 10. 5. 2 Linear-phase band-pass filters.
  - ST Quartz: 20db + 2db.
  - Lithium Niobate: 15db + 1.5db.
- 3.10.5.3 Biphase-coded tapped delay line filters.

  - ST Quartz: 30db + 3db (100 MHz) center frequency. ST Quartz: 30db + 3db (200 MHz) center frequency.
- 3. 10.6 Time-sidelobe suppression level.

- 3. 10. 6. 1 Pulse compression filters.
  - a. ST Quartz: ≥ -25db.
  - b. Lithium Niobate: ≥-25db.
- 3. 10. 6. 2 Linear-phase band-pass filters.
  - a. ST Quartz: ≥-35db.
  - b. Lithium Niobate: ≥ -35db.
- 3. 10. 6. 3 Biphase-coded tapped delay line filters.
  - a. ST Quartz: ≥ -19db (100 MHz) center frequency.
  - b. ST Quartz: ≥ -19db (200 MHz) center frequency.
- 3.10.7 Feedthrough suppression. The feedthrough suppression shall be greater than -50db for all types of filters. This shall be relative to the Output Signal Level.
- 3. 10. 8 Spurious echo suppression. The spurious echo suppression shall be greater than -35db for all types of filters. Spurious echo refers to the double and triple transit phenomena.
- 3. 10. 9 Voltage standing wave ratio (VSWR). The VSWR shall be less than 1.5:1 for all types of filters over the operating band with a 50 ohm impedance ( $Z_0$ ).
- 3.11 High temperature storage. Filters shall show no evidence of physical or mechanical damage and no electrical short circuits after subjection to a temperature of 75°C (see 4.6.10 and 4.6.8).
- 3.12 Shock (specified pulse). Filters shall show no evidence of mechanical or physical damage and no electrical short circuits (see 4.6.11 and 4.6.8).
- 3.13 Vibration (low frequency). Filters shall show no evidence of mechanical or physical damage and no electrical short circuits (see 4.6.12 and 4.6.8).
- 3. 14 Moisture resistance. Filters shall show no evidence of mechanical or physical damage and no short circuits. All of the electrical characteristics (final) shall be met in accordance with the limits provided in the government approved contractor's plan (see 4.6.13 and 4.6.8).
- 3.15 <u>Life.</u> After 500 hours of life, the filters shall show no evidence of mechanical or physical damage; and shall meet all of the electrical characteristics (final) in accordance with the limits provided in the government approved contractor's plan (see 4.6, 14).
- 3. 16 Marking. All markings shall remain legible throughout processing and testing in accordance with MIL-STD-130.

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- 3. 16. 1 Wafer. Identification shall be provided on each chip on the substrate to indicate the manufacturer; crystal type; batch or lot; crystal cut and orientation.
- 3. 16.2 Filter. Identification of the type of device along with a descriptive identifying number indicating operating frequency and bandwidth.
- 3.17 Workmanship. Chips and filters shall be processed in such a manner as to be uniform in quality and shall be free from cracks or other defects that will affect life, serviceability and appearance.

#### 4. QUALITY ASSURANCE PROVISIONS

- 4.1 Responsibility for inspection. The contractor is responsible for the performance of all inspections specified herein. The contractor may utilize his own facilities or any commercial laboratory acceptable to the government. Tests shall be performed under the supervision of a government representative. Inspection records of the examinations and tests shall be kept complete and available to the government as specified in the contract.
  - 4.2 Classification of inspection. Inspection shall be classified as follows:
    - First article inspection (does not include preparation for delivery) (see 4.4).
    - b. Quality conformance inspection.
- 4.3 Inspection condition. Unless otherwise specified herein, all inspections shall be in accordance with the test conditions specified in general requirement of MIL-STD-202.
- 4.4 First article inspections. This inspection shall consist of all the tests in tables III and IV including the use of the contractor submitted government-approved plan on test methods and procedures for determining the electrical characteristics and the electrical characteristics final limits. No failures in excess of those indicated shall be permitted.
  - 4.4.1 Sample.
  - 4.4.1.1 Wafers. (See table II.)
- 4.4.1.2 Circuit chips. The wafers shall be acceded into discrete circuit chips with the exclusion of one wafer for each type of substrate and shall be submitted for inspection as indicated in table II.
  - 4.4.2 Test routine.

- 4.4.2.1 Wafer submission. Sample units shall be subjected to the inspection specified in table III, in the order shown prior to dicing into discrete circuit devices. Ten (10) each of the first four categories in table II shall be tested and seven (7) each of the last two categories (ST Quartz 100 and 200 MHz, respectively). There shall be no failures.
- 4.4.2.2 Circuit devices. Eighty-four (84) operable filter circuit devices shall be submitted to the inspections specified in table IV, in the order shown. Twelve sample units shall be used for group II inspection only. The remaining units shall be subjected to group I inspection and subdivided into the remaining groups for their particular examination or test. Forty-two sample units of each substrate material (100 MHZ and 200 MHZ) of the operable biphase-coded tapped delay line filter circuit devices shall be submitted to the inspections specified in Table IV, in the order shown, using 36 sample units for group I; 6 sample units for group II; 9 sample units for groups III and IV; 6 sample units for group V, and 12 sample units for group VI. The number of defects shall remain as indicated for each group excluding group VI, where only 1 defect shall be allowed.

Table II. Class of devices with minimum number of wafers, circuits per wafer and total number of operable filter circuit devices.

Class of devices	Minimum Nr. of wafers	Minimum Nr. of circuits per wafer	Operable filter circuit devices
Linear FM pulse	10-ST Quartz	10	84
compression filters	10-Lithium Niobate	10	84
Linear band-pass	10-ST Quartz	15	84
filters	10-Lithium Niobate	15	84
Biphase-coded tapped delay line filters	7-ST Quartz (freq 100 MHz)	7	42 84
	7-ST Quartz (freq 200 MHz)	7	42)

Table III. First article inspection of each type of wafer.

Examination or test	R equirement paragraph	Test paragraph
Marking	3. 16. 1	
Visual check (using a standard for reference under magnification) (250X)	3. 2. 4. 1 3. 17	4. 6. 1. 1
Adhesion of metallic film	3, 2, 1, 2	4.6.2
Short circuit	3.9	4.6.8

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Table IV. First article inspection of each class of filter devices (circuit devices).

Examination or test	Requirement paragraph	Test paragraph	Num! Samples	Defects
Group I Visual check (20X magnification) Marking Dimensions Strip lead (lead integrity) Internal wire bonding (lead integrity) Electrical characteristics	3. 2. 4. 2 3. 17 3. 16. 2 3. 5. 3 3. 5. 1. 2 3. 5. 2	4. 6. 1. 2 4. 6. 3 4. 6. 4. 2 4. 6. 4. 1 4. 6. 9	72	\right\{\right\} \cdot \
Group II Solderability (when applicable)	3.8	4.6.7	12	0
Group III High temperature storage Electrical characteristics Center frequency	3. 11 3. 10 3. 10. I thru 3. 10. 1. 3, incl.	4.6.10 4.6.9	18	} 。
Insertion loss	3. 10. 5 thru 3. 10. 5. 3, incl.		)	)
Group IV Life Short circuit test Electrical characteristics (Final)	3. 15 3. 9 3. 10	4.6.14 4.6.8 4.6.9	} 18	} 1
Group V Hermetic seal Short circuit test	3.6 3.9	4.6.5 4.6.8	} 12	} •
Group VI Vibration Short circuit test Shock Short circuit test Thermal shock (10 cycles) Short circuit test Moisture resistance Short circuit test Electrical characteristics (Final)	3. 13 3. 9 3. 12 3. 9 3. 7 3. 9 3. 14 3. 9 3. 10	4. 6. 12 4. 6. 8 4. 6. 11 4. 6. 8 4. 6. 6 4. 6. 8 4. 6. 13 4. 6. 8 4. 6. 9	}24	} 2

## 4.4.3 Defectives.

- 4.4.3.1 Wafers. No defects shall be allowed in table III; any defects shall be cause for refusal to grant first article inspection approval.
- 4.4.3.2 Filter circuit devices. Defects in excess of those allowed in table IV shall be cause for refusal to grant first article inspection approval.
  - 4.5 Quality conformance inspection.
- 4.5.1 Inspection of product for delivery. Inspection of products for delivery shall consist of groups A, B and C inspection.
- 4.5.1.1 Inspection lot. An inspection lot shall be as specified in MIL-STD-105 and applies to each of the six types of wafers or filter circuit devices, as applicable.
- 4.5.1.2 Group A inspection. Group A inspection shall consist of the examinations and tests in table V in the order shown. Subgroup I examination and tests are on wafers and subgroup II on the filter circuit devices.

Table V. Group A inspection.

Examination or test	Requirement paragraph	Method paragraph
Subgroup I		
Marking	3, 16, 1	
Adhesion of metallic film	3, 2, 1, 2	4.6.2
Short circuit	3.9	4.6.8
Visual Inspection Subgroup II	3. 2. 4. 1, 3, 17	4.6.1
Visual (magnification 20X)	3. 2. 4. 2, 3. 17	4. 6. 1. 2
Marking	3, 16, 2	
Hermetic seal	3.6	4.6.5
Strip lead (lead integrity)	3, 5, 1, 2	4.6.4.2
<pre>Internal wire bonding (lead   integrity)</pre>		4. 6. 4. 1

- 4.5.1.2.1 Sampling plan. 100 percent inspection shall be performed on subgroup I on the wafers which shall then be diced into discrete circuits; and subgroup II inspection shall be performed using 100 percent inspection.
- 4.5.1.2.2 Rejected samples. If during the 100 percent inspection of subgroup I, screening indicated that over 30 percent of the total filter circuit devices on all wafers (undiced) be discarded, the lot (wafers) shall be rejected.
- 4.5.1.3 Group B Inspection. Group B inspection shall consist of the tests specified in table VI, in the order shown and shall be made on sample units which have been subjected to and have passed group A, subgroup II inspection.

Table VI. Group B inspection.

Examination or test	Requirement paragraph	Method paragraph
Eletrical characteristics		
Center frequency of operation Bandwidth Time delay Time-bandwidth product Insertion loss Time-sidelobe suppression level Feedthrough suppression Spurious echo suppression Voltage standing wave ratio (VSWR)	3. 10. 1, 3. 10. 1. 1, 3. 10. 1. 2, 3. 10. 1. 3 3. 10. 2, 3. 10. 2. 1, 3. 10. 2. 2, 3. 10. 2. 3 3. 10. 3, 3. 10. 3. 1, 3. 10. 3. 2, 3. 10. 3. 3 3. 10. 4, 3. 10. 4. 1, 3. 10. 4. 2, 3. 10. 4. 3 3. 10. 5, 3. 10. 5. 1, 3. 10. 5. 2, 3. 10. 5. 3 3. 10. 6, 3. 10. 6. 1, 3. 10. 6. 2, 3. 10. 6. 3  3. 10. 7 3. 10. 8 3. 10. 9	4.6.9 4.6.9 4.6.9 4.6.9

- 4.5.1.3.1 Sampling plan. Sampling plan shall be in accordance with special procedures for small sample inspection of MIL-STD-105. The AQL shall be 6.5 percent defective using inspection level S-4.
- 4.5.1.3.2 Test routine. The samples specified in 4.5.1.3 shall be subjected to the tests in table VI in the order shown.
- 4.5.1.3.3 Rejected lots. If an inspection lot is rejected, the contractor may withdraw the particular lot once, screen out defectives, and reinspect once. Such lots shall be kept separate from new lots and shall be clearly identified as reinspected lots. Rejected lots shall be reinspected using tightened inspection.
- 4.5.1.4 Group C inspection. Group C inspection shall consist of the tests specified in table VII, in the order shown. Group C inspection shall be made on sample units selected from inspection lots which have passed groups A and B inspections.
- 4. 5. 1. 4. 1 Sampling plan. Six sample units of each type of filter circuit device shall be selected for each of subgroups 1, 2 and 3 at random from each lot as specified in 4. 5. 1. 1.
- 4.5.1.4.1.1 Test routine. The samples selected in accordance with 4.5.1.3 shall be subjected to the tests shown in table VII. Not more than one defect shall be allowed for a single group of six samples.
- 4.5.1.4.2 Disposition of samples. Filter circuit devices subjected to group C inspection shall not be delivered on the contract or order. Samples emanating from lots which have passed groups A, B and C inspection may be delivered on the contract.

Table VII. Group C inspection.

Examination or test	Requirement paragraph	Test paragraph
Group I		
High temperature storage	3.11	4.6.10
Short circuit	3.9	4.6.8
Hermetic seal	3.6	4.6.5
Short circuit	3.9	4.6.8
Subgroup II		
Solderability (strip leads) (when applicable)	3.8	4.6.7
Life	3. 15	4. 6. 14
Electrical characteristics (final)	3. 10	4.6.9
Subgroup III		
Vibration	3, 13	4. 6. 12
Short circuit	3.9	4.6.8
Shock	3. 12	4. 6. 11
Short circuit	3.9	4.6.8
Thermal shock (10 cycles)	3. 7	4.6.6
Short circuit	3.9	4.6.8
Moisture resistance	3. 14	4, 6, 13
Electrical characteristics (final)	3. 10	4.6.9

<sup>4.5.1.4.3</sup> Noncompliance. If a sample fails to pass group C inspection, the contractor shall take corrective action on the materials or processes, or both, as warranted, and on all units of product which can be corrected and which were manufactured under essentially the same materials, processes, and so forth, and which are considered subject to the same failure. Acceptance of the product shall be discontinued until corrective action, acceptable to the government, has been taken. After the corrective action has been taken, group C inspection shall be repeated on additional sample units (all inspections or the inspection which the original sample failed at the option of the government). Groups A and B inspection may be reinstituted; however, final acceptance shall be withheld until the group C reinspection has shown that the corrective action was successful. In the event of failure, action shall be furnished to the contracting officer.

#### 4.6 Methods of examination and test.

## 4.6.1 Visual.

4.6.1.1 Wafer (see 3.2.4.1 and 3.17). A government approved comparison standard shall be utilized using 1000X magnification.

#### SCS-476

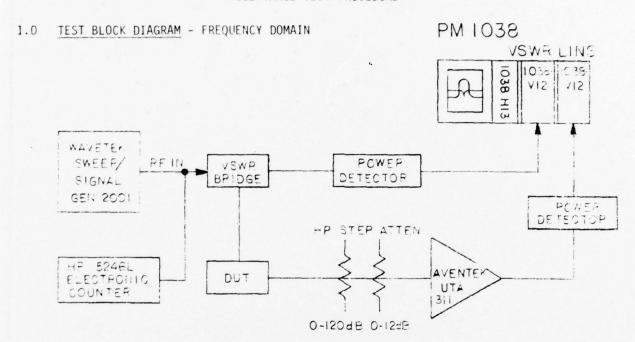
- 4.6.1.2 Filter device (see 3.2.4.2 and 3.17). An examination for circuit inspections shall be performed under 20X magnification.
- 4.6.2 Adhesion of metallic film (see 3.2.1.2). A one-inch strip of pressure sensitive cellophane tape, conforming to type I, class A of Federal Specification L-T-90, shall be applied to the metallized surface, adhesion side down, employing firm hand pressure. The tape shall then be removed with one abrupt motion, and the adhesive side examined for detached particles of metallic film.
- 4.6.3 <u>Dimensions (see 3.5.3)</u>. Dimensions shall be measured using a micrometer.
- 4.6.4 Lead integrity (internal wire bonding and strip lead). Filter devices shall be tested in accordance with method 2011 of MIL-STD-883, method 4.6.4.1 or 4.6.4.2 as applicable.
  - 4. 6. 4. 1 Internal wire bonding. The following details shall apply:
    - a. Test condition D Tension.
    - b. Weight to be attached to lead 2 grams.
    - c. Length of time weight is to be attached A minimum of 10 seconds.
  - 4. 6. 4. 1. 2 Strip lead. Test condition A Tension.
- 4.6.5 Hermetic seal (see 3.6). Filter devices shall be tested in accordance with method 112B, MIL-STD-202. The following details shall apply:
  - a. Test condition C.
  - b. Leak-rate sensitivity 10<sup>-8</sup> atm cc/sec.
  - c. Procedure IV, test for gross leaks using test condition A.
- 4.6.6 Thermal shock (see 3.7). Filter devices shall be tested in accordance with method 107, MIL-STD-202, test condition A (10 cycles).
- 4.6.7 Solderability (strip leads only, when applicable) (see 3.8). Filter devices shall be tested in accordance with method 2003 of MIL-STD-883. Each strip lead on a filter device shall be tested.
- 4.6.8 Short circuit and open circuit tests. All chips and filter circuit devices, as applicable, shall be tested for short circuits by any suitable means including the open circuit test between the external connection and the surface wave circuit.
- 4.6.9 Electrical characteristics (see 3.10). The government approved contractor's plan of electrical test methods, procedures and limits of degradation (electrical characteristics final) shall be used.
- 4.6.10 High temperature storage (see 3.11 and 3.9). Filter devices shall be tested in accordance with method 1008 of MIL-STD-883. The following details shall apply.

- Test condition A (75°C).
- b. Test duration 72 hours.
- c. At the end of the exposure period, the devices shall be allowed to stabilize at room temperature and the filter device tested for short circuits.
- 4.6.11 Shock (specified pulse). Filter devices shall be tested in accordance with method 213 of MIL-STD-202. The following details shall apply:
  - Test condition I
  - Method of mounting Filter devices shall be rigidly mounted by their normal mounting means.
- 4.6.12 Vibration (low frequency) (see 3.13). Filters shall be tested in accordance with method 201 of MIL-STD-202. The filters shall be rigidly mounted by their normal mounting means.
- 4.6.13 Moisture resistance (see 3.14). Filters shall be tested in accordance with method 106D of MIL-STD-202. The following details shall apply:
  - Polarizing voltage 50 Vdc
  - Final measurements Before measurements, all units shall be removed from the test chamber and stabilized at room temperature. The filters shall be visually inspected and all electrical characteristics shall be performed and degradation limits shall be as indicated in the government approved contractor's plan.
- 4.6.14 Life (at elevated ambient temperature) (see 3.15). Filters shall be tested in accordance with method 108 in MIL-STD-202. The following details and exceptions shall apply.
  - Mounting Normal mounting means as used in a system or sub-system.
  - Distance between filter devices 6 inches.
  - Test temperature and tolerance 85°C + 10°C.
  - Final measurements Before measurements are made, all units shall be removed from the test chamber and stabilized at room temperature. All electrical characteristics shall be performed and degradation limits shall be as indicated in the government approved contractor's plan.
  - PREPARATION FOR DELIVERY.

The substrates, circuit chips and filters shall be in accordance with best commercial practices.

REV **JNS** LTR DESCRIPTION DATE APPROVED AUTHORITY DDT 82701 1950512-800 SHEET 1 2 3 4 5 6 7 8 9 10 11 12 13 14 15 16 REV STATUS LEVEL OF SHEETS REV UNLESS OTHERWISE | CONTRACT: HUGHES AIRCRAFT COMPANY HUGHES SPECIFIED FULLERTON, CALIFORNIA **DIMENSIONS ARE** IN INCHES AND PER ANSI Y14.5 D.CRISWELL 18-18-10 BANDPASS FILTER, TEST ACCEPTANCE PROCEDURE 10-10-17 XXX. FSCM NO. DWG NO. SIZE REV XX. 16/78 1950512-800 ISSUED ANGLES SCALE WT 3-19 SHEET 1 OF 15 D14-338 GS 1/77

## ACCEPTANCE TEST PROCEDURE

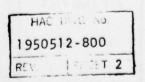


BLOCK DIAGRAM FOR MEASUREMENT OF VOLTAGE STANDING WAVE RATIO AND INSERTION LOSS IN THE FREQUENCY DOMAIN

#### 2.0 TEST EQUIPMENT SETUP - FREQUENCY DOMAIN

10

- 2.1 Connect Horizontal output of the Wavetek 2001 to Horizontal input of PM 1038.
- 2.2 Connect RF output of the Wavetek 2001 to RF input of VSWR Bridge.
- 2.3 Connect the Channel A Power Detector of the PM 1038 to Reflected RF Output on the VSWR Bridge.
- 2.4 Connect Device under test on the VSWR Bridge to the input port of the test fixture.
- 2.5 Connect the output port of the test fixture to the two HP Step Attenuators.
- 2.6 Connect the two HP Step Attenuators to the input of the Aventek UTA-311 amplifier.



- 2.7 Connect the output of the Aventek UTA-311 amplifier to the Channel B Power Detector of the PM 1038.
- 2.8 Connect the RF output of the 2001 to the input of HP 5246L Electronic Counter.

## 3.0 OPERATING LEVELS AND CALIBRATION - FREQUENCY DOMAIN

- 3.1 Connect the HP Step Attenuators to Device Under Test on the VSWR Bridge.
- 3.2 Adjust output of the 2001 for maximum output. Place Mode switch to S/S. Select desired frequency band with the Band switch. Set TRIG/RECUR switch to RECUR. Put ALC switch into INT position. Select sweep width with START/STOP knobs. Set SWEEP TIME to 1-.1 position. Set all marker buttons to OUT position.
- 3.3 Set OFFSET dBm/dB selector to the Nominal Insertion Loss of the device to be tested on Channel B of PM 1038. Polarity switch out, Smooth switch out. Push INPUT dB switch in, push 10 dB/DIV switch in. Set REF LINE to CL.
- 3.4 Set HP Attenuators to the same setting as on the OFFSET dBm/dB selector.
- 3.5 Adjust the trace to center line on PM 1038 with the REFERENCE knob.
- 3.6 Check dB range by changing the HP Step Attenuators in 10 dB steps for a 10 dB change on the PM 1038. To prevent saturation of the UTA-311 amplifier add more attenuation on the HP Step Attenuators as needed.
- 3.7 Select greater sensitivity on the dB/DIV of the PM 1038 centering the reference each time. Select ACESS MEMORY, slow down the SWEEP TIME on the 2001. Depress the PRESS TO STORE button on the PM 1038 for at least one sweep of the trace. Push the MEMORY button to make sure the trace you just saw is in memory. Then select INPUT MINUS MEMORY. The center line is now equal to dB on the OFFSET dBm/dB selector.
- 3.8 Remove from the HP Step Attenuators the same amount of dB selected on the OFFSET dBm/dB on the PM 1038.
- 3.9 Reconnect the attenuators and VSWR Bridge to the test fixture.
- 3.10 Select a resistive load to match the VSWR required for the device being tested and place in the test fixture.
- 3.11 Set OFFSET dBm/dB to 00.0 on Channel A of the PM 1038. Set Polarity and smooth switch out. Push INPUT dB switch in. Depress 10dB/DIV in. Set REF LINE TO C.L. Adjust trace to the center line on the PM 1038 with the REFERENCE knob. Select greater sensitivity on dB/DIV centering the reference each time. Select ACESS MEMORY. Slow SWEEP TIME on the 2001 down. Depress the PRESS TO STORE button on the PM 1038 for at least one sweep of the trace. Push the MEMORY button to make sure the trace you just saw is in memory. Then select INPUT MINUS MEMORY. Center line is now equal to the VSWR desired.

## 4.0 CALIBRATION OF TIME DOMAIN TEST SETUP

- 4.1 Set the HP608D signal generator for proper center frequency of device under test.
- 4.2 Set amplitude output for maximum RF output.
- 4.3 Set the EH 139B pulse generator for a 8 KHz repetition rate,  $1\mu$  sec Pulse Width with an amplitude of 2v peak to peak and an offset of -1v.
- 4.4 For BPQ, BPLN, PCQ, PCLN plugin a good device into the test fixture and fine adjust the pulse width, ramp rate (rise and fall), offset and amplitude to obtain peak output of the device. All measurements made on the BPQ, BPLN, PCQ, PCLN are made with reference to the peak of the response.
- 4.5 For TDL-100 and TDL-200 replace the D.U.T. (device under test) with a straight through connection. Fine adjust the pulse width, Ramp rate (rise and fall), Offset and amplitude making sure that each bit from the TDR (reverse coded line) is of equal amplitude. When this is done use the peak of this amplitude as a reference for making the insertion loss measurement of the delay line.

## 5.0 TEST EQUIPMENT SETUP - TIME DOMAIN

- 5.1 Connect RF output of the HP608D signal generator to the HP 5246L counter.
- 5.2 Connect TRIG OUT of the EH 139B Pulse generator to Ext. TRGIN on the HP138A OSCILLOSCOPE.
- 5.3 Connect OUT on the EH139B Pulse generator to SW on RF switch #1 and RF switch #2.
- 5.4 Connect RF output of the HP608D signal generator to IN on RF switch #1.
- 5.5 Connect OUT on RF switch #1 to IN on RF switch #2.
- 5.6 For PCQ and PCLN go to step 11. For BPQ and BPLN go to step 16. For TDL-100 and TDL-200 continue to next step.
- 5.7 Connect OUT of RF switch #2 to IN of UTA311 amplifier #1.
- 5.8 Connect OUT of UTA311 amplifier #1 to input of the TDR (reverse coded delay line).
- 5.9 Connect output of the TDR to IN of UTA311 amplifier #2.
- 5.10 For TDL-100 and TDL-200 go to step 13.
- 5.11 For PCQ and PCLN connect OUT of RF switch #2 to input of PELN (pulse expansion line).
- 5.12 Connect output of PELIV to IN of UTA311 amplifier #2.

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- 5.13 Connect OUT of UTA311 amplifier #2 to a 10dB pad.
- 5.14 Connect 10dB pad to IN of UTA311 amplifier #3.
- 5.15 For TDL-100, TDL-200, PCQ and PCLN go to step 17.
- 5.16 For BPQ and BPLN connect OUT of RF switch #2 to IN of UTA311 amplifier #3.
- 5.17 Connect OUT of UTA311 amplifier to a 10dB pad.
- 5.18 Connect 10dB pad to IN of AV9M amplifier.
- 5.19 Connect OUT of AV9M amplifier to input of D.U.T. (device under test).
- 5.20 Connect output of D.U.T. to HP355D step attenuator.
- 5.21 Connect HP355D step attenuator to HP355C step attenuator.
- 5.22 Connect HP355C step attenuator to IN of UTA311 amplifier #4.
- 5.23 Connect OUT of UTA311 amplifier #4 to channel A of HP138A oscilloscope.

## 6.0 MEASUREMENT PROCEDURE

Insertion Loss For the BPQ, BPLN, PCQ and PCLN insertion loss is measured in the frequency domain. With the frequency domain equipment setup and calibrated, for the device under test set the peak of the response to the reference line by adjusting the OFFSET dBm/dB selectors on channel B of the PM 1038. The insertion loss can be directly read from the OFFSET dBm/dB selector. Record this value.

Insertion loss for the TDL-100's and TDL-200's is measured in the time domain. See Figure 3.

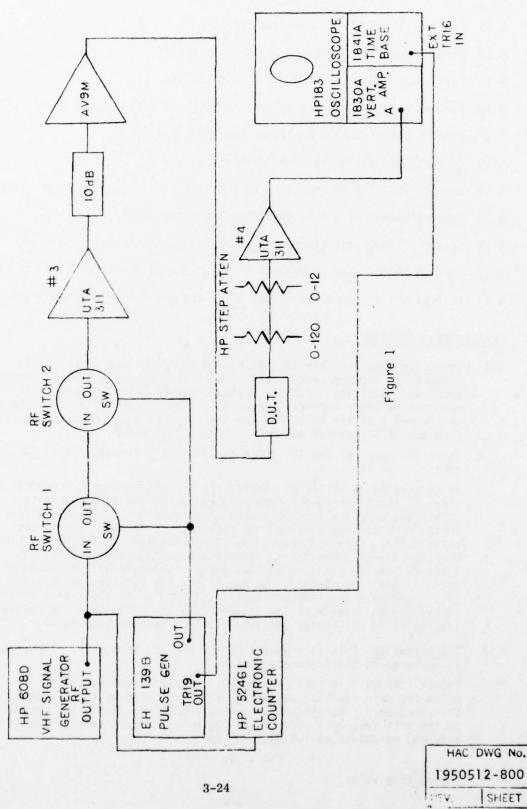
By connecting an RF barrel connector (straight through connection) (in place of the device under test) and adjusting the step attenuators (HP355C&D) and oscilloscope preamplifier gain for full scale deflection on the oscilloscope display, the reference or maximum signal level is established. Note and record the Step Attenuator (HP335C&D) settings. When the barrel connector is removed and the device under test is installed in its place, a smaller signal amplitude will be noted on the oscilloscope presentation. Do not change the oscilloscope preamplifier gain. Decrease the step attenuator settings until the signal amplitude is exactly full scale on the oscilloscope presentation. The change (decrease) in attenuator settings is the Insertion Loss in dB.

6.2 3dB Bandwidth This is measured on the BPQ and BPLN only. The bandwidth is measured in the frequency domain.

Select 1dB/DIV. Set REF LINE to +3. Rotate frequency control to -3dB below the main response on the low frequency side of the passband. Record this frequency. Rotate the frequency control to -3dB below the main response on the high frequency side of the passband. Record this frequency. Determine the bandwidth as follows:

fhi - flo = BW

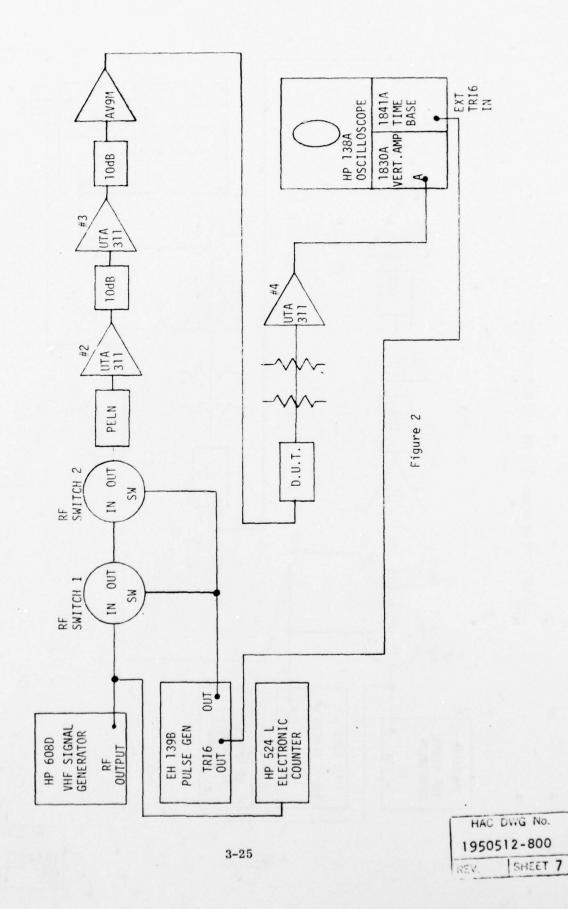
Record this value.



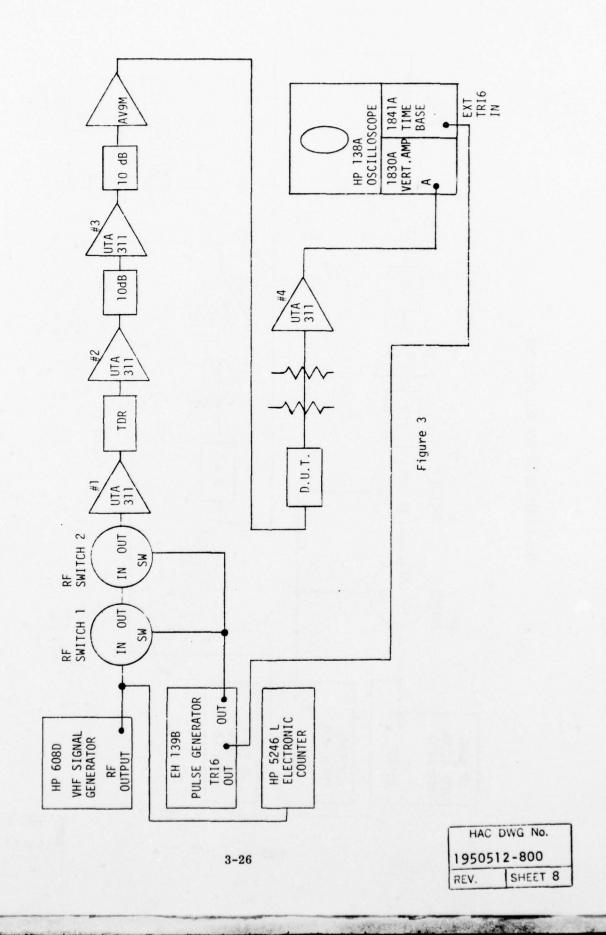
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SHEET

TIME DOMAIN SETUP FOR PCQ AND PCLN



TIME DOMAIN SETUP FOR TDL-100 AND TDL-200



TRI9 IN 1841A TIME BASE EXT HP 138A OSCILLOSCOPE 1830A VERT.AMP 5 0 AV9M TEST SETUP FOR MEASURING CENTER FREQUENCY OF TDL-100 AND TDL-200 10 dB Figure 4 UTA 311 RF SWITCH 2 TUO MI SW RF SWITCH 1 IN OUT MS PULSE GENERATOR
TR19
OUT HP 5246 L ELECTRONIC COUNTER VHF SIGNAL GENERATOR EH 139B HP 608D RF OUTPUT HAC DWG No. 1950512-800 3-27 SHEET 9 REV.

TIME DOMAIN RESPONSES BPQ, BPLN, PCQ, PCLN

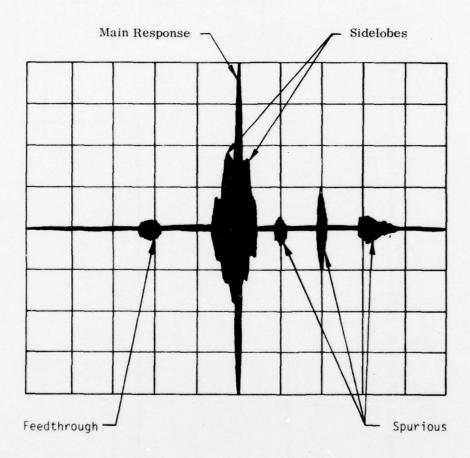


Figure 5

# TIME DOMAIN RESPONSES TDL-100, TDL-200

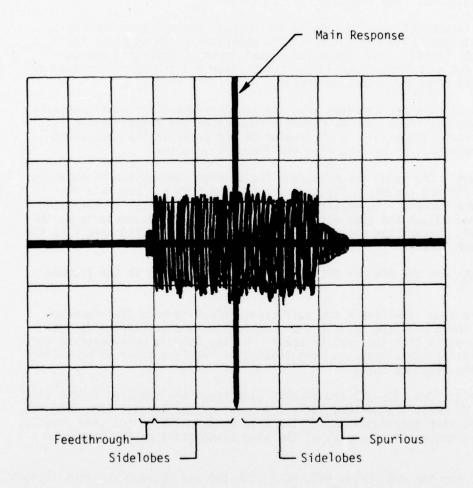


Figure 6

6.3 <u>Center Frequency</u> For the BPQ and BPLN. Determine center frequency using the frequency measurements taken to determine the bandwidth and use this formula:

$$\frac{fhi + flo}{2} = fo$$

Center frequency for the TDL-100 and TDL-200 is measured with the time domain equipment. See Figure 4.

The test is accomplished by summing the output response from the device under test (DUT) with the output of the generator which supplies the original RF signal. When these two signal inputs are exactly the same, but  $180^{\rm O}$  out of phase, cancellation takes place and the precise frequency can be read from the signal generator.

When both signals are inserted into the scope preamplifier simultaneously at the same amplitude and the center frequency of the signal source is adjusted for optimum null in the center of the presentation, the exact center frequency can be read from the frequency counter.

- Feedthrough The setup for measuring feedthrough suppression is shown in Figure 1 for BPQ and BPLN, Figure 2 for PCQ and PCLN and Figure 3 for TDL-100 and TDL-200. To measure feedthrough note the level of the feedthrough and adjust the step attenuators until the main response is at the same level. Record the amount of dB change of the step attenuators as the feedthrough level.
- 6.5 Side Lobes For the BPQ and BPLN side lobes are measured in the frequency domain.

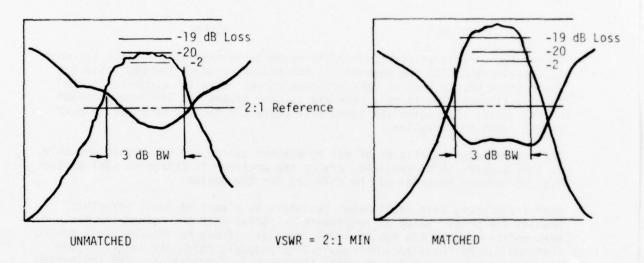
To measure side lobe levels add sufficient offset to move the response curve to the top of the reticle and read leading and trailing side lobe levels directly from the reticle scale. A side lobe is considered to exist when a distinct peak occurs on the leading or trailing slope or on either side of the response curve.

For the PCQ, PCLN, TDL-100 and TDL-200 side lobes are measured in the time domain. To measure side lobes note the level of the largest side lobe and adjust the step attenuators until the main response is at the same level. Record the amount of dB change of the step attenuators as the side lobe level.

- 6.6 Spurious For the BPQ, BPLN, PCQ, PCLN, TDL-100 and TDL-200 spurious signals are measured in the time domain. To measure the spurious signals note the level of the largest spurious signals and adjust the step attenuators until the main response is at the same level. Record the amount of dB change of the step attenuators as the spurious level.
- 6.7 VSWR: For the BPQ, BPLN, PCQ, PCLN, TDL-100 and TDL-200 the VSWR is measured in the frequency domain. With the PM 1038 calibrated to the desired VSWR check both the input part and the output part to verify the specified VSWR.

APPENDIX: Tuning Bandpass Filters and Pulse Compression Filters (applies to all types of test equipment setups)

The center frequency of SAW devices is determined by the transducer design and is fixed by the metalized pattern deposited on the surface of the crystal. Tuning the packaged devices does not significantly alter the center frequency although it may skew the response curve and effect the 3dB bandwidth. The major purpose for tuning a SAW device is to minimize the input and output VSWR or "match" the SAW device to external circuit element. A device is "matched" or tuned when the return loss is minimized within the 3dB bandwidth unless otherwise specified. The sketches below illustrate a matched and an unmatched filter response.

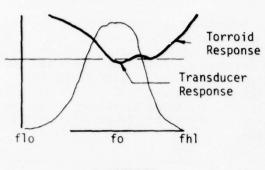


Thus, tuning is usually done by monitoring the return loss. Tuning is electrically accomplished by the addition of series or parallel inductance to compensate for the inherent capacitance of the metalized pattern. It is physically accomplished by expanding or compressing turns on a torroidal powdered iron core using a pair of tweezers. When the desired response is achieved, the core and the turns on it are held in position by the addition of RTV compound. The RTV compound if used to excess will also influence the tuning. So also will the orientation of the core and the proximity of a metal cover.

The procedure then is to install the unit to be tuned into a properly calibrated test setup and expand or compress the turns on the core whose terminals are connected to the SWR Bridge so that the VSWR response is centered on the 3dB bandwidth of the device.

If the sweep width of the generator is set very wide compared to the bandpass of the device to be tested, it will be noted that the VSWR response is a composite of two curves. One curve is the resonance of the transducer. This is usually approximately equal to the 3dB bandwidth of the device being tested. The second curve is the response of the torroid and its parasitic

capacitance. This is usually quite broad. The illustration below shows this phenomena.



flo to th1

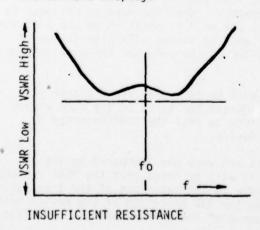
UNTUNED

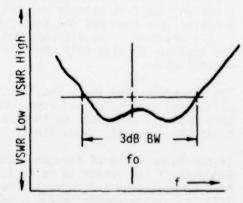
TUNED

Tuning the torroid shifts the torroid response in frequency so that its peak is superimposed with the peak of the transducer response thereby producing the minimum return loss or VSWR response curve. Usually, compressing the turns will cause the torroid response to move toward the low frequency end of the sweep. Spreading the turns will cause the torroid response to move in the opposite direction.

The use of large quantities of RTV to achieve tuning has not proven workable. If this appears to be required, advise the engineer in charge so that another type of torroid material can be selected for the device.

Most transducers have small metal resistors as a part of their structure. Usually the proper value of resistance in series with the transducer has been established at the design level, however, it may be discovered in tuning that additional resistance is required to properly match the device. This can be caused by variation of metal thickness in fabrication. The indication that more resistance is required occurs when the VSWR response curve is properly tuned frequencywise (both responses superimposed) but the VSWR is too great over the 3dB bandwidth. The illustration below shows the incorrect and correct display.





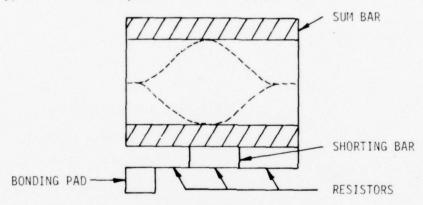
CORRECT RESISTANCE

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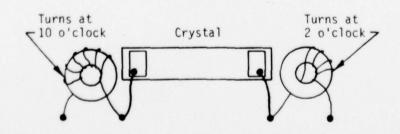
The incorrect condition above can be remedied by the addition of a section of resistance in the transducer, however, a slight detuning may be noted as the resistor will add a small amount of series inductance. This additional inductance can usually be tuned out by spreading the turns on the torroid.

Each transducer has several sections of resistors which are shorted out by thin metal shorts. Resistance is added by scribing through the shorting bars. This is a delicate operation. Consult your supervisor for approval and technique before attemption to add resistance. The sketch below shows a typical transducer pattern with resistors.



The addition of resistors will also increase insertion loss and can be used for this purpose. In general the VSWR will be improved by adding resistance so that increasing insertion loss by this method results in a better VSWR. On the other hand improving VSWR by this method may increase insertion loss beyond specification. In any case advise your supervisors if the addition of resistance is required so he can establish the reason for it and can modify metal thickness or whatever may be the cause.

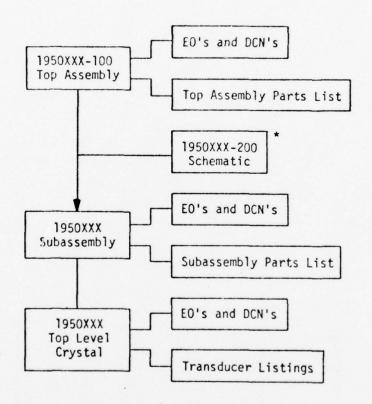
The orientation of the turns on the torroidal cores sometimes influences feedthrough suppression. In those cases where this has appeared as a problem it has been found that the greatest feedthrough suppression occurs when the turns are positioned away from the crystal as shown below:



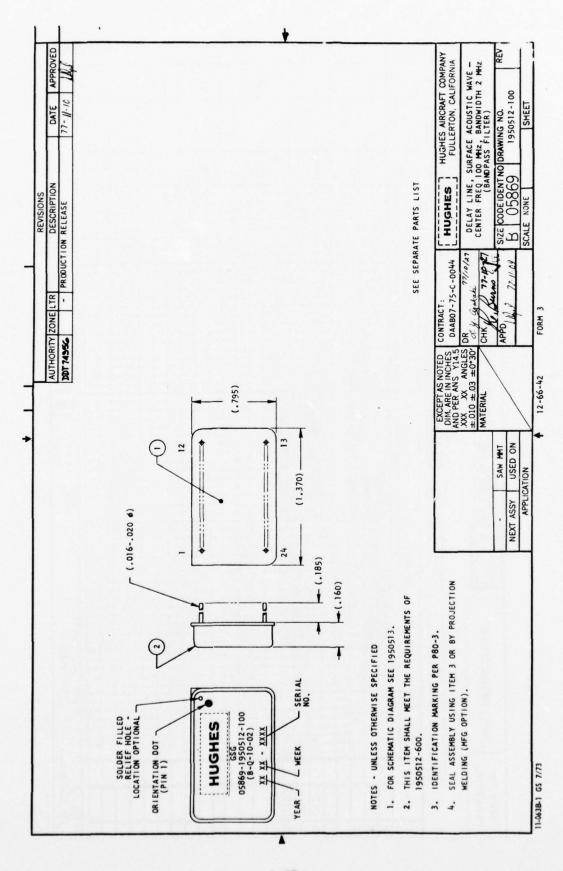
3-33 (3-34 BLANK)

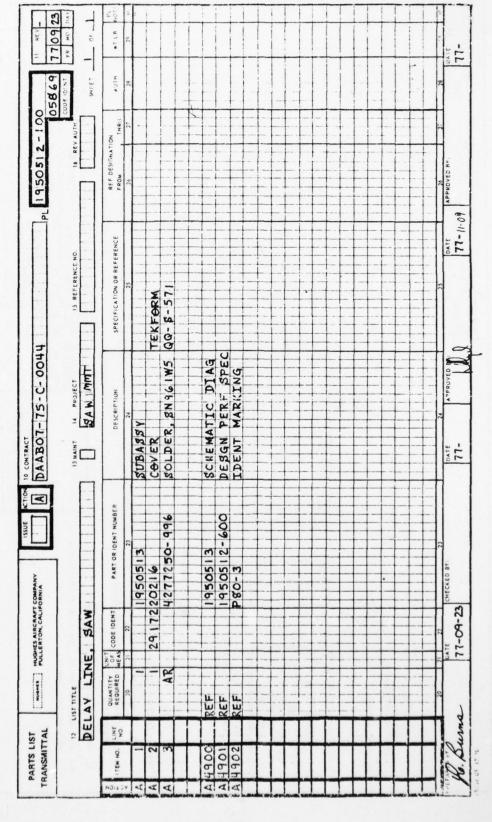
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## DRAWING HEIRARCHY SCHEMATIC

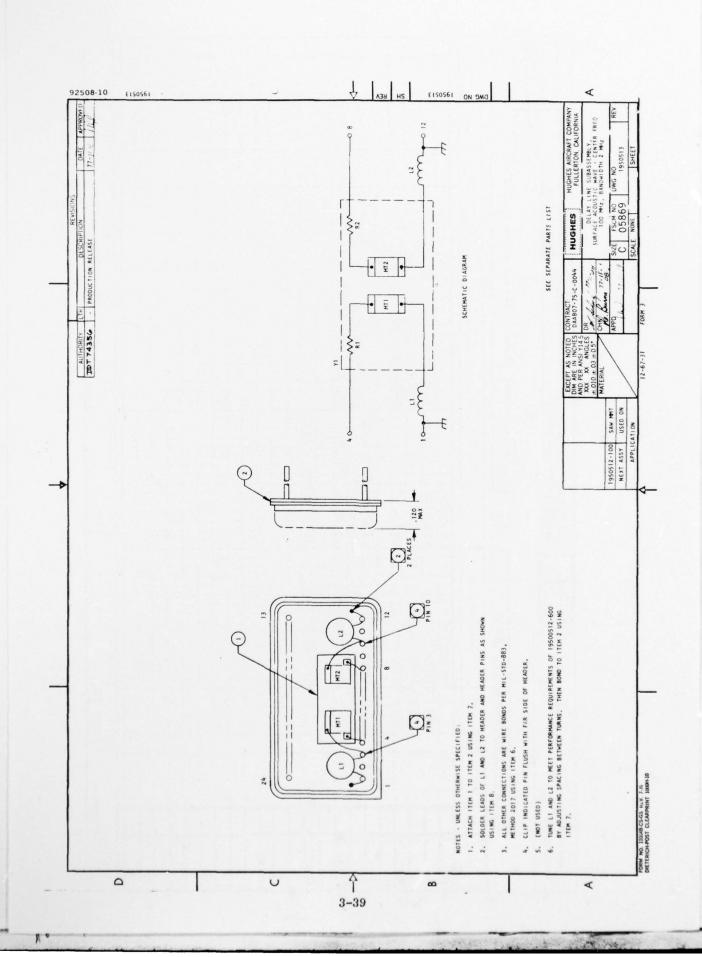


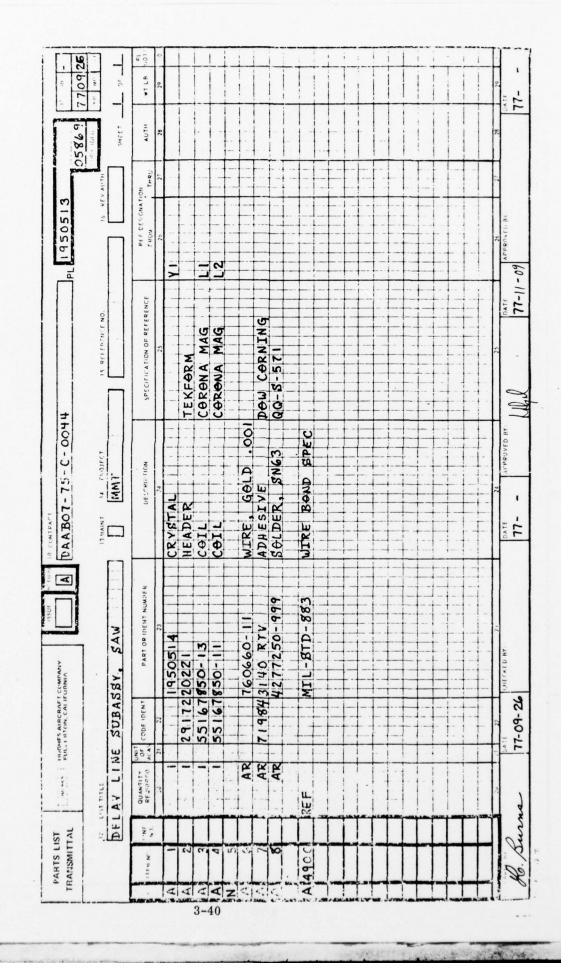
\*Optional, can be included in 1950XXX.





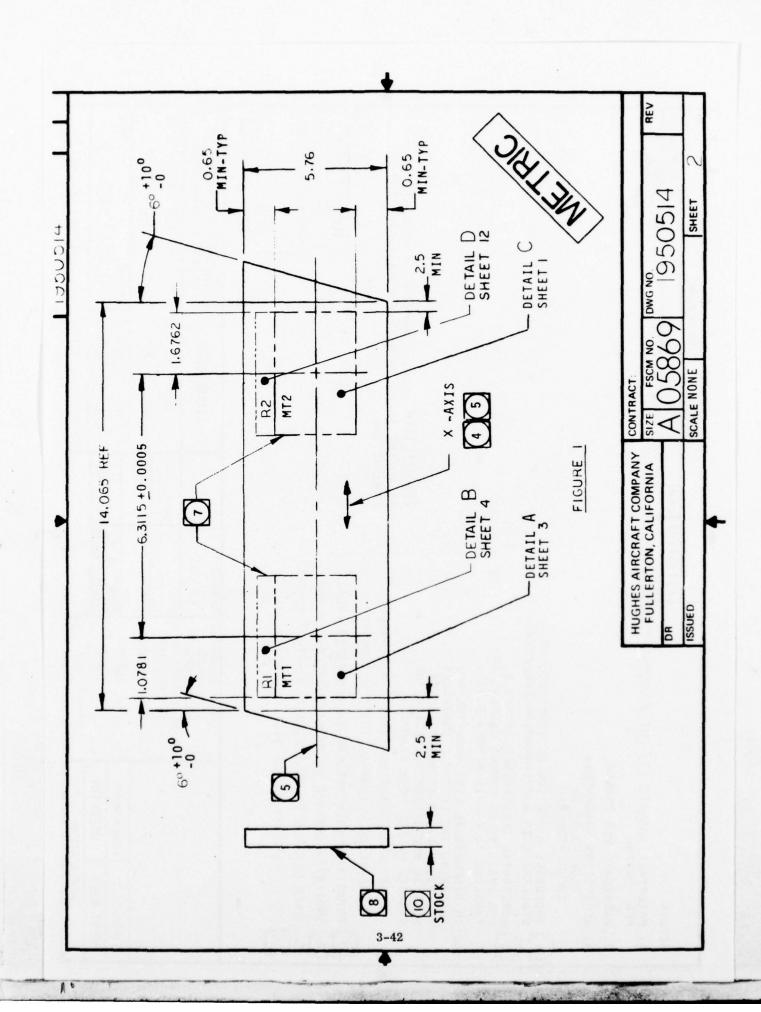
Nº

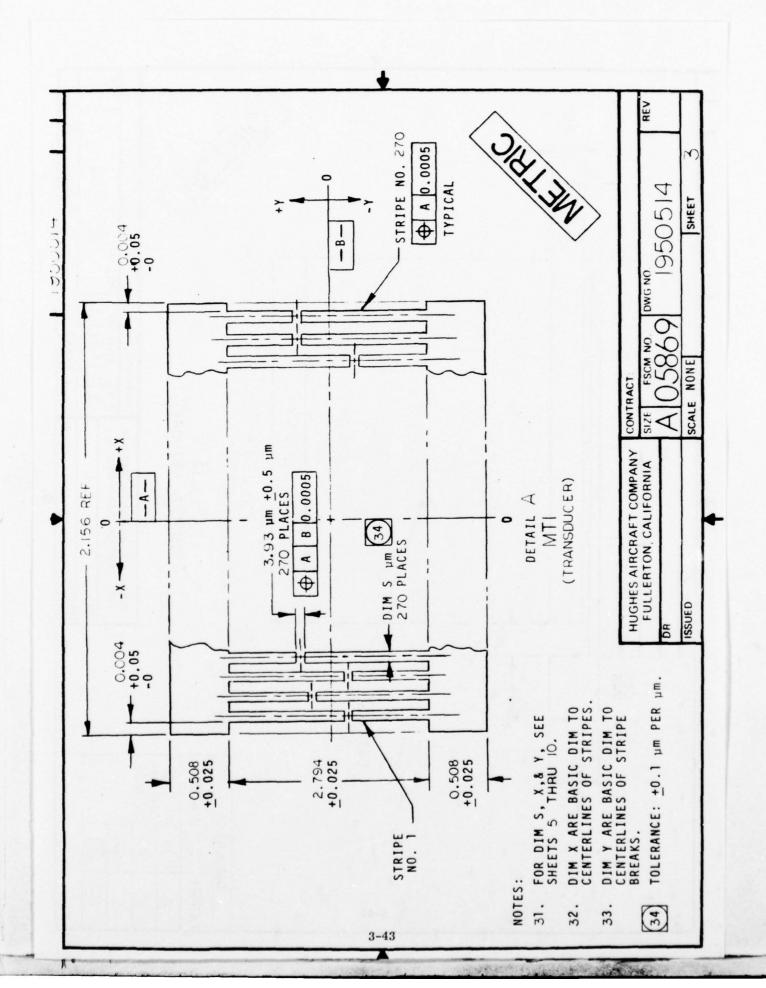


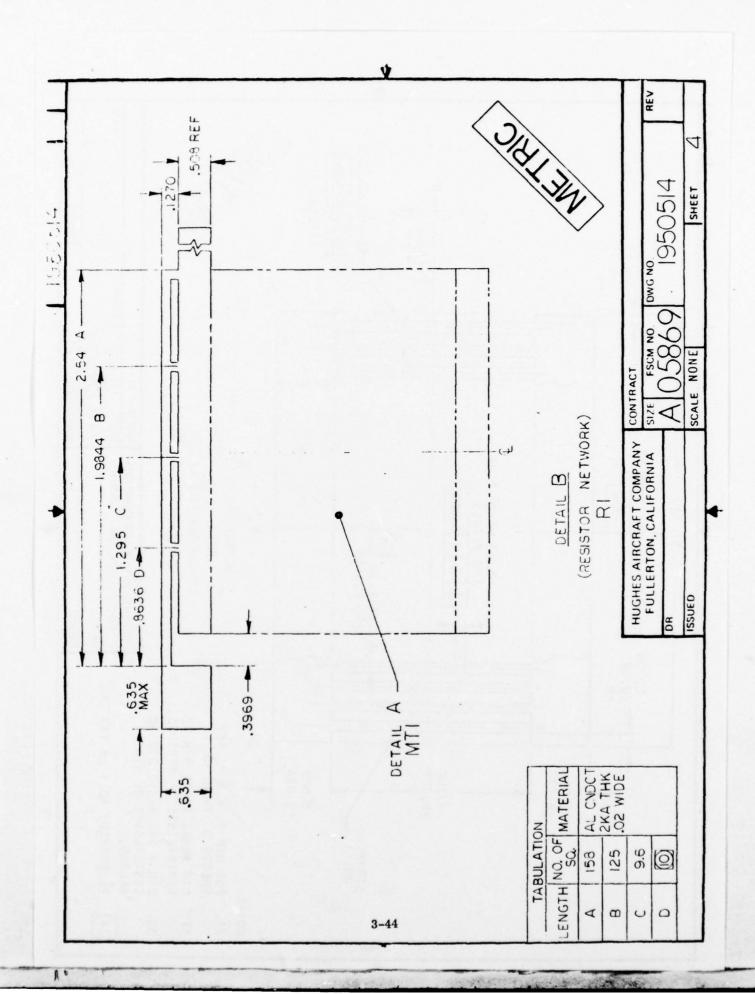


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APPROVED (AMERICAN) PROJECTION REV METRIC HUGHES AIRCRAFT COMPANY 2 FULLERTON, CALIFORNIA THIRD ANGLE TO BE INSTALLED IN NEXT ASSEMBLY AT POINT OF DOMHZ CENTER FREQ., 2 MHZ BANDWIDTH OF CRYSTAL, SURFACE ACOUSTIC WAVE FRAGILE ITEM (EASILY DAMAGED BY HANDLING) 1950514 SHEET 1 DATE REVISIONS PRODUCTION RELEASE DESCRIPTION 3 HUGHES SCALE NONE MANUFACTURE. SIZE 37.60.6Z 20-60-81 DAAB07-75C-0074 LTR AUTHORITY ULT 86948 2.5,0000 BACK SURFACE TO BE ROUGHENED WITH #180 GRIT. CONTRACT 8 INDICATED SURFACE TO BE CORRUGATED PER P82 DEPOSITION FILM APPLIED IN INDICATED AREA. CHK TO BE DETERMINED AT TIME OF FABRICATION.  $1.45870E-02 = 1.45870 \times 10^{-2} = 0.014587$ 1. MATERIAL: QUARTZ (ST CUT, X PROPAGATING) STALLINE AXIS & PROPAGATION DIRECTION. 1.34567E 00 = 1.34567 x 10<sup>0</sup> = 1.34567 INDICATES DIRECTION OF SPECIFIED CRY-DIMENSIONS ARE UNLESS OTHERWISE +0.002 +20 PER ANSI Y 14.5 +0.02 +0.5 SPECIFIED HORIZONTAL CENTERLINES OF MT1 & MT2 SHALL BE CO-LINEAR WITHIN AND FOLLOWING THE LETTER E INDICATES MUST BE MULTIPLIED TO OBTAIN THE PARALLEL TO X-AXIS WITHIN 0.250. THE POWER OF 10 BY WHICH THE NO. IN DIMENSIONAL LISTINGS, THE NO. ANGLES xxx. ××. FOR EXAMPLE: Z 3. DEPOSITION THICKNESS: 2. FABRICATE PER 780294 0.20 +0.01 µm USED ON SAW-MMT CORRECT VALUE. **APPLICATION** PER 760781. ASSY 950513 NOTES: NEXT o (2) 9







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DIM S STRIPE LIDIH	8 W B B B B B B B B B B B B B B B B B B	FSCP NO. DRAWING NO. 05869 1950514 SHELT
DIM Y BREAK LOCATION	11111111111111111111111111111111111111	D HAMMING TRANSCUCER SIZE A A SCAL
STRIPE LOCATION		T BPG LNAPODIZ DE STRIPES:
STRIPL NO.		TRANSDUCER NA DATE: JAN 7 RFF DES: MT1 TCTAL NUMBER

		REV 6
STRIPE WIDTH	WWWWWWWWWWWWWWWWWWWWWWWWWWWWWWWWWWWW	FSCM NO. DFAWING NO. 05869 1950514 : NONE SHEET
DIN Y BREAK LOCATION	11111111111111111111111111111111111111	IZED HAMMING TRANSCUCER SIZE A A A A A A A A A A A A A A A B A A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B A B
STRIPE LOCATION		NAME: ECOMMT RPO LNAFOD N 2C,1978 T1 FR CF ELECTRODE STRIPES:
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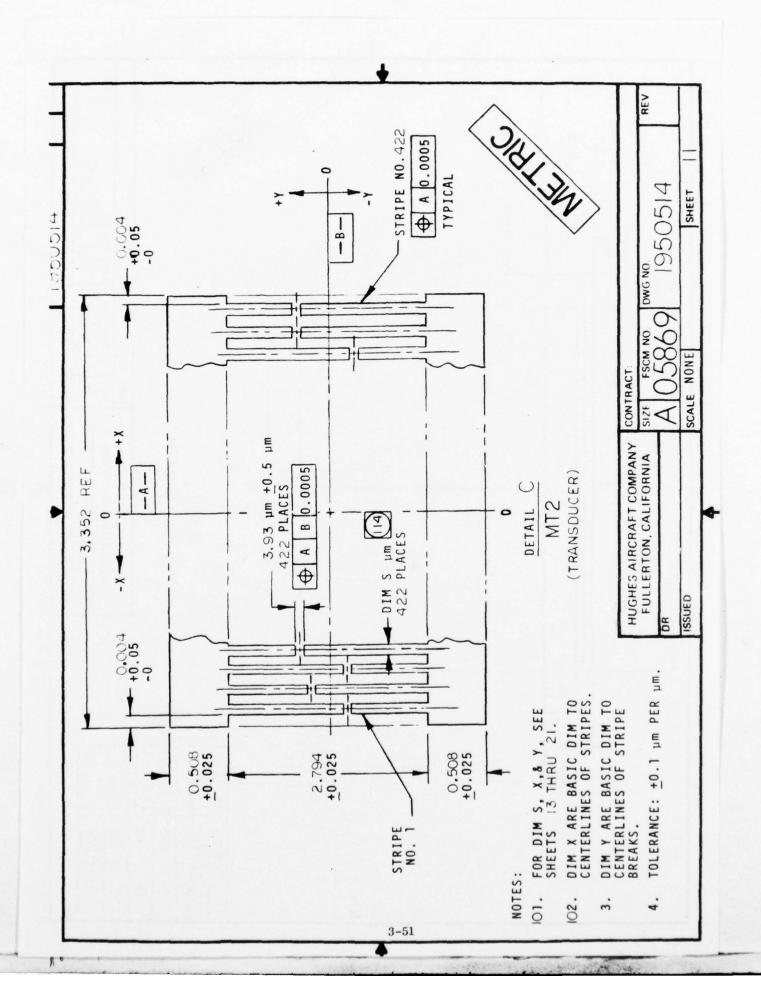
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DIM X STRIPE LOCATION	11.00.00.00.00.00.00.00.00.00.00.00.00.0	E: ECOMMT BPG LNAPODIZE 1978 F ELECTRODE STRIPES: 2
STRIPE NO.		TRANSEUCER NAM DATE: JAN 20 REF DES: MT1 TCTAL NUMBER C

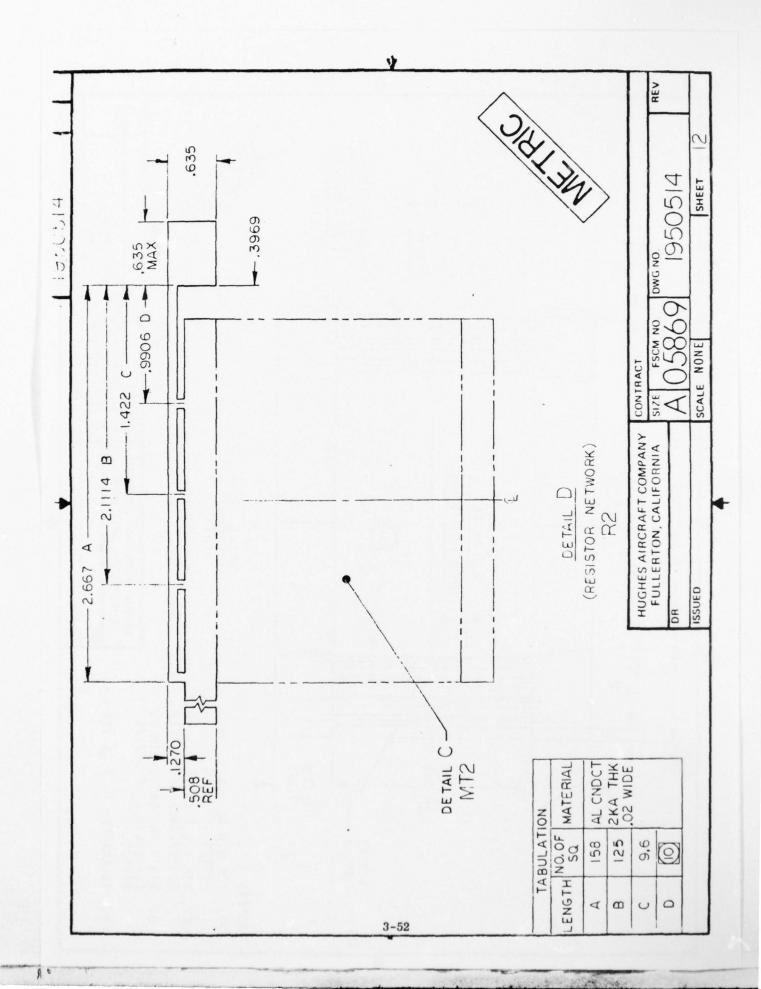
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STRIPE WIDTH	W W W W W W W W W W W W W W W W W W W	FSCP NO. CRAMING NO. 05869 1950514 : NONE
DIM Y		MMING TRANSCUCER SIZE A SCALE:
TICN PREA		EPG LNAFODIZED HAM STRIPES: 270
STRIPE LUCA	$\begin{array}{cccccccccccccccccccccccccccccccccccc$	SSDUCER NAME: ECOMMIT: COMMIT: DES: WILL NUMBER OF ELECTRODE
STRIPL NG.		TRANSD DATE: REF DE TOTAL

DIM S STRIPE WIDTH	NEWENDRINNERS NEWS NEWS NEWS NEWS NEWS NEWS NEWS NEW	LE: NONE CRAWING NO.
DIM Y BREAK LOCATION		. 270 S.C.A. S.C.A.
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BREAK LCCATION	00	O O	1.27000E 00 1.27000E 00	000	0 0 U U	O O	00	900		HAMMING TRANSDUCER	•
O.P.										LAAPODIZ	SINITES: KIN
STRIPE LOCATION	9.08927E-01	9.2466FE-01	9.40405E-01 9.48274E-01 9.56144E-01	9.74683E-01 9.79752E-01	9.87622E-01	1.00336E 00 1.01123E 00	1.01910E 00 1.02697E 00	1.04271E 00 1.05058E 00	1.05845E	C+1978	OF ELECTRODE S
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BREAK LOCATION	######################################	VASILE INANSDUCIN SIZE
STRIPE LOCATION	11111111111111111111111111111111111111	20,1978 20,1978 2 OF ELECTRODE STRIFES:
STRIFE NG.		DATE: JAN PEF PES: MI TOTAL NUMPF

		REV 14
STRIPE WIDTH	88 888 88 888 888 888 888 888 888 888	FSCP NO. CRAWING NO. 05869 1950514 E: NONE SHEET
DIM Y BREAK LCCATION	### ### #### #########################	ZED VASILE TRANSDUCER SIZE A 422 SCALI
STRIPE LOCATION	11111111111111111111111111111111111111	K NAME: ECOMMI EPG AFCDI AN 20,1978 MT2 PFR OF ELECTRODE STRIPES:
STRIPE NG.	まるでもほうではらいまるでもちらなるないないないない。 これでも ちゅう はいしょう しゅうしょう しゅうしょう しゅうしょう しゅうしゅう しゅう	TRANSDUCE DATE: J RFF DES: I TCTAL NUMI

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		REV 15
DIM S STRIPE WIDTH	WH WW WH WW W	FSCM NO. DRAWING NO. 05869 1950514 : NONE SHEET
DIM Y BREAK LCCATION	### ### ### ### ### ### ### ### ### ##	SIZE STANSDUCK SIZE
DIM X STRIPE LOCATION	10010101010101010101010101010101010101	APPE: ECOMMI BPG AFCDI A 20,1978 12 FR OF ELECTRODE STRIPES:
STRIPE NO.	まるさみほらでもららりまえきみほらでみらりまえをみらせてんらりまえでみたらでんりのまるさんだらでん	THANSDUCER DATE: JA PEFF DES: JA TOTAL NUMB

		RE.
DIM S STRIPE WIDTH	WWWWWWWWWWWWWWWWWWWWWWWWWWWWWWWWWWWW	FSCP NO. DRAWING NO. 1956514 SHEET
DIM Y BREAK LCCATION	6.000000000000000000000000000000000000	ZED VASILE TRANSDUCER SIZE A A 422 SCALES
STRIPE LOCATION	100 100 100 100 100 100 100 100	NAME: FCOMMT PPG APCDI N 20,1978 72 ER OF ELECTRODE STRIPES:
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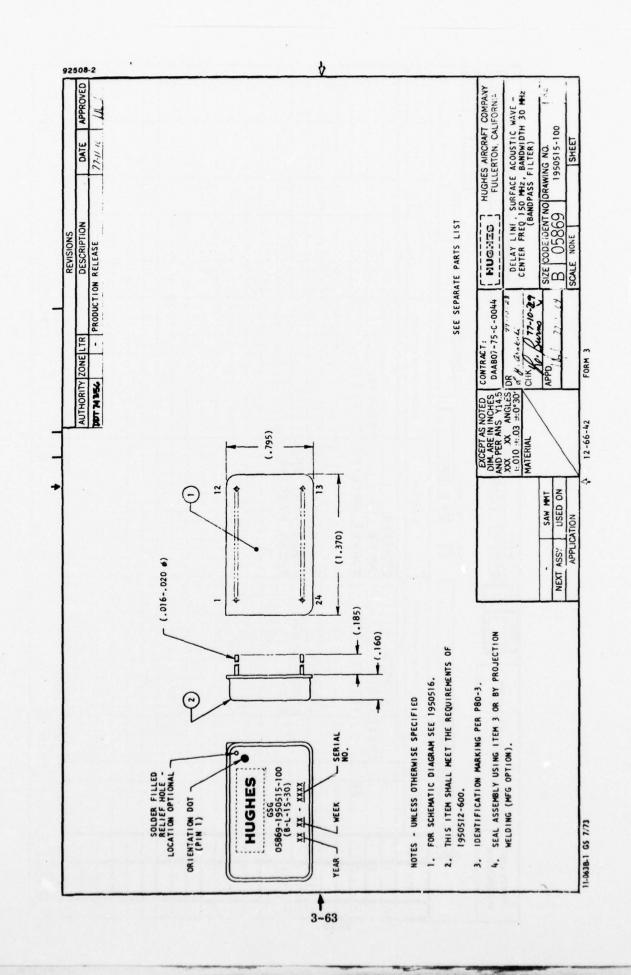
		REV 17
DIM S STRIPE WIDTH	80 80 80 80 80 80 80 80 80 80 80 80 80 8	ZE FSCM NO. DRAWING NO. 05869 1950514 ALE: NONE. SHEET
DIM Y BREAK LOCATION	11. 1. 1. 1. 1. 1. 1. 1. 1. 1. 1. 1. 1.	A 422 SC 422 SC 422 SC 85
STRIPE LOCATION	11. 1. 1. 1. 1. 1. 1. 1. 1. 1. 1. 1. 1.	IN 20,1978 IN 20,1978 ITS CF ELECTRODE STRIPES:
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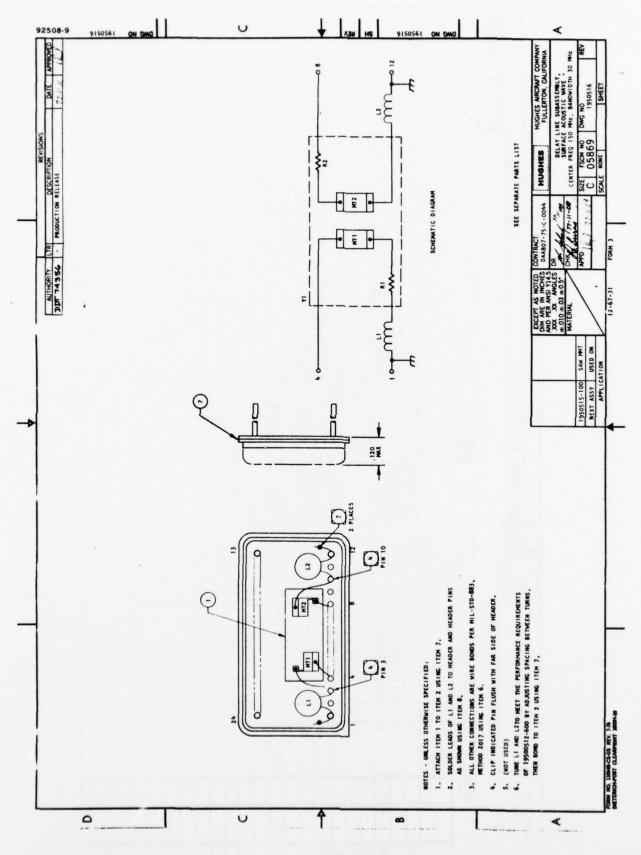
DIM S STRIPE WIDTH	**************************************	ZE FSCM NO. DRAWING NO. 05869 1950514
DIM Y BREAK LOCATION		12ED VANIEL TRANSDUCEN ST A 422
DIM X STRIPE LOCATION	11.1.1.1.1.1.1.1.1.1.1.1.1.1.1.1.1.1.1	DAN 20,1978 MT2 OF ELECTRODE STRIPES
STRIFF NO.	まるさんともて とりじまるさん ちららまる こうちょう こうこう ちらう しょう ちょう ちょう カラ しゃりり	TRANSPUCE DATE: REF DES: TCTAL NUM

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STRIPE WIDTH	80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80       80 <td< th=""><th>E FSCM NO. CRAUING NO. 05869 1950514 LE: NONE SHEET</th></td<>	E FSCM NO. CRAUING NO. 05869 1950514 LE: NONE SHEET
DIM Y BREAK LOCATION		VASILE TRANSDUCER SIZE A A 422 SCALE
STRIPE LOCATION	11.00000000000000000000000000000000000	ER NAME: ECOMMT BPG AFCDIZED JAN 20,1978 MBFR CF ELECTRODE STRIPES: 4
.00		TRANSDUCE DATE: J REF DES: TCTAL NUM



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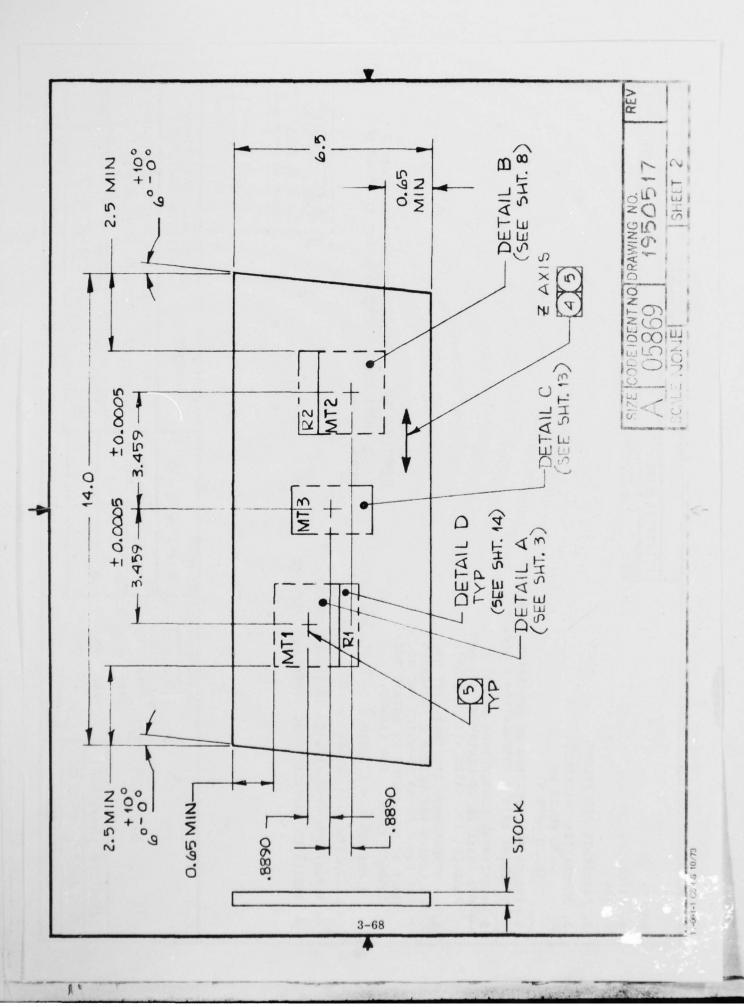
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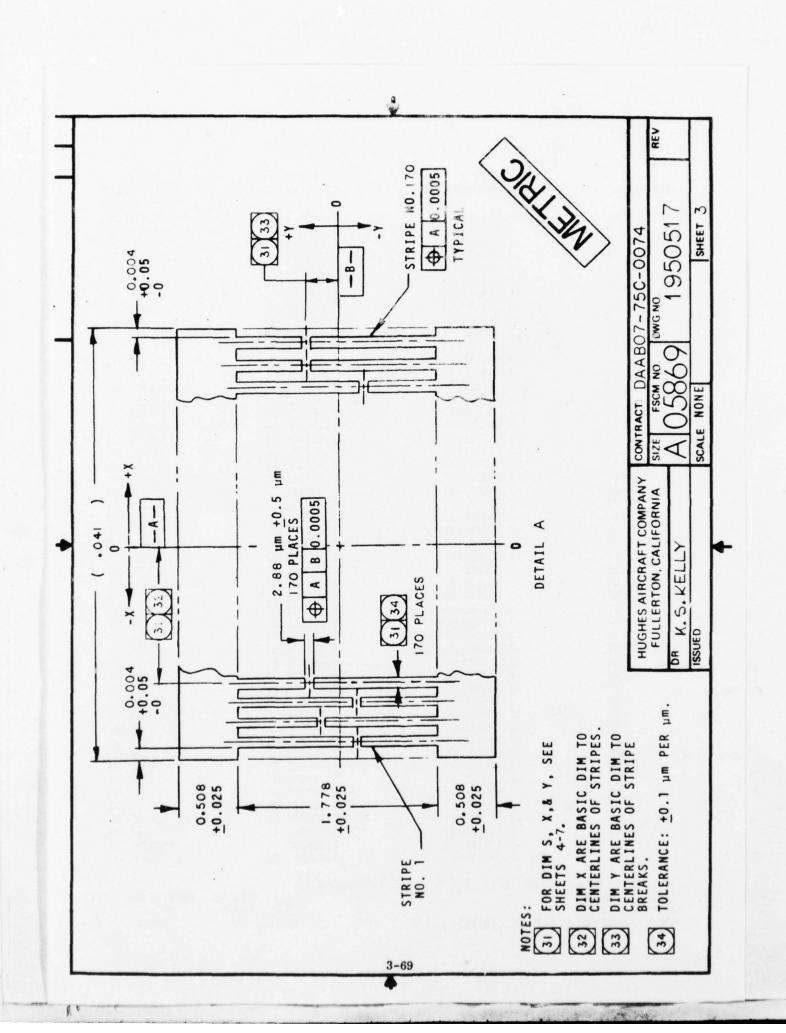


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CRYSTAL, SURFACE ACOUSTIC WAVE - BP-LN APPROVED (AMERICAN) PROJECTION REV METRIC HUGHES AIRCRAFT COMPANY OF 14 FULLERTON, CALIFORNIA FRAGILE ITEM (EASILY DAMAGED BY HANDLING) -to be installed in next assembly at point of 50 MHz CENTER FREQ., 50 MHz BANDWITH 1950517 DATE SHEET DWG NO REVISIONS PROTUCTION RELEASE DESCRIPTION × HUGHES SCALE NONE MANUFACTURE SIZE 78-05-16 DAAB07-75C-0074 26 66 LTR AUTHORITY K.S.KELLY CONTRACT DDT 7. DEPOSITION FILM APPLIED IN INDICATED AREA. 8. INDICATED SURFACE TO BE CORRUGATED PER P82  $1.45870E-02 = 1.45870 \times 10^{-2} = 0.014587$ STALLINE AXIS & PROPAGATION DIRECTION. 1.34567E 00 = 1.34567 x 10<sup>0</sup> = 1.34567 INDICATES DIRECTION OF SPECIFIED CRY-DIMENSIONS ARE MILLIMETERS & UNLESS OTHERWISE +0.002 +5<sub>0</sub> PER ANSI Y 14.5 +0.02 +0.5 SPECIFIED HORIZONTAL CENTERLINES OF MT1 & MT2 SHALL BE CO-LINEAR WITHIN AND -AXIS WITHIN 0.250. FOLLOWING THE LETTER E INDICATES MUST BE MULTIPLIED TO OBTAIN THE IN DIMENSIONAL LISTINGS, THE NO. THE POWER OF 10 BY WHICH THE NO. ANGLES XXX. CORRECT VALUE. FOR EXAMPLE: ××. 1. MATERIAL: LITHIUM NIOBATE Z 3. DEPOSITION THICKNESS: 2. FABRICATE PER 780294 SAW/MMT USED ON 0.20 +0.01 µm (2000) +100 R) **APPLICATION** PARALLEL TO 1950516 **NEXT ASSY** PER NOTES: 9 2





STRIPE NO.	DIM X STRIPE LOCATION	DIM Y BREAK LOCATION	DIM S STRIPE WIDTH
1	-4.86432E-01	5.66407E-02	2.87829E 00
	-4.80675E-01	5.66407E-02	2.87829E 00
2 3 4	-4.74818E-01	1.90297E-02	2.87829E 00
4	-4.69162E-01	1.90297E-02	2.87829E 00
5	-4.63405E-01	-2.21336E-02	2.87829E 00
6	-4.57649E-01	-2.21336E-02	2.87829E 00
6 7	-4.51892E-01	2.68795E-02	2.87829E 00
8	-4.46135E-01	2.68795E-02	2.87829E 00
9	-4.46379E-01	-3.16357E-02	2.87829E 00
10	-4.34622E-01	-3.16357E-02	2.87829E 00
11	-4.28886E-01	3.41986E-02	2.87829E 00
12	-4.23109E-01	3.41986E-02	2.87829E 00
13	-4.17352E-01	-3.28562E-02	2.87829E 00
14	-4.11596E-01	-3.28562E-02	2.87829E 00
15	-4.05839E-01	2.68865E-02	2.87829E 00
16	-4.00083E-01	2.66865E-02	2.87829E 00
17	-3.94326E-01	-1.54610E-02	2.87829E 00
18	-3.88570E-01	-1.54610E-02	2.87829E 00
19	-3.82813E-01	-1.51130E-04	2.87829E 00
20	-3.77056E-01	-1.51130E-04	2.87829E 00
21	-3.71300E-01	1.84252E-02	2.87829E 00
22 23	-3.65543E-01	1.84252E-02	2.87829E 00
24	-3.59787E-01	-3.68249E-02 -3.68249E-02	2.87829E 00
25	-3.54030E-01 -3.48273E-01	5.23786E-02	2.87829E 00 2.87829E 00
26	-3.42517E-01	5.23786E-02	2.87829E 00
27	-3.36760E-01	-6.20306E-02	2.87829E 00
28	-3.31004E-01	-6.20306E-02	2.87829E 00
29	-3.25247E-01	6.31545E-02	2.87829E 00
30	-3.19491E-01	6.31545E-02	2.87829E 00
- 31	-3.13734E-01	-5.41261E-02	2.87829E 00
32	-3.07977E-01	-5.41261E-02	2.87829E 00
33	-3.02221E-01	3.47269E-02	2.87829E 00
34	-2.96484E-01	3.47269E-02	2.87829E 00
35	-2.90708E-01	-6.36523E-03	2.87829E 00
36	-2.84951E-01	-6.36523E-03	2.87829E 00
37	-2.79194E-01	-2.78498E-02	2.78729E 00
38	-2.73438E-01	-2.78498E-02	2.87829E 00
39	-2.67681E-01	6.33463E-02	2.87829E 00
40	-2.61925E-01	6.33463E-02	2.87829E 00
41	-2.56168E-01	-9.46250E-02	2.87829E 00
42 43	-2.50412E-01 -2.44655E-01	-9.46250E-02 1.15975E-01	2.87829E 00 2.87829E 00
44	-2.44655E-01 -2.38898E-01	1.15975E-01	2.87829E 00
45	-2.33142E-01	-1.22315E-01	2.87829E 00
46	-2.27385E-01	-1.22315E-01	2.87829E 00
47	-2.21629E-01	1.10094E-01	2.87829E CO
48	-2.15872E-01	1.10094E-01	2.87829E 00
49	-2.10115E-01	-7.80809E-02	2.87829E 00
50	-2.04359-01	-7.80809E-02	2.87829E 00

TRANSDUCER NAME: ECOMMT BPLN, 148 MHZ RICE TRANSDUCER DATE: JAN 20, 1978
REF DES: MT1
TOTAL NUMBER OF ELECTRODE STRIPES: 170

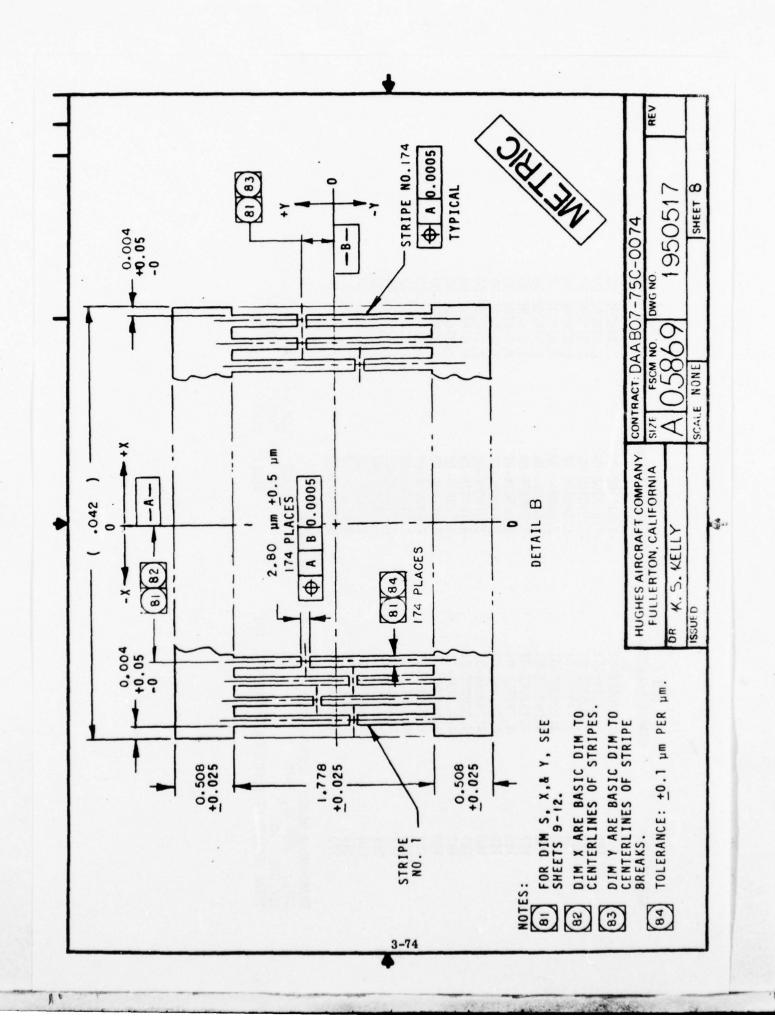
SIZE FSCM NO. DRAWING NO. REV A 05869 SCALE: NONE 1950517 SHEET 4

	DIM X	DIM Y	DIM S	
STRIPE NO.	STRIPE LOCATION	BREAK LOCATION	STRIPE WIDTH	-
51	-1.98802E-01	2.78778E-02	2.87829E 00	
52	-1.92846E-01	2.78778E-02	2.87829E 00	
53	-1.87889E-01	3.58737E-02	2.87829E 00	
54	-1.81332E-01	3.58737E-02	2.87829E 00	
55	-1.75576E-01	-1.05683E-01		
56	-1.69819E-01		2.87829E 00	
57	-1.64063E-01	-1.05683E-01	2.87829E 00	
58		1.71845E-01	2.87829E 00	
59	-1.58306E-01	1:71845E-01	2.87829E 00	
	-1.52550E-01	-2.23444E-01	2.87829E 00	
60	-1.46793E-01	-2.23444E-01	2.87829E 00	
61	-1.41036E-01	2.49599E-01	2.87829E 00	
62	-1.35280E-01	2.49599E-01	2.87829E 00	
63	-1.29523E-01	-2.40862E-01	2.87829E 00	
64	-1.23767E-01	-2.40862E-01	2.87829E 00	
65	-1.18010E-01	1.90549E-01	2.87829E 00	
66	-1.12253E-01	1.90549E-01	2.87829E 00	
67	-1.06497E-01	-9.58506E-02	2.87829E 00	
68	-1.06740E-01	-9.58505E-02	2.87829E 00	
69	-9.49836E-02	-4.14820E-02	2.87829E 00	
70	-8.92271E-02	-4.14820E-02	2.87829E 00	
71	-8.34705E-02	2.14911E-01	2.87829E 00	
72	-7.77139E-02	2.14911E-01	2.87829E 00	
73	-7.19873E-02	-4.13476E-01	2.87829E 00	
74	-6.62007E-02	-4.13476E-01	2.87829E 00	
75	-6.04442E-02	6.22729E-01	2.87829E 00	
76	-5.46876E-02	6.22729E-01	2.87829E 00	
77	-4.89310E-02	-8.26083E-01	2.87829E 00	
78	-4.31744E-02	-8.26083E-01	2.87829E 00	
79	-3.74178E-02	1.00650E 00	2.87829E 00	
80	-3.16612E-02	1.00650E 00	2.87829E 00	
81	-2.59046E-02	-1.14830E 00	2.87829E 00	
82	-2.01481E-02	-1.14830E 00	2.87829E 00	
83	-1.43916E-02	1.23887E 00	2.87829E 00	
84	-8.63488E-03	1.23887E 00	2.87829E 00	
85	-2.87829E-03	-1.27000E 00	2.87829E 00	
86	2.87829E-03	-1.27000E 00	2.87829E 00	
87	8.63488E-03	1.23887E 00	2.87829E 00	
88	1.43915E-02	1.23887E 00	2.87829E 00	
89	2.01481E-02	-1.14830E 00	2.87829E 00	
90	2.59046E-02	-1.14830E 00	2.87829E 00	
91	3.16612E-02	1.00650E 00	2.87829E 00	
92	3.74178E-02	1.00650E 00	2.87829E 00	
93	4.31744E-02	-8.26083E-01	2.87829E 00	
94	4.89310E-02	-8.26083E-01	2.87829E 00	
95	5.46876E-02	6.22729E-01	2.87829E 00	
96	6.04442E-02	6.22729E-01	2.87829E 00	
	6.62007E-02	-4.13476E-01	2.87829E 00	
97 98	7.19573E-02	-4.13476E-01	2.87829E 00	
		2.14911E-01		
99	7.77139E-02		2.87829E 00	
100	8.34705E-02	2.14911E-01	2.87829E 00	
TRANSDUCER NAME:			500W W0 5550000000000000000000000000000	
DATE: JAN 20,	1978	SIZE	FSCM NO. DRAWING NO.	REV
REF DES: MT1	FLECTRODE CTRIBES	A	05869 1950517	-
TOTAL NUMBER OF	ELECTRODE STRIPES: 17	O SCALE:	NONE SHEET	5

STRIPE NO.	DIM X STRIPE LOCATION	DIM Y BREAK LOCATION	DIM S STRIPE WIDTH
101	8.92271E-02	-4.14820E-02	2.87829E 00
102	9.49836E-02	-4.14820E-02	2.87829E 00
103	1.00740E-01	-9.58505E-02	2.87829E 00
104	1.06497E-01	-9.58505E-02	2.87829E 00
105	1.12253E-01	1.90549E-01	2.87829E 00
106	1.18010E-01	1.90549E-01	2.87829E 00
107	1.23767E-01	-2.40862E <b>-</b> 01	2.87829E 00
108	1.29523E-01	-2.40862E-01	2.87829E 00
109	1.35280E-01	2.49599E-01	2.87829E 00
110	1.41036E-01	2.49599E-01	2.87829E 00
111	1.46793E-01	-2.23444E-01	2.87829E 00
112	1.52550E-01	-2.23444E-01	2.87829E 00
113	1.68306E-01	1.71845E-01	2.87829E 00
114	1.64063E-01	1.71845E-01	2.87829E 00
115	1.69819E-01	-1.05683E-01	2.87829E 00
116	1.75576E-01	-1.05683E-01	2.87829E 00
117	1.81332E-01	3.58737E-02	2.87829E 00
118	1.87089E-01	3.58737E-02	2.87829E 00
119	1.92846E-01	2.78778E-02	2.87829E 00
120	1.98602E-01	2.78778E-02	2.87829E 00
121	2.04359E-01	-7.80809E-02	2.87829E 00
122	2.10115E-01	-7.80809E-02	2.87829E 00
123	2.15872E-01	1.10094E-01	2.87829E 00
124	2.21029E-01	1.10094E-01	2.87829E 00
125	2.27385E-01	-1.22315E-01	2.87829E 00
126	2.33142E-01	-1.22315E-01	2.87829E 00
127	2.38898E-01	1.15975E-01	2.87829E 00
128	2.44655E-01	1.15975E-01	2.87829E 00
129	2.50412E-01	-9.46250E-02	2.87829E 00
130	2.56168E-01	-9.46250E-02	2.87829E 00
131	3.61925E-01	6.33463E-02	2.87829E 00
132	2.67681E-01	6.33463E-02	2.87829E 00
133	2.73438E-01	-2.78498E-02	2.87829E 00
134	2.79194E-01	-2.78498E-02	2.87829E 00
135	2.84951E-01	-6.36523E-03	2.87829E 00
136 137	2.90708E-01 2.96464E-01	-6.36523-03	2.87829E 00 2.87829E 00
138	3.02221E-01	3.47269E-02 3.47269E-02	2.87829E 00
139	3.07977E-01	-6.41261E-02	2.87829E 00
140	3.13734E-01	-5.41261E-02	2.87829E 00
141	3.19491E-01	6.31545E-02	2.87829E 00
142	3.25247E-01	6.31545E-02	2.87829E 00
143	3.31004E-01	-6.20306E-02	2.87829E 00
144	3.36760E-01	-6.20306E-02	2.87829E 00
145	3.42517E-01	5.23786E-02	2.87829E 00
146	3.48273E-01	5.23786E-02	2.87829E 00
147	3.54030E-01	-3.68249E-02	2.87829E 00
148	3.59787E-01	-3.68249E-02	2.87829E 00
149	3.65543E-01	1.84252E-02	2.87829E 00
150	3.71300E-01	1.84252E-02	2.87829E 00

TRANSDUCER NAME: ECOMMT BPLN, 148MHZ RICE TRANSDUCER
DATE: JAN 20, 1978
REF DES: MT1
TOTAL NUMBER OF ELECTRODE STRIPES: 170
SCALE: NONE
SIZE FSCM NO. DRAWING NO. REV
A 05869 1950517
SCALE: NONE SHEET 6

		RE 7
DIM S STRIPE WIDTH	2.87829E 00	DRAWING NO. 1950517 SHEET
		FSCM NO. 05869 NONE
DIM Y BREAK LOCATION	-1.51130E-04 -1.51130E-04 -1.51610E-02 2.66865E-02 2.66865E-02 -3.28562E-02 3.41986E-02 3.41986E-02 3.41986E-02 2.68795E-02 -3.16357E-02 2.68795E-02 2.68795E-02 2.68795E-02 5.66407E-02	SIZE A SCALE:
BREAK	1.54 1.54 1.54 1.54 1.54 1.54 1.54 1.54	TRANSDUCER
DIM X STRIPE LOCATION		ECOMMT BPLN, 148MHZ RICE 1978 ELECTRODE STRIPES: 170
STRIPE NO.	151 152 153 154 156 160 161 163 165 165 168 170	TRANSDUCER NAME: DATE: JAN 20, 1 REF DES: MT1 TOTAL NUMBER OF E

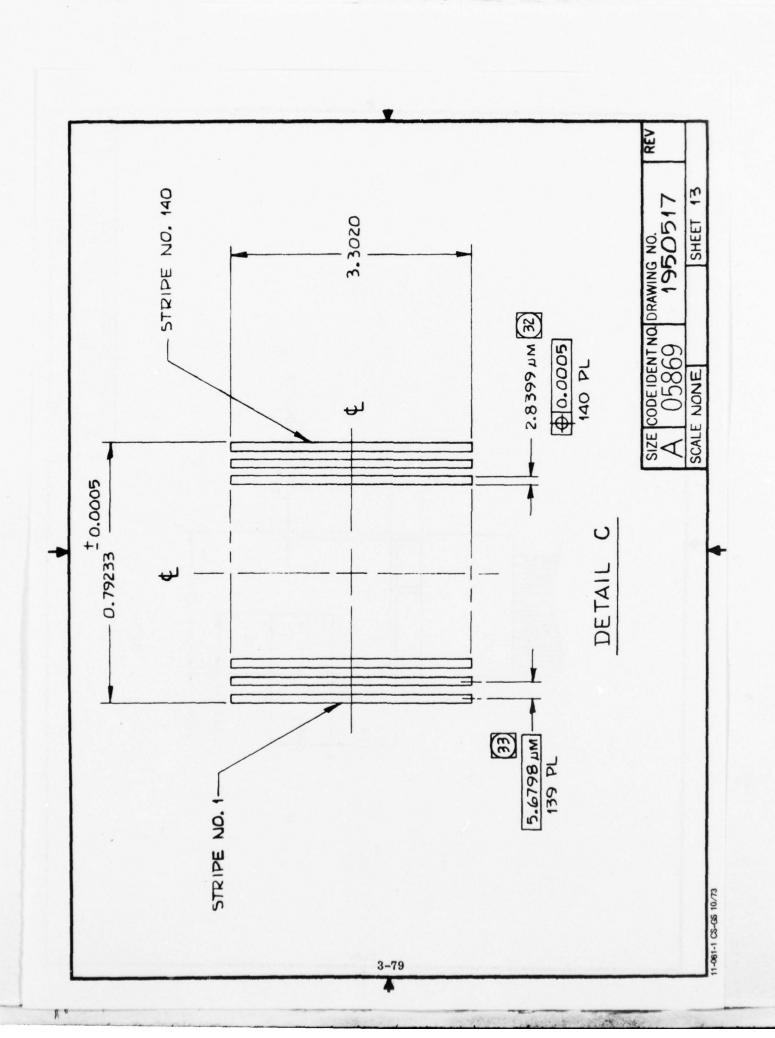


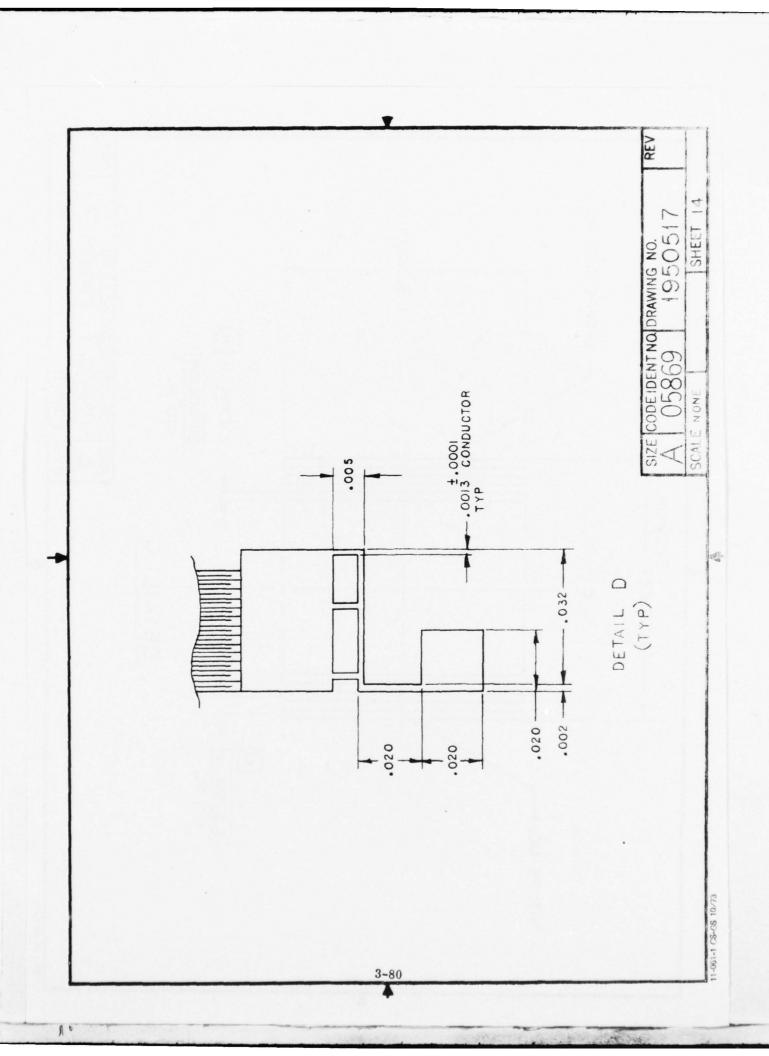
STRIPE NO.	DIM X STRIPE LOCATION	DIM Y BREAK LOCATION	DIM S STRIPE WIDTH
1	-4.84841E-01	5.72935E-02	2.80255E 00
2	-4.79236E-01	5.72935E-02	2.80255E 00
3 4	-4.73631E-01	3.15138E-02	2.80255E 00
4	-4.68026E-01	3.15138E-02	2.80255E 00
5	-4.62421E-01	-3.08419E-02	2.80255E 00
6	-4.56815E-01	-3.08419E-02	2.80255E 00
7	-4.51210E-01	3.25221E-02	2.80255E 00
8	-4.45635E-01	3.25221E-02	2.80255E 00
9	-4.40000E-01 -4.34395E-01	-3.41985E-02	2.80255E 00
11	-4.28790E-01	-3.41985E-02 3.35356E-02	2.80255E 00 2.80255E 00
12	-4.23185E-01	3.35356E-02	2.80255E 00
13	-4.17580E-01	-2.94843E-02	2.80255E 00
14	-4.11975E-01	-2.94843E-02	2.80255E 00
15	-4.06370E-01	2.10172E-02	2.80255E 00
16	-4.00764E-01	2.10172E-02	2.80255E 00
17	-3.95159E-01	-8.17625E-03	2.80255E 00
18	-3.89554E-01	-8.17625E-03	2.80255E 00
19	-3.83949E-01	-7.89812E-03 ·	2.80255E 00
20	-3.78344E-01	-7.89812E-03	2.80255E 00
21	-3.72739E-01	2.55206E-02	2.80255E 00
22	-3.67134E-01	2.55206E-02	2.80255E 00
23	-3.61529E-01	-4.22757E-02	2.80255E 00
24	-3.55924E-01	-4.22757E-02	2.80255E 00
25	-3.50319E-01	5.55041E-02	2.80255E 00
26	-3.44714E-01	5.55041E-02	2.80255E 00
27	-3.39108E-01	-6.26706E-02	2.80255E 00
28 29	-3.33503E-01 -3.27898E-01	-6.26706E-02 6.16051E-02	2.80255E 00 2.80255E 00
30	-3.22293E-01	6.16051E-02	2.80255E 00
31	-3.16688E-01	-5.11213E-02	2.80255E 00
32	-3.11083E-01	-5.11213E-02	2.80255E 00
33	-3.05478E-01	3.12725E-02	2.80255E 00
34	-2.99873E-01	3.12725E-02	2.80255E 00
35	-2.94268E-01	-3.49758E-03	2.80255E 00
36	-2.88662E-01	-3.49758E-03	2.90255E 00
37	-2.83057E-01	-2.93040E-02	2.80255E 00
38	-2.77452E-01	-2.93040E-02	2.80255E 00
39	-2.71847E-01	6.30999E-02	2.80255E 00
40	-2.66242E-01	6.30999E-02	2.80255E 00
41	-2.60637E-01	-9.30731E-02	2.80255E 00
42 43	-2.55032E-01	-9.30731E-02	2.80255E 00
43	-2.49427E-01 -2.43822E-01	1.14181E-01 1.14181E-01	2.80255E 00 2.80255E 00
45	-2.43022E-01 -2.38217E-01	-1.21912E-01	2.80255E 00
46	-2.32612E-01	-1.21912E-01	2.80255E 00
47	-2.27006E-01	1.12959E-01	2.80255E 00
48	-2.21401E-01	1.12959E-01	2.80255E 00
49	-2.15798E-01	-8.58824E-02	-2.80255E 00
50	-2.10191E-01	-8.58824E-02	2.80255E 00
TRANSDUCER NAME: DATE: JAN 20.	ECOMMT BPLN, 152MHZ R	ICE TRANSDUCER SIZE FSCM NO.	DRAWING NO.
DATE: JAN 20, REF DES: MT2		A 05869	1950517
	ELECTRODE STRIPES: 174	SCALE: NONE	SHEET

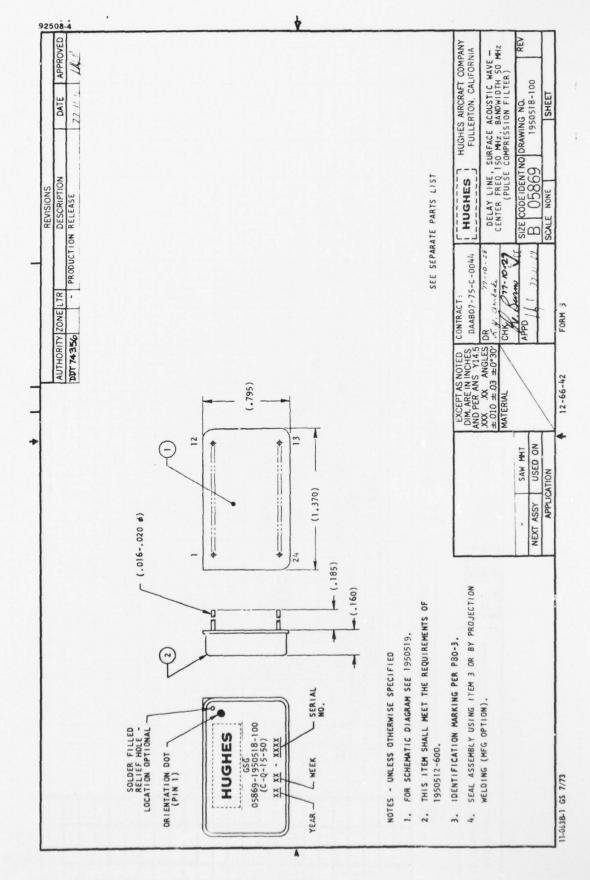
	DIM X	DIM Y	DIM S
STRIPE NO.	STRIPE LOCATION	BREAK LOCATION	STRIPE WIDTH
51	-2.04586E-01	4.16039E-02	2.80255E 00
52	-1.98981E-01	4.16039E-02	2.80255E 00
53	-1.93378E-01	1.64351E-02	2.80255E 00
54	-1.87771E-01	1.64351E-02	2.80255E 00
55	-1.82166E-01	-8.23009E-02	2.80255E 00
56	-1.76561E-01	-8.23009E-02	2.80255E 00
57	-1.70955E-01	1.47993E-01	2.80255E 00
58	-1.65351E-01	1.47993E-01	2.80255E 00
59	-1.59745E-01	-2.04175E-01	2.80255E 00
60	-1.54140E-01	-2.04175E-01	2.80255E 00
61	-1.48535E-01	2.41097E-01	2.80255E 00
62	-1.42930E-01	2.41097E-01	2.80255E 00
63	-1.37325E-01	-2.49735E-01	2.80255E 00
64	-1.31720E-01	-2.49735E-01	2.80255E 00
65	-1.26115E-01	2.22894E-01	2.80255E 00
66	-1.22514E-01	2.22894E-01	2.80255E 00
67	-1.14904E-01	-1.56195E-01	2.80255E 00
68	-1.09299E-01	-1.56195E-01	2.80255E 00
69	-1.03694E-01	4.88569E-02	2.80255E 00
70	-9.80892E-02	4.88569E-02	2.80255E 00
71	-9.24821E-02	9.59179E-02	2.80255E 00
72	-8.68790E-02	9.59179E-02	2.80255E 00
73 74	-8.12739E-02 -7.56688E-02	-2.70940E-01 -2.70940E-01	2.80255E 00 2.80255E 00
75	-7.00637E-02	4.65489E-01	2.80255E 00
76 76	-8.44586E-02	4.65489E-01	2.80255E 00 2.80255E 00
77	-5.88535E-02	-6.66195E-01	2.80255E 00
78	-5.32484E-02	-6.66195E-01	2.80255E 00
79	-4.76433E-02	8.58214E-01	2.80255E 00
80	-4.20382E-02	8.58214E-01	2.80255E 00
81	-3.64331E-02	-1.02664E 00	2.80255E 00
82	-3.08280E-02	-1.02664E 00	2.80255E 00
83	-2.52229E-02	1.15796E 00	2.80255E 00
84	-1.96178E-02	1.15796E 00	2.80255E 00
85	-1.40127E-02	-1.24139E 00	2.80255E 00
86	-8.40764E-03	-1.24139E 00	2.80255E 00
87	-2.80255E-03	1.27000E 00	2.80255E 00
88	2.80255E-03	1.27000E 00	2.80255E 00
89	8.40764E-03	-1.24139E 00	2.80255E 00
90	1.40127E-02	-1.24139E 00	2.80255E 00
91	1.96178E-02	1.15796E 00	2.80255E 00
92	2.52229E-02	1.15796E 00	2.80255E 00
93	3.08280E-02	-1.02664E 00	2.80255E 00
94	3.64331E-02	-1.02664E 00	2.80255E 00
95	4.20382E-02	8.58214E-01	2.80255E 00
96	4.76433E-02	8.58214E-01	2.80255E 00
97	5.32484E-02	-6.66195E-01	2.80255E 00
98	5.88535E-02	-6.66195E-01	2.80255E 00
99	5.44586E-02	4.65489E-01	2.80255E 00
100	7.00637E-02	4.65489E-01	.2.80255E 00
TRANSDUCER NAME:	ECOMMT BPLN, 152MHZ RIC		DDAUTHO HO
DATE: JAN 20, 1	19/8	SIZE FSCM NO.	
REF DES: MT2	LECTRODE STRIPES. 174	A 05869	1950517
IOTAL NUMBER OF E	ELECTRODE STRIPES: 174	SCALE: NONE	SHEET

	DIM X	DIM Y	DIM S
STRIPE NO.	STRIPE LOCATION	BREAK LOCATION	STRIPE WIDTH
101	7.56688E-02	-2.78940E-01	2.80255E 00
102	8.12739E-02	-2.70940E-01	2.80255E 00
103	8.68790E-02	9.59179E-02	2.80255E 00
104	8.24841E-02	9.59179E-02	2.80255E 00
105	9.80892E-02	4.88569E-02	
106	1.03694E 01		2.80255E 00
107	1.09299E-01	4.88569E-02	2.80255E 00
		-1.56195E-01	2.80255E 00
108	1.14904E-01	-1.56195E-01	2.80255E 00
109	1.20510E-01	2.22894E-01	2.80255E 00
110	1.26115E-01	2.22894E-01	2.80255E 00
111	1.31720E-01	-2.49735E-01	2.80255E 00
112	1.37325E-01	-2.49735E-01	2.80255E 00
113	1.42930E-01	2.41097E-01	2.80255E 00
114	1.48535E-01	2.41097E-01	2.80255E 00
115	1.54140E-01	-2.04175E-01	2.80255E 00
116	1.59745E-01	-2.04175E-01	2.80255E 00
117	1.65350E-01	1.47993E-01	2.80255E 00
118	1.70955E-01	1.47993E-01	2.80255E 00
119	1.76561E-01	-8.23009E-02	2.80255E 00
120	1.82166E-01	-8.23009E-02	2.80255E 00
121	1.87771E-01	1.64351E-02	2.80255E 00
122	1.93376E-01	1.64351E-02	2.80255E 00
123	1.98981E-01	4.16039E-02	2.80255E 00
124	2.04586E-01	4.16039E-02	2.80255E 00
125	2.10191E-01	-8.58824E-02	2.80255E 00
126	2.15796E-01	-8.58824E-02	2.80255E 00
127	2.21401E-01	1.12959E-01	2.80255E 00
128	2.27006E-01	1.12959E-01	2.80255E 00
129	2.32812E-01	-1.21912E-01	2.80255E 00
130	2.38217E-01	-1.21912E-01	2.80255E 00
131	2.43822E-01	1.14181E-01	
132	2.49427E-01		2.80255E 00
133	2.55032E-01	1.14181E-01	2.80255E 00
134	2.60637E-01	-8.30731E-02	2.80255E 00
135		-9.30731E-02	2.80255E 00
	2.66242E-01	6.30999E-02	2.80255E 00
136	2.71847E-01	6.30999E-02	2.80255E 00
137	2.77452E-01	-2.93040E-02	2.80255E 00
138	2.83057E-01	-2.93040E-02	2.80255E 00
139	2.88662E-01	-3.49758E-03	2.80255E 00
140	2.94268E-01	-3.49758E-03	2.80255E 00
141	2.99873E-01	3.12725E-02	2.80255E 00
142	3.05478E-01	3.12725E-02	2.80255E 00
143	3.11083E-01	-5.11213E-02	2.80255E 00
144	3.16688E-01	-5.11213E-02	2.80255E 00
145	3.22293E-01	6.16051E-02	2.80255E 00
146	3.27898E-01	6.16051E-02	2.80255E 00
147	3.33503E-01	-6.26706E-02	2.80255E 00
148	3.39108E-01	-6.26706E-02	2.80255E 00
149	3.44714E-01	5.55041E-02	2.80255E 00
150	3.50319E-01	5.55041E-02	2.80255E 00
TO \$1100110FF			
	ECOMMT BPLN, 152MHZ RIC		DOMITHO NO TELL
DATE: JAN 20, 197	8	SIZE FSCM NO.	DRAWING NO. REV
REF DES: MT2	CTROPE CTRIPEC. 174	A 05869	1950517
TOTAL NUMBER OF ELE	CTRODE STRIPES: 174	SCALE: NONE	SHEET 11

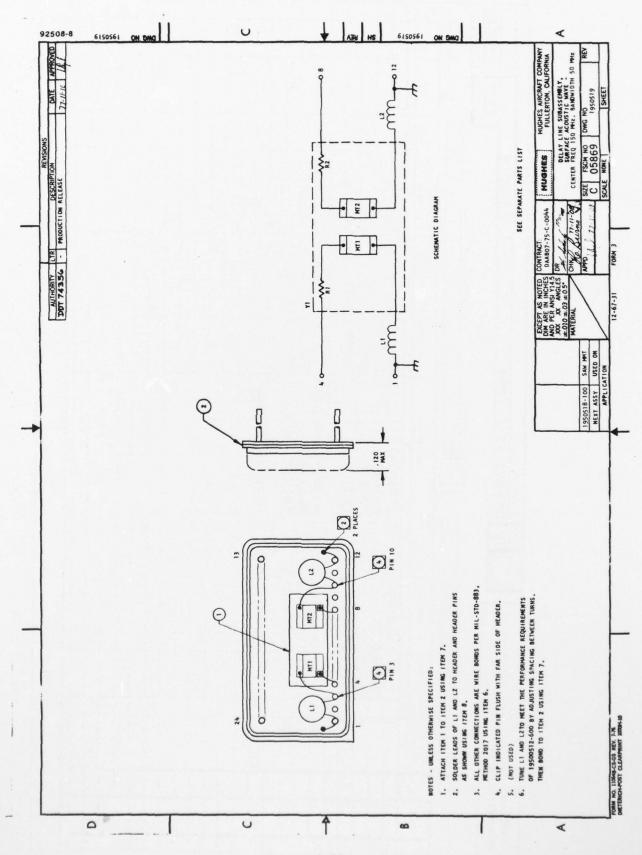
		RFV	N .	12
DIM S STRIPE WIDTH	2.80255E 00	DRAWING NO.	1950517	SHEET
		FSCM NO	05869	NONE
DIM Y BREAK LOCATION	-4.22757E-02 2.55206E-02 2.55206E-02 -7.89812E-03 -7.89812E-03 -7.89812E-03 -7.89812E-03 -7.89812E-03 -7.89812E-03 -7.89812E-03 -7.89812E-03 -8.17625E-03 -2.10172E-02 -2.94843E-02 -2.94843E-02 -2.94843E-02 -3.35356E-02 3.35356E-02 3.35221E-02 3.25221E-02 3.25221E-02 3.25221E-02 3.25221E-02 3.25221E-02 3.15138E-02 3.25221E-02 5.72935E-02	. ST7F	S12E A	SCALE:
BREAK	4.4.9.9.4.6.8.8.8.8.8.8.8.8.8.8.8.8.8.8.8.8.8.8	TRANSDUCER		
DIM X STRIPE LOCATION		ECOMMT BPLN, 152MHZ RICE TR	9/10	ELECTRODE STRIPES: 174
STRIPE NO.		DUCER NAME:	REF DES MT2	BER OF

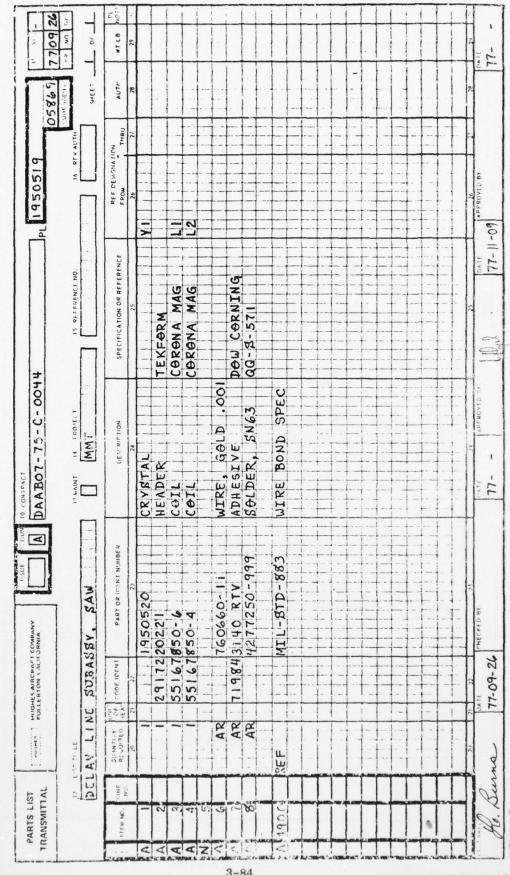






TRANSMITTAL	HUGHES AIRCRAFT COMPANY FULLERTON, CALIFORNIA	LIFORNIA A	DAABO7-75-C-0044		PL 1950518-100		1 A
12	LIST TITLE			15 REFERENCE NO.	O 5	17 200E 10F N 1 YE	77 09 23
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TEM NO. LINE	QUANTITY OF CODE IDENT	PART OR IDENT NUMBER	DESCRIPTION	SPECIFICATION OR REFERENCE	REF DESIGNATION	, нти	WT LB BOI
Ī	20	23	24	25	H	28	22 10
A		1950519	SUBASSY			1	1
V 2		29 17220216	COVER	TEKFORM			
	AR	4277250-996		QQ-8-571			
-							
7440C	REF	1950519	SCHEMATIC DIAG				
1001	REF	1950512-600	DESGN PERF SPEC				
2065	REF	P80-3					-
wat to							
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	26 21 22	23	2.4	25	3.	67.	200
Ho Runs	77-09-73	CHECKED BY	77 - 77	100 POTE 11.09	AFFRICATIONS	1 LV 2	





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APPROVED DATE 13.06-REVISIONS PRODUCTION RELEASE DESCRIPTION AUTHORITY LTR DDI 86948 QUARTZ MATERIAL NOTES:

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1. MATERIAL: QUARTZ PER 760781

2. FABRICATE PER 780294

3. DEPOSITION THICKNESS: 0.20 +0.01 µm (2000 +100 R) STALLINE AXIS & PROPAGATION DIRECTION.

SHORIZONTAL CENTERLINES OF MT1 &

HORIZONTAL CENTERLINES OF MT1 & MT2 SHALL BE CO-LINEAR WITHIN AND PARALLEL TO X-AXIS WITHIN 0.25°.

6. IN DIMENSIONAL LISTINGS, THE NO. FOLLOWING THE LETTER E INDICATES THE POWER OF 10 BY WHICH THE NO. MUST BE MULTIPLIED TO OBTAIN THE CORRECT VALUE. FOR EXAMPLE:

1.45870E-02 = 1.45870 × 10<sup>-2</sup> = 0.014

1.45870E-02 = 1.45870  $\times$  10<sup>-2</sup> = 0.014587 1.34567E 00 = 1.34567  $\times$  10<sup>0</sup> = 1.34567 DEPOSITION FILM APPLIED IN INDICATED AREA. BACK SURFACE TO BE ROUGHENED WITH #180 GRIT.

TO BE DETERMINED AT TIME OF FABRICATION.

]o (@)

8

INDICATED SURFACE TO BE CORRUGATED PER P82

FRAGILE ITEM (EASILY DAMAGED BY HANDLING) to be installed in next assembly at point of manufacture. METRIC
THIRD ANGLE
(AMERICAN) PROJECTION



DAABO7-75C-0044

DAABO7-75C-0044

DABABO7-75C-0044

CRYSTAL, SURFACE ACOUSTIC WAVE CHK

CHK

SIZE FSCM NO. DWG NO.

SIZE FSCM NO.

DAGHES AIRCRAFT COMPANY
FULLERTON, CALIFORNIA
FOLLERTON, CALIFORNIA
FOLLERTON, CALIFORNIA
FOLHOWING
MANAGEMENT

OF STATE

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DIMENSIONS ARE MILLIMETERS &

Z

PER ANSI Y14.5

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UNLESS OTHERWISE

20

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SHEET 1

3

SCALE NONE

+20

ANGLES

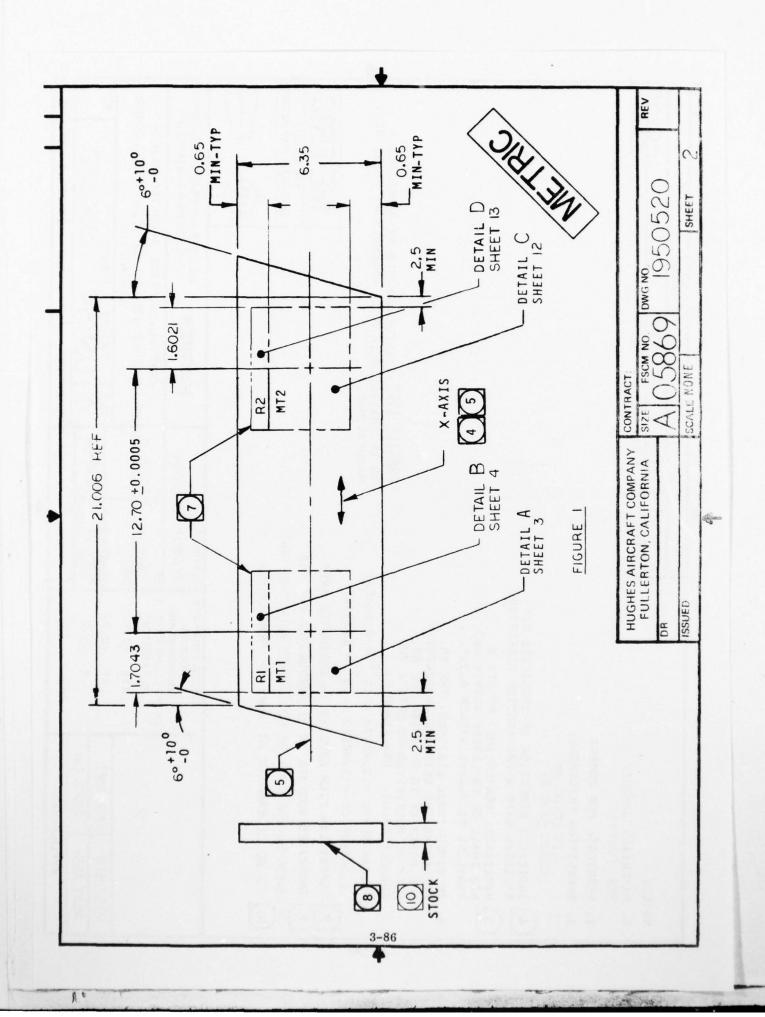
+0.5

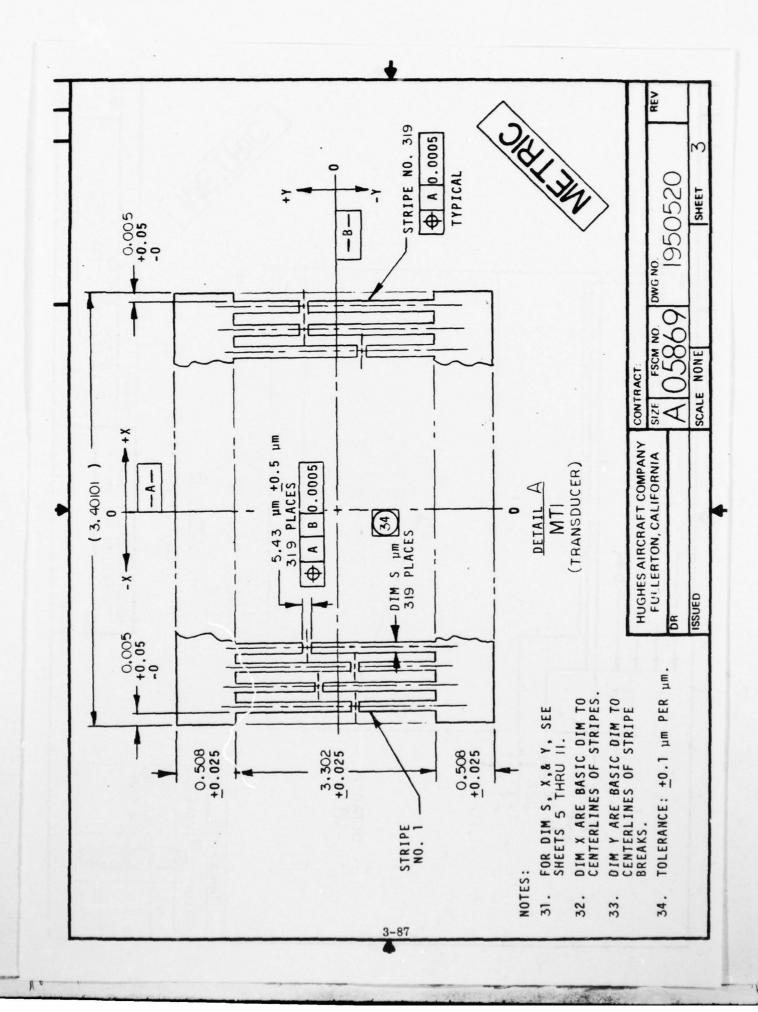
USED ON

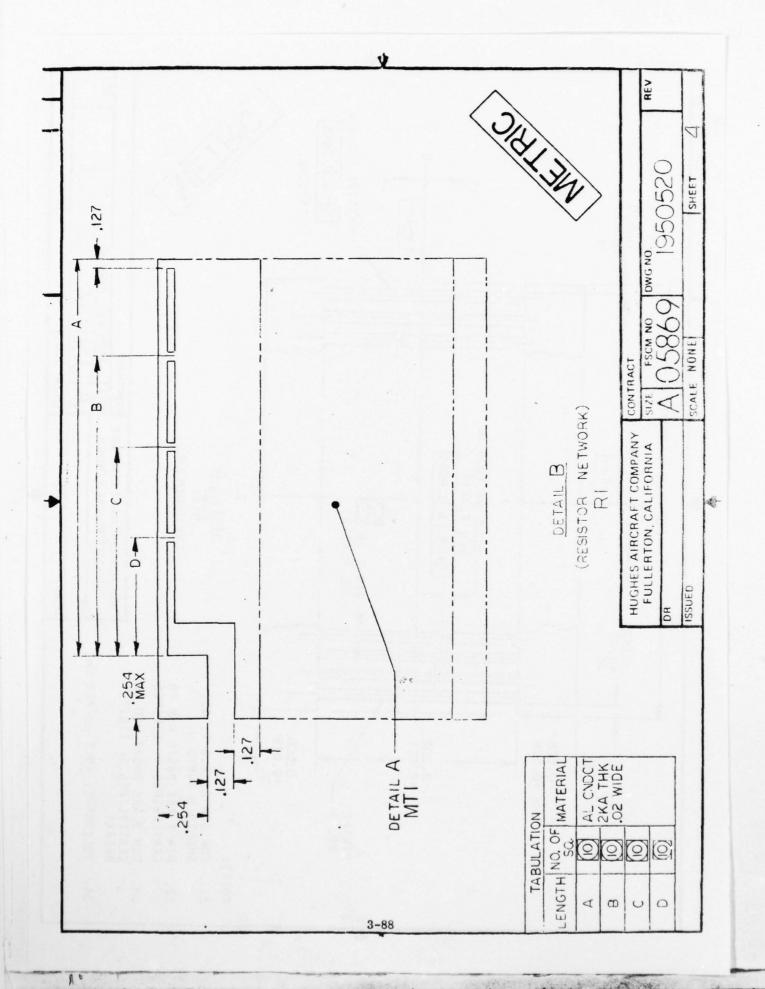
950519 NEXT ASSY **APPLICATION** 

SAW-MMT

3-85







STRIPE NO.	DIM X STRIPE LOCATION	DIM Y BREAK LOCATION	DIM S STRIPE WIDTH
1	-1.67240E 00	1.16066E-05	6.38666E 00
2	-1.65963E 00	-9.24131E-04	6.37627E 00
3	-1.84689E 00	6.90036E-03	6.36592E 00
3 4	-1.63417E 00	-2.52713E-02	6.35563E 00
5	-1.62147E 00	6.48206E-02	6.34539E 00
6	-1.63879E 00	-1.33777E-01	6.33520E 00
7	-1.59613E 00	2.37680E-01	6.32505E 00
8	-1.58349E 00	-3.77527E-01	
9	-1.57087E 00	5.49154E-01	6.31495E 00
10	-1.55827E 00	<b>-7.42896E-01</b>	6.30491E 00
11	-1.54569E 00		6.29491E 00
12	-1.53313E 00	9.44315E-01	6.28496E 00
13	-1.52059E 00	-1.13620E 00	6.27505E 00
14	-1.50807E 00	1.30075E 00	6.26520E 00
		-1.42184E 00	6.25538E 00
15 16	-1.49557E 00	1.48711E 00	6.24562E 00
	-1.48309E 00	-1.49664E 00	6.23589E 00
17	-1.47062E 00	1.49664E 00	6.22622E 00
18	-1.45818E 00	-1.49664E 00	6.21659E 00
19	-1.44576E 00	1.49664E 00	6.20700E 00
20	-1.43335E 00	-1.49664E 00 ·	6.19746E 00
21 22	-1.42097E 00	1.49664E 00	6.18796E 00
	-1.40860E 00	-1.49664E 00	6.17851E 00
23 24	-1.39625E 00 -1.38392E 00	1.49664E 00	6.16910E 00
25	-1.37161E 00	-1.49664E 00	6.15973E 00
26	-1.35932E 00	1.49664E 00	6.15040E 00
27	-1.34705E 00	-1.49664E 00 1.49664E 00	6.14112E 00
28	-1.33479E 00	-1.49664E 00	6.13188E 00 6.12267E 00
29	-1.32256E 00	1.49664E 00	6.11352E 00
30	-1.31034E 00	-1.49664E 00	6.10440E 00
31	-1.29814E 00	1.49664E 00	6.09532E 00
32	-1.28596E 00	-1.49664E 00	6.08629E 00
33	-1.27380E 00	1.49664E 00	6.07729E 00
34	-1.26165E 00	-1.49664E 00	6.06833E 00
35	-1.24952E 00	1.49664E 00	6.05942E 00
36	-1.23741E 00	-1.49664E 00	6.05054E 00
37	-1.22532E 00	1.49664E 00	6.04170E 00
38	-1.21325E 00	-1.49664E 00	6.03290E 00
39	1 001100 00	1.49664E 00	6.02413E 00
40	-1.18915E 00	-1.49664E 00	6.01541E 00
41	-1.17713E 00	1.49664E 00	6.00672E 00
42	-1.16512E 00	-1.49664E 00	5.99808E 00
43	-1.15313E 00	1.49664E 00	5.98947E 00
44	-1.14116E 00	-1.49644E 00	5.98089E 00
45	-1.12921E 00	1.49664E 00	5.97235E 00
46	-1.11727E 00	-1.49664E 00	5.96385E 00
47	-1.10536E 00	1.49664E 00	5.95539E 00
48	-1.09345E 00	-1.49664E 00	5.94696E 00
49	-1.08157E 00	1.49664E 00	5.93856E 00
50	-1.06976E 00	-1.49664E 00	5.93020E 00
	ECOMMT PCQ, UNAPODIZED 1		DRAUTHO NO
DATE: JAN 18, 197	8	SIZE FSCM NO.	DRAWING NO. F
REF DES: MT1 TOTAL NUMBER OF ELE	CTRODE STRIPES: 319	A 05869 SCALE: NONE	1950520 SHEET
TOTAL HUMBER OF ELE	CINODE SINIFES: 319	SCALE: NONE	SHEET

REV

STRIPE NO.	DIM X STRIPE LOCATIO	DIM Y BREAK LOCATION	DIM S STRIPE WIDTH
51 52 53 54 55 56 57 58 59 60 61 62 63 64 65 66 67 68 69 70 71 72 73 74 75 76 77 78 79 80 81 82 83 84 85 86 87 88 89 90 91 92 93 94 95 96 97 97 98 99 100 71 97 98 99 90 90 91 91 92 93 94 95 96 97 97 97 97 97 97 97 97 97 97 97 97 97	-1.05785E 00 -1.04601E 00 -1.03419E 00 -1.02239E 00 -1.01060E 00 -9.98834E-01 -9.87081E-01 -9.75344E-01 -9.63623E-01 -9.51918E-01 -9.28555E-01 -9.16898E-01 -9.05257E-01 -8.93631E-01 -8.82021E-01 -8.70427E-01 -8.55848E-01 -8.47284E-01 -8.35736E-01 -8.12687E-01 -8.12687E-01 -7.89698E-01 -7.8926E-01 -7.66769E-01 -7.55328E-01 -7.43901E-01 -7.55328E-01 -7.43901E-01 -7.55328E-01 -7.66769E-01 -7.55328E-01 -7.66769E-01 -7.55328E-01 -7.66769E-01 -7.55328E-01 -7.66769E-01 -7.55328E-01 -7.43901E-01 -6.98343E-01 -6.98343E-01 -6.98343E-01 -6.9926E-01 -5.563060E-01 -5.96688E-01		5.92188E 00 5.91360E 00 5.90534E 00 5.89712E 00 5.88894E 00 5.88879E 00 5.87267E 00 5.86459E 00 5.84852E 00 5.84852E 00 5.84954E 00 5.83258E 00 5.80892E 00 5.80110E 00 5.79330E 00 5.77781E 00 5.76245E 00 5.76245E 00 5.74721E 00 5.75481E 00 5.73962E 00 5.73208E 00 5.73208E 00 5.74721E 00 5.76245E 00 5.76476E 00 5.7656547E 00 5.66547E 00 5.66547E 00 5.66547E 00 5.65098E 00 5.65098E 00 5.62233E 00 5.63660E 00 5.62233E 00 5.63660E 00 5.63660E 00 5.63660E 00 5.63660E 00 5.63660E 00 5.65098E 00
TOTAL NUMBER OF E	LECTRODE STRIPES:	319 SCALE:	NONE SHEET 6

STRIPE NO.	DIM X STRIPE LOCATION	DIM Y BREAK LOCATION	DIM S STRIPE WIDTH
101	-4.85083E-01	1.49664E 00	5.54574E 00
102	-4.73998E-01	-1.49664E 00	5.53893E 00
103	-4.62927E-01	1.49664E 00	5.53215E 00
104	-4.51869E-01	-1.49664E 00	5.52539E 00
105	-4.40825E-01	1.49664E 00	5.51865E 00
106	-4.29795E-01	-1.49664E 00	5.51195E 00
107	-4.18777E-01	1.49664E 0U	5.50526E 00
108	-4.07773E-01	-1.49664E 00	5.49860E 00
109	-3.96783E-01	1.49664E 00	5.49196E 00
110	-3.85806E-01	-1.49664E 00	5.48534E 00
111	-3.74842E-01	1.49664E 00	5.47876E 00
112	-3.63891E-01	-1.49664E 00	5.47220E 00
113	-3.52953E-01	1.49664E 00	5.46565E 00
114	-3.42028E-01	-1.49664E 00	5.45913E 00
115	-3.31116E-01	1.49664E 00	5.45264E 00
116	-3.20217E-01	-1.49664E 00	5.44617E 00
117 118	-3.09331E-01 -2.98458E-01	1.49664E 00 -1.49664E 00	5.43972E 00
119	-2.87598E-01	1.49664E 00	5.43329E 00
120	-2.76751E-01		5.42689E 00 5.42051E 00
121	-2.65916E-01	-1.49664E 00 1.49664E 00	5.41415E 00
122	-2.55094E-01	-1.49664E 00	5.40781E 00
123	-2.44285E-01	1.49664E 00	5.40150E 00
124	-2.33488E-01	-1.49664E 00	5.39521E 00
125	-2.22704E-01	1.49664E 00	5.38894E 00
126	-2.11932E-01	-1.49664E 00	5.38269E 00
127	-2.01173E-01	1.49664E 00	5.37646E 00
128	-1.90427E-01	-1.49664E 00	5.37026E 00
129	-1.79692E-01	1.49664E 00	5.36407E 00
130	-1.68970E-01	-1.49664E 00	5.35791E 00
131	-1.58260E-01	1.49664E 00	5.35177E 00
132	-1.47563E-01	-1.49664E 00	5.34565E 00
133	-1.36878E-01	1.49664E 00	5.33955E 00
134	-1.26205E-01	-1.49664E 00	5.33348E 00
135	-1.15544E-01	1.49664E 00	5.32742E 00
136	-1.04895E-01	-1.49664E 00	5.32138E 00
137	-9.42584E-01	1.49664E 00	5.31537E 00
138	-8.36336E-01	-1.49664E 00	5.30937E 00
139	-7.30209E-02	1.49664E 00	5.30339E 00
140	-6.24200E-02	-1.49664E 00	5.29744E 00
141	-5.18311E-02	1.49664E 00	5.29150E 00 5.28559E 00
142 143	-4.12540E-02 -3.06887E-02	-1.49664E 00 1.49664E 00	5.27969E 00
144	-2.01352E-02	-1.49664E 00	5.27382E 00
145	-9.59342E-03	1.49664E 00	5.26796E 00
146	9.36670E-04	-1.49664E 00	5.26213E 00
147	1.14551E-02	1.49664E 00	5.25631E 00
148	2.19619E-02	-1.49664E 00	5.25051E 00
149	3.24572E-02	1.49664E 00	5.24473E 00
150	4.29409E-02	-1.49664E 00	5.23897E 00
TRANSDUCER NAME:	ECOMMT PCQ, UNAPODIZED TR	RANSDUCER	

TRANSDUCER NAME: ECOMMT PCQ, UNAPODIZED TRANSDUCER
DATE: JAN 18, 1978

REF DES: MT1

TOTAL NUMBER OF ELECTRODE STRIPES: 319

SIZE FSCM NO. DRAWING NO. REV
A 05869 1950520
SCALE: NONE SHEET 7

STRIPE NO.	DIM X STRIPE LOCATION	DIM Y BREAK LOCATION	DIM S STRIPE WIDTH
151 152	5.34131E-02 6.38738E-02	1.49664E 00 -1.49664E 00	5.23323E 00
			5.22751E 00
153	7.43231E-02	1.49664E 00	5.22180E 00
154	8.47610E-02	-1.49664E 00	5.21612E 00
155	9.51876E-02 1.05603E-01	1.49664E 00	5.21045E 00
156 157		-1.49664E 00	5.20480E 00
158	1.16007E-01 1.26400E-01	1.49664E 00	5.19917E 00
159	1.36781E-01	-1.49664E 00 1.49664E 00	5.19356E 00
160	1.47151E-01	-1.49664E 00	5.18797E 00
161	1.57511E-01	1.49664E 00	5.18239E 00 5.17683E 00
162	1.67859E-01	-1.49664E 00	5.17635E 00 5.17130E 00
163	1.78196E-01	1.49664E 00	5.16577E 00
164	1.88522E-01	-1.49664E 00	5.16027E 00
165	1.98837E-01	1.49664E 00	5.15478E 00
166	2.09141E-01	-1.49664E 00	5.14931E 00
167	2.19434E-01	1.49664E 00	5.14386E 00
168	2.29717E-01	-1.49664E 00	5.13843E 00
169	2.39988E-01	1.49664E 00	5.13301E 00
170	2.50249E-01	-1.49664E 00	5.12761E 00
171	2.60498E-01	1.49664E 00	5.12222E 00
172	2.70738E-01	-1.49664E 00	5.11686E 00
173	2.80966E-01	1.49664E 00	5.11151E 00
174	2.91184E-01	-1.49664E 00	5.10618E 00
175	3.01391E-01	1.49664E 00	5.10086E 00
176	3.11587E-01	-1.49664E 00	5.09556E 00
177	3.21773E-01	1.49664E 00	5.09028E 00
178	3.31948E-01	-1.49664E 00	5.08501E 00
179	3.42113E-01	1.49664E 00	5.07976E 00
180	3.52267E-01	-1.49664E 00	5.07453E 00
181	3.62411E-01	1.49664E 00	5.06931E 00
182	3.72545E-01	-1.49664E 00	5.06411E 00
183	3.82668E-01	1.49664E 00	5,05892E 00
184 185	3.92780E-01	-1.49664E 00	5.05375E 00
186	4.02883E-01 4.12975E-01	1.49664E 00 -1.49664E 00	5.04860E 00 5.04346E 00
187	4.12975E-01 4.23056E-01	1.49664E 00	5.03834E 00
188	4.33128E-01	-1.49664E 00	5.03323E 00
189	4.43189E-01	1.49664E 00	5.02814E 00
190	4.53241E-01	-1.49664E 00	5.02306E 00
191	4.63282E-01	1.49664E 00	5.01800E 00
192	4.73313E-01	-1.49664E 00	5.01295E 00
193	4.83334E-01	1.49664E 00	5.00792E 00
194	4.93344E-01	-1.49664E 00	5.00291E 00
195	5.03345E-01	1.49664E 00	4.99791E 00
196	5.13336E-01	-1.49664E 00	4.99292E 00
197	5.23317E-01	1.49664E 00	4.98795E 00
198	5.33288E-01	-1.49664E 00	4.98300E 00
199	5.43249E-01	1.49664E 00	4.97805E 00
200	5.53200E-01	-1.49664E 00	4.97313E 00
TRANSDUCER	NAME: ECOMMT PCQ, UNAPODIZED	TRANSDUCER	

TRANSDUCER NAME: ECOMMT PCQ, UNAPODIZED TRANSDUCER DATE: JAN 18, 1978
REF DES: MT1
TOTAL NUMBER OF ELECTRODE STRIPES: 319 SIZE FSCM NO. A 05869 SCALE: NONE

DRAWING NO. 1950520 SHEET REV 8

STRIPE NO.	DIM X STRIPE LOCATION	DIM Y BREAK LOCATION	DIM S STRIPE WIDTH
201 202 203 204 205 206 207 208 209 210 211 212 213 214 215 216 217 218 219 220 221 222 223 224 225 226 227 228 229 230 231 232 244 225 226 227 228 229 230 231 232 244 245 240 241 242 243 244 245 246 247 248 249 240 241 242 243 244 245 246 247 248 249 240 241 242 243 244 245 246 247 248 249 240 241 242 243 244 245 246 247 248 249 240 241 242 243 244 245 246 247 248 249 240 241 242 243 244 245 246 247 248 249 240 241 242 243 244 245 246 247 248 249 240 241 242 243 244 245 246 247 248 249 249 240 241 242 243 244 245 246 247 248 249 240 241 246 247 248 249 249 240 241 246 247 248 249 249 240 240 241 240 241 240 241 240 241 240 241 242 243 244 245 246 247 248 249 240 240 241 242 243 244 245 246 247 248 249 240 240 241 242 243 244 245 246 247 248 249 240 240 241 242 243 244 245 246 247 248 249 249 240 240 241 242 243 244 245 246 247 248 249 249 240 240 240 240 240 240 240 240 240 240	5.83141E-01 5.73073E-01 5.82995E-01 5.92907E-01 6.82809E-01 6.12702E-01 6.22585E-01 6.32458E-01 6.42322E-01 6.52176E-01 6.62028E-01 6.71855E-01 6.81681E-01 6.91497E-01 7.01303E-01 7.11101E-01 7.20888E-01 7.30667E-01 7.40436E-01 7.59946E-01 7.59946E-01 7.59946E-01 7.69888E-01 7.79429E-01 7.89142E-01 7.89856E-01 8.08561E-01 8.18256E-01 8.37619E-01 8.37619E-01 8.37619E-01 8.376238E-01 8.56947E-01 8.66597E-01 8.66597E-01 8.76238E-01 8.76238E-01 9.31474E-01 9.33898E-01 9.43477E-01 9.53047E-01 9.53047E-01 9.53047E-01 9.53047E-01 9.53047E-01 9.14714E-01 9.24310E-01 9.14714E-01 9.24310E-01 9.14714E-01 9.24310E-01 9.14714E-01 9.24310E-01 9.14714E-01 9.24310E-01 9.14714E-01 9.24310E-01 9.14714E-01 9.14714E-01 9.24310E-01	1.49664E 00 -1.49664E 00	4.96822E 00 4.96332E 00 4.96332E 00 4.95357E 00 4.94871E 00 4.94387E 00 4.93905E 00 4.93424E 00 4.92944E 00 4.91531E 00 4.91531E 00 4.90055E 00 4.89625E 00 4.89625E 00 4.89625E 00 4.88688E 00 4.88688E 00 4.88688E 00 4.86371E 00 4.86371E 00 4.86371E 00 4.86832E 00 4.8757E 00 4.8757E 00 4.87294E 00 4.86832E 00 4.86371E 00 4.87294E 00 4.86832E 00 4.86371E 00 4.8731E 00 4.7857E 00 4.7857E 00 4.79612E 00 4.79612E 00 4.77857E 00
TRANSDUCER NAME: EL DATE: JAN 18, 1978 REF DES: MTI TOTAL NUMBER OF ELEC		SIZE FSCM No. A 05869	DRAWING NO. 1950520 SHEET

Ne

STRIPE NO.	DIM X STRIPE LOCATION	DIM Y BREAK LOCATION	DIM S STRIPE WIDTH
251 252 253 254 255 256 257 258 259 260 261 262	1.04827E 00 1.05775E 00 1.06721E 00 1.07667E 00 1.08612E 00 1.09556E 00 1.10500E 00 1.11442E 00 1.12384E 00 1.13325E 00 1.14265E 00 1.15204E 00	1.49664E 00 -1.49664E 00 1.49664E 00 -1.49664E 00	4.73978E 00 4.73552E 00 4.73128E 00 4.72705E 00 4.72283E 00 4.71863E 00 4.71443E 00 4.71025E 00 4.70607E 00 4.70191E 00 4.69775E 00 4.69362E 00
263 264 265 266 267 268 269 270 271	1.16142E 00 1.17080E 00 1.18016E 00 1.18952E 00 1.19887E 00 1.20821E 00 1.21755E 00 1.22687E 00 1.23619E 00	1.49664E 00 -1.49664E 00 1.49664E 00 -1.49664E 00 -1.49664E 00 -1.49664E 00 -1.49664E 00 -1.49664E 00	4.68948E 00 4.68537E 00 4.68126E 00 4.67716E 00 4.67307E 00 4.66900E 00 4.66494E 00 4.66088E 00 4.65683E 00
272 273 274 275 276 277 278 279 280	1.24550E 00 1.25480E 00 1.26409E 00 1.27338E 00 1.28266E 00 1.29193E 00 1.30119E 00 1.31044E 00 1.31969E 00	-1.49664E 00 1.49664E 00 -1.49664E 00 1.49664E 00 -1.49664E 00 -1.49664E 00 -1.49664E 00 -1.49664E 00	4.65280E 00 4.64878E 00 4.64477E 00 4.64076E 00 4.63677E 00 4.63279E 00 4.62882E 00 4.62485E 00 4.62091E 00
281 282 283 284 285 286 287 288	1.32893E 00 1.33816E 00 1.34738E 00 1.35659E 00 1.36580E 00 1.37500E 00 1.38419E 00 1.39337E 00	1.49664E 00 -1.49664E 00 1.49664E 00 -1.49664E 00 1.49664E 00 -1.49664E 00 -1.49664E 00	4.61696E 00 4.61303E 00 4.60911E 00 4.60520E 00 4.60130E 00 4.59741E 00 4.59353E 00 4.58966E 00
289 290 291 292 293 294 295 296 297	7.40855E 00 1.41172E 00 1.42088E 00 1.43003E 00 1.43917E 00 1.44831E 00 1.45744E 00 1.46656E 00 1.47567E 00	1.49664E 00 -1.49664E 00 1.49664E 00 -1.49664E 00 -1.49664E 00 -1.49664E 00 -1.49664E 00 -1.49664E 00 1.49664E 00	4.58579E 00 4.58194E 00 4.57810E 00 4.57427E 00 4.57044E 00 4.56663E 00 4.56283E 00 4.55903E 00 4.55525E 00
298 299 300 TRANSFER NAME:	1.48478E 00 1.49388E 00 1.50297E 00 ECOMMT PCQ, UNAPODIZED TRA	-1.49664E 00 1.49122E 00 -1.45565E 00	4.55147E 00 4.54770E 00 4.54395E 00

TRANSFER NAME: ECOMMT PCQ, UNAPODIZED TRANSDUCER

DATE: JAN 18, 1978

REF DES: MT1

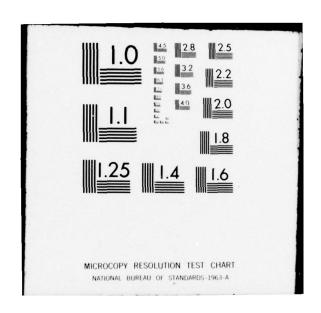
TOTAL NUMBER OF ELECTRODE STRIPES: 319

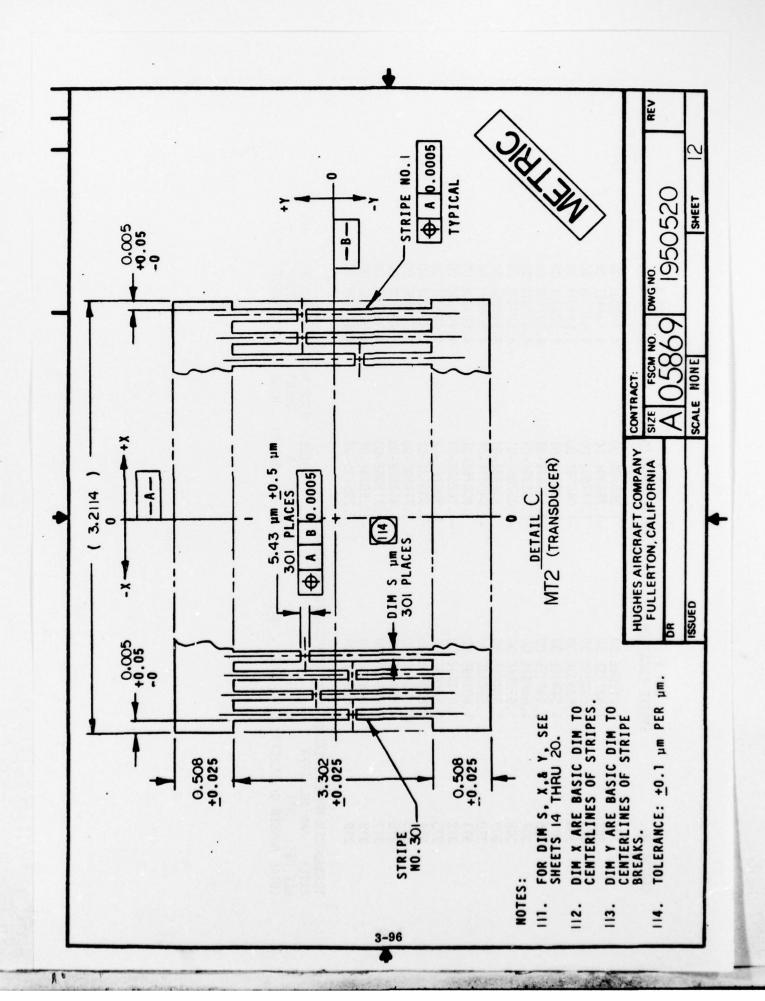
SIZE FSCM NO. DRAWING NO. REV
A 05869 1950520

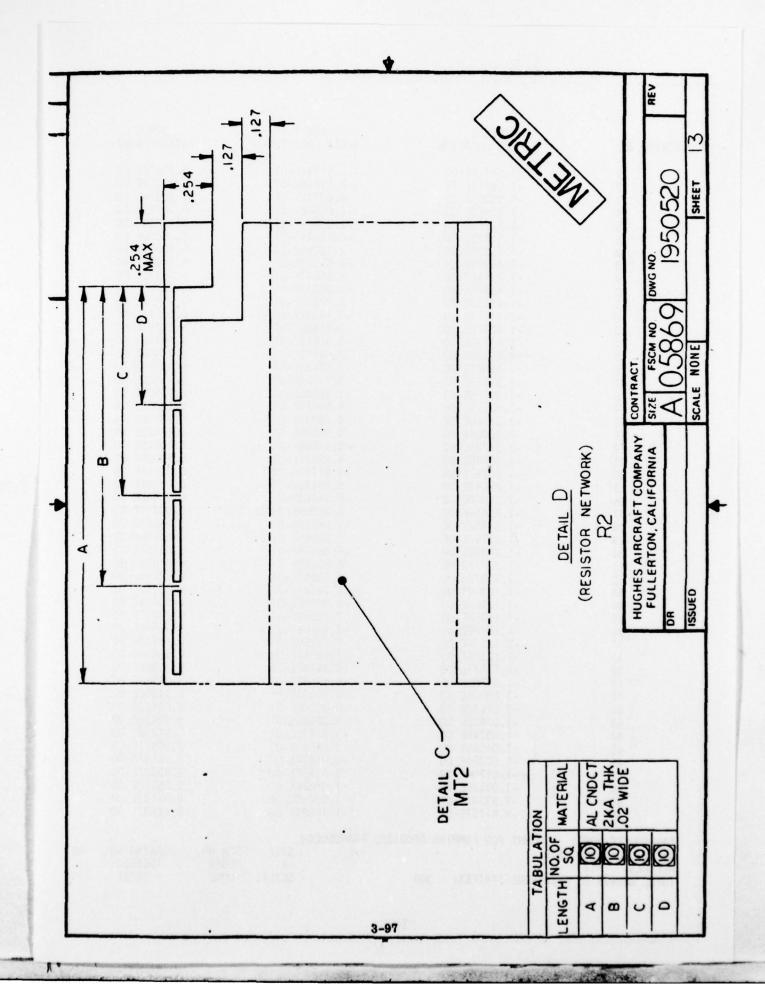
SCALE: NONE SHEET 10

		REV 11
DIM S STRIPE WIDTH 4.54020E 00 4.53273E 00 4.52901E 00 4.52530E 00 4.51791E 00 4.51792E 00 4.51055E 00 4.50689E 00		DRAWING NO. 1950520 SHEET
		FSCM NO. 05869 NONE
DIM Y BREAK LOCATION 1.38878E 00 -1.29439E 00 1.17763E 00 -1.04469E 00 8.02266E-01 -7.57184E-01 6.15825E-01 -4.83785E-01 3.65494E-01 1.80876E-01	-1.16260E-01 6.90074E-02 -3.69312E-02 1.71460E-02 -6.4527E-03 1.71398E-03 -2.25074E-04 2.29517E-06	TRANSDUCER SIZE A A SCALE:
DIM X STRIKE LOCATION 1.51206E 00 1.53020E 00 1.53926E 00 1.54832E 00 1.55737E 00 1.5574E 00 1.5544E 00 1.59348E 00 1.59348E 00		ECOMMT PCQ, UNAPODIZED 1978  ELECTRODE STRIPES: 319
301 302 302 303 304 305 305 306 307 309 310	312 313 314 315 316 318 219	TRANSDUCER NAME: EC DATE: JAN 18, 1978 REF DES: MT1 TOTAL NUMBER OF ELECT

-	AD-A064 197 HUGHES AIRCRAFT CO FULLERTON CALIF GROUND SYSTEMS GROUP F/G 9/5 PHOTOLITHOGRAPHIC TECHNIQUES FOR SURFACE ACOUSTIC WAVE (SAW) DEETC(U) DEC 78 A W DOZIER UNCLASSIFIED FR-79-12-40-VOL-1 DELET-TR-75-0044-F-VOL-1 NL												
		3 of 4 AD64197				000 19 V	RACE TO WIL		Billion and	0 P 0 P 0 D 0 D		ř Lik	100
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		· marketing			0.00	*							







STRIPE NO.	DIM X STRIPE LOCATION	DIM Y BREAK LOCÁTION	DIM S STRIPE WIDTH
1	-1.57775E 00	2.61195E-01	6.31014E 00
	-1.56514E 00	-2.61718E-01	6.30012E 00
2 3 4	-1.55255E 00	2.63172E-01	6.29014E 00
4	41.53998E 00	-2.65546E-01	6.28022E 00
5	-1.52742E 00	2.68829E-01	6.27034E 00
5 6	-1.51489E 00	-2.73014E-01	6.26050E 00
7	-1.50238E 00	2.78085E-01	6.25072E 00
8	-1.48989E 00	-2.84035E-01	6.24097E 00
9	-1.47742E 00	2.90847E-01	6.23127E 00
10	-1.46496E 00	-2.98511E-01	6.22162E 00
11	-1.45253E 00	3.07012E-01	6.21201E 00
12	-1.44012E 00	-3.16343E-01	6.20245E 00
13 14	-1.42772E 00 -1.41535E 00	3.26480E-01	6.19293E 00
15	-1.40299E 00	-3.37419E-01 3.49145E-01	6.18346E 00
16	-1.39065E 00	-3.61631E-01	6.17402E 00 6.16464E 00
17	-1.37833E 00	3.74883E-01	6.15529E 00
18	-1.36603E 00	-3.88862E-01	6.14599E 00
19	-1.35375E 00 ·	4.03577E-01	6.13672E 00
20	-1.34148E 00	-4.18993E-01	6.12750E 00
21	-1.32924E 00	4.35105E-01	6.11832E 00
22	-1.31701E 00	-4.51886E-01	6.10919E 00
23	-1.30480E 00	4.69335E-01	6.10009E 00
24	-1.29261E 00	-4.87421E-01	6.09104E 00
25	-1.28043E 00	5.06142E-01	6.08202E 00
26	-1.26828E 00	-5.25463E-01	6.07304E 00
27	-1.25614E 00	5.45385E-01 .	6.06411E 00
28	-1.24402E 00	-5.65869E-01	6.05521E 00
29	-1.23192E 00	5.86919E-01	6.04635E 00
30	-1.21984E 00	-6.08518E-01	6.03753E 00
31	-1.20777E 00	6.30628E-01	6.02875E 00
32	-1.19572E 00	-6.53245E-01	6.02001E 00
33 34	-1.18369E 00 -1.17168E 00	6.76356E-01 -6.99918E-01	6.01130E 00 6.00264E 00
35	-1.15968E 00	7.23949E-01	5.99401E 00
36	-1.14770E 00	-7.48404E-01	5.98542E 00
37	-1.13574E 00	7.73280E-01	5.97686E 00
38	-1.12379E 00	-7.98541E-01	5.96834E 00
39	-1.11187E 00	8.24182E-01	5.95986E 00
40	-1.09995E 00	-8.50188E-01	5.95141E 00
41	-1.08806E 00	8.76533E-01	5.94300E 00
42	-1.07618E 00	-9.03206E-01	5.93462E 00
43	-1.07432E 00	9.30185E-01	5.92628E 00
44	-1.05248E 00	-9.57432E-01	5.91798E 00
45	-1.04065E 00	9.84960E-01	5.90971E 00
46	-1.02884E 00	-1.01274E 00	5.90147E 00
47	-1.01704E 00	1.04075E 00	5.89327E 00
48	-1.00526E 00	-1.06898E 00	5.88510E 00
49	-9.93503E-01	1.09739E 00	5.87697E 00
50	-9.81757E-01	-1.12599E 00	5.86887E 00
TRANSDUCER NAME:	ECOMMT PCQ FAMMING APODI	ZED TRANSDUCER SIZE FSCM	NO. DRAWING NO.
DATE: JAN 18, 19 REF DES: MT2	3/0	A 0586	
TOTAL NUMBER OF E	LECTRODE STRIPES: 301	SCALE: NON	

REV

STRIPE NO.	DIM X STRIPE LOCATION	DIM Y BREAK LOCATION	DIM S STRIPE WIDTH
51	-9.70028E-01	1.15474E 00	5.86081E 00
52	-9.58314E-01	-1.18364E 00	5.85277E 00
53	-9.46616E-01	1.21266E 00	5.84477E 00
54	-9.34935E-01	-1.24178E 00	5.83681E 00
55	-9.23269E-01	1.27100E 00	5.82887E 00
56	-9.11619E-01	-1.30029E 00	5.82097E 00
57	-8.99985E-01	1.32963E 00	5.81310E 00
58	-8.88367E-01	-1.35901E 00	5.80526E 00
59	-8.76764E-01	1.38842E 00	5.79745E 00
60	-8.65177E-01	-1.41781E 00	5.78967E 00
61	-8.53605E-01	1.44720E 00	5.78193E 00
62	-8.42049E-01	-1.47656E 00	5.77421E 00
63	-8.30509E-01	1.50588E 00	5.76653E 00
64	-8.18983E-01	-1.53512E 00	5.75888E 00
65	-8.07473E-01	1.56430E 00	5.75126E 00
66	-7.95978E-01	-1.59338E 00	5.74367E 00
67	-7.84498E-01	1.62234E 00	5.73611E 00
68	-7.73034E-01	-1.65119E 00	5.72858E 00
69	-7.61584E-01	1.67990E 00	5.72107E 00
70	-7.50149E-01	-1.70846E 00 .	5.71360E 00
71	-7.38729E-01	1.73684E 00	5.70616E 00
72	-7.27325E-01	-1.76503E 00	5.69874E 00
73	-7.15935E-01	1.79304E 00	5.69136E 00
74	-7.04559E-01	-1.82083E 00	5.68400E 00
75	-6.93198E-01	1.84838E 00	5.67667E 00
76	-6.81862E-01	-1.87571E 00	5.66937E 00
77	-6.70521E-01	1.90278E 00	5.66209E 00
78	-6.59204E-01	-1.92958E 00	5.65485E 00
79	-6.47902E-01	1.95611E 00	5.64764E 00
80	-6.36613E-01	-1.98233E 00	5.64045E 00
81	-6.25340E-01	2.00826E 00	5.63329E 00
82	-6.14080E-01	-2.03389E 00	5.62615E 00
83	-6.02835E-01	2.05918E 00	5.61905E 00
84	-5.91604E-01	-2.08413E 00	5.61196E 00
85	-5.80387E-01	2.10872E 00	5.60491E 00
86	-5.69184E-01	-2.13296E 00	5.59789E 00
87	-5.57996E-01 -5.46821E-01	2.15683E 00	5.59088E 00
88 89	-5.35660E-01	-2.18032E 00 2.20343E 00	5.58391E 00 5.57696E 00
90	-5.24513E-01	-2.22611E 00	5.57003E 00
91	-5.13380E-01	2.24839E 00	5.56314E 00
92	-5.02260E-01	-2.27025E 00	5.55627E 00
93	-4.91155E-01	2.29170E 00	5.54942E 00
94	-4.80063E-01	-2.31270E 00	· 5.54259E 00
95	-4.68984E-01	2.33325E 00	5.53580E 00
96	-4.57919E-01	-2.35334E 00	5.52903E 00
97	-4.46868E-01	2.37297E 00	5.52228E 00
98	-4.35830E-01	-2.39213E 00	5.51556E 00
99	-4.24806E-01	2.41083E 00	5.50887E 00
100	-4.13795E-01	-2.42902E 00	5.50219E 00
TRANSDUCER NAME:	ECOMMT PCQ FAMMING APODIA		
DATE: JAN 18, 1 REF DES: MT2	1978	SIZE	FSCM NO. DRAWING NO. 05869 1950520
	ELECTRODE STRIPES: 301	SCALE:	NONE SHEET

REV

15

STRIPE NO.	DIM X STRIPE LOCATION	DIM Y BREAK LOCATION	DIM S STRIPE WIDTH
101	-4.02797E-01	2 446745 00	E 405545 00
102	-3.91813E-01	2.44674E 00 -2.46396E 00	5.49554E 00
103	-3.80841E-01	2.48067E 00	5.48892E 00
104	-3.69883E-01	-2.49687E 00	5.48232E 00
105	-3.58938E-01	2.51257E 00	5.47574E 00
106	-3.4800-E-01	-2.52774E 00	5.46919E 00
107	-3.37088E-01	2.54239E 00	5.46266E 00 5.45616E 00
108	-3.26182E-01	-2.55651E 00	5.44967E 00
109	-3.15289E-01	2.57010E 00	5.44321E 00
110	-3.04409E-01	-2.58315E 00	5.43677E 00
iii	-2.93542E-01	2.59566E 00	5.43036E 00
112	-2.82687E-01	-2.60763E 00	5.42397E 00
113	-2.71846E-01	2.61905E 00	5.41760E 00
114	-2.61017E-01	-2.62992E 00	5.41125E 00
115	-2.50201E-01	2.64024E 00	5.40492E 00
116	-2.39397E-01	-2.65000E 00	5.39863E 00
117	-2.28606E-01	2.65921E 00	5.39234E 00
118	-2.17828E-01	-2.66785E 00	5.38608E 00
119	-2.07062E-01	2.67594E 00	5.37985E 00
120	-1.96308E-01	-2.68346E 00 ·	5.37363E 00
121	-1.85567E-01	2.69043E 00	5.36744E 00
122	-1.74839E-01	-2.69683E 00	5.36127E 00
123	-1.64122E-01	2.70266E 00	5.35512E 00
124	-1.53418E-01	-2.70794E 00	5.34898E 00
125	-1.42726E-01	2.71264E 00	5.34287E 00
126	-1.32047E-01	-2.71679E 00	5.33679E 00
127	-1.21379E-01	2.72037E 00	5.33072E 00
128	-1.10724E-01	-2.72339E 00	5.32467E 00
129	-1.00080E-01	2.72585E 00	5.31864E 00
130	-8.94491E-02	-2.72775E 0Ò	5.31264E 00
131	-7.88298E-02 -6.82225E-02	2.72909E 00 -2.72988E 00	5.30665E 00 5.30069E 00
132 133	-5.76270E-02	2.73011E 00	5.29474E 00
134	-4.70435E-02	-2.73017E 00	5.28882E 00
135	-3.64717E-02	2.72892E 00	5.28292E 00
136	-2.59118E-02	-2.72751E 00	5.27703E 00
137	-1.53636E-02	2.72555E 00	5.27116E 00
138	-4.82711E-03	-2.72305E 00	5.26531E 00
139	5.69770E-03	2.72002E 00	5.25949E 00
140	1.62109E-02	-2.71645E 00	5.25368E 00
141	2.67125E-02	2.71235E 00	5.24789E 00
142	3.72025E-02	-2.70773E 00	5.24212E 00
143	4.76810E-02	2.70258E 00	5.23638E 00
144	5.81480E-02	-2.69692E 00	5.23064E 00
145	6.86036E-02	2.69074E 00	5.22493E 00
146	7.90477E-02	-2.68405E 00	5.21924E 00
147	8.94805E-02	2.67687E 00	5.21356E 00
148	9.99020E-02	-2.66919E 00	5.20790E 00
149	1.10312E-01	2.66100E 00	5.20226E 00
150	1.20711E-01	-2.65234E 00	5.19664E 00
TRANSDUCER NAME: DATE: JAN 18, 1	ECOMMT PCQ FAMMING APODI	ZED TRANSDUCER SIZE FSCM NO	. DRAWING NO.
REF DES: MT2	1370	A 05869	1950520
	ELECTRODE STRIPES: 301	SCALE: NONE	SHEET

STRIPE NO.	DIM X STRIPE LOCATION		DIM Y BREAK LOCATI	ION	DIM S STRIPE WIDTH
	1 212225 21		0.640105.6		5 101045 00
151	1.31099E-01		2.64319E (		5.19104E 00
152	1.41475E-01		-2.63357E		5.18545E 00
153	1.51841E-01		2.62348E (		5.17989E 00
154	1.62195E-01		-2.61292E		5.17434E 00
155	1.72538E-01		2.60191E (		5.16881E 00
156	1.82870E-01		-2.59045E		5.16330E 00
157	1.93191E-01		2.57854E (	00	5.15780E 00
158	2.03501E-01		-2.56619E 0	00	5.15233E 00
159 160	2.13801E-01 2.24089E-01		2.55342E 0 -2.54022E 0		5.14686E 00
161	2.34366E-01		2.52660E (		5.14142E 00 5.13600E 00
162	2.44633E-01		-2.51257E	00	5.13059E 00
163	2.54889E-01		2.49815E		5.12519E 00
164	2.65134E-01		-2.48332E		5.11982E 00
165	2.753 <b>68E-</b> 01		2.46811E		5.11446E 00
166	2.85592E-01		-2.45252E		5.10912E 00
167	2.95805E-01		2.43656E		5.10380E 00
168	3.06007E-01		-2.42024E		5.09849E 00
169	3.16198E-01		2.40355E		5.09320E 00
170	3.26380E-01		-2.38652E		5.08792E 00
171	3.36550E-01		2.36915E		5.08267E 00
172	3.46710E-01		-2.35145E		5.07743E 00
173	3.56860E-01		2.33343E	00	5.07220E 00
174	3.66999E-01		-2.31509E 0		5.06699E 00
175	3.77128E-01		2.29644E C		5.06179E 00
176	3.87246E-01		-2.27749E 0	00	5.05662E 00
177	3.97354E-01		2.25826E 0		5.05146E 00
178	4.07452E-01		-2.23874E 0	00	5.04631E 00
179	4.17540E-01		2.21896E 0		5.04118E 00
180	4.27617E-01		-2.19891E (		5.03606E 00
181	4.37684E-01		2.17860E 0		5.03096E 00
182	4.47741E-01		-2.15805E		5.02588E 00
183 184	4.57787E-01 4.67824E-01		2.13726E 0 -2.11625E 0		5.02081E 00 5.01576E 00
185	4.77850E-01				
186	4.87867E-01		2.09501E ( -2.07356E (		5.01072E 00 5.00570E 00
187	4.97873E-01		2.05191E		5.00069E 00
188	5.07870E-01		-2 03007E		4.99570E 00
189	5.17856E-01		2.00805E		4.99072E 00
190	5.27833E-01		-1.98585E	00	4.98576E 00
191	5.37799E-01		1.96348E (	00	4.98081E 00
192	5.47756E-01		-1.94096E		4.97587E 00
193	5.57703E-01		1.91829E (		4.97096E 00
194	5.67640E-01		-1.89548E (		4.96605E 00
195	5.77567E-01		1.87255E (	00	4.96116E 00
196	5.87484E-01		-1.84949E (	00	4.95629E 00
197	5.97392E-01		1.82632E (		4.95142E 00
198	6.07290E-01		-1.80305E (		4.94658E 00
199	6.17178E-01		1.77968E (		4.94174E 00
200	6.27057E-01		-1.75623E (	00	4.93693E 00
	COMMT PCQ FAMMING	APODIZED TR		TE ECON NO	DDAWING NO
DATE: JAN 18, 1978 REF DES: MT2			SIZ		DRAWING NO. 1950520
TOTAL NUMBER OF ELEC	TRODE STRIPES:	301	SCA	ALE: NONE	SHEET

REV

STRIPE NO.	DIM X STRIPE LOCATION	DIM Y BREAK LOCATION	DIM S STRIPE WIDTH
201	6.36926E-01	1.73270E 00	4.93212E 00
202	6.46786E-01	-1.70910E 00	4.92733E 00
203	6.56636E-01	1.68545E 00	4.92255E 00
204	6.66476E-01	-1.66175E 00	4.91779E 00
205	6.76307E-01	1.63800E 00	4.91304E 00
206	6.86128E-01	-1.61423E 00	4.90831E 00
207	6.95940E-01	1.59043E 00	4.90359E 00
208	7.05742E-01	-1.56661E 00	4.89888E 00
209	7.15535E-01	1.54279E 00	4.89419E 00
210	7.25319E-01	-1.51897E 00	4.88950E 00
211	7.35094E-01	1.49517E 00	4.88484E 00
212	7.44859E-01	-1.47138E 00	4.88018E 00
213	7.54614E-01	1.44761E 00	4.87554E 00
214	7.64361E-01	-1.42389E 00	4.87091E 00
215	7.74098E-01	1.40020E 00	4.86630E 00
216	7.83826E-01	-1.37658E 00	4.86170E 00
217	7.93545E-01	1.35300E 00	4.85711E 00
218	8.03254E-01	-1.32950E 00	4.85253E 00
219	8.12955E-01	1.30607E 00	4.84797E 00
220	8.22646E-01	-1.28273E 00	4.84342E 00
221	8.32329E-01	1.25948E 00	4.83889E 00
222	8.42002E-01	-1.23632E 00	4.83436E 00
223	8.51666E-01	1.21328E 00	4.82985E 00
224	8.61321E-01 8.70968E-01	-1.19035E 00	4.82535E 00
225 226	8.80605E-01	1.16753E 00 -1.14485E 00	4.82086E 00 4.81639E 00
227	8.90233E-01	1.12231E 00	4.81193E 00
228	8.99853E-01	-1.09990E 00	4.80748E 00
229	9.09463E-01	1.07765E 00	4.80304E 00
230	9.19085E-01	-1.05555E 00	4.79862E 00
231	9.28658E-01	1.03362E 00	4.79421E 00
232	9.38242E-01	-1.01186E 00	4.78981E 00
233	9.47817E-01	9.90278E-01	4.78542E 00
234	9.57383E-01	-9.68876E-01	4.78104E 00
235	9.66941E-01	9.47665E-01	4.77668E 00
236	9.76490E-01	-9.26653E-01	4.77233E 00
237	9.86030E-01	9.05842E-01	4.76799E 00
238	9.95562E-01	-8.85238E-01	4.76366E 00
239	1.00508E 00	8.64851E-01	4.75934E 00
240	1.01460E 00	-8.44686E-01	4.75504E 00
241	1.02411E 00	8.24744E-01	4.75074E 00
242	1.03360E 00	-8.05036E-01	4.74646E 00
243	1.04308E 00	7.855658-01	4.74219E 00
244	1.05257E 00	-7.66338E-01	4.73794E 00 4.73369E 00
245	1.06204E 00	7.47357E-01 -7.28628E-01	4.73369E 00 4.72945E 00
246 247	1.07151E 00 1.08096E 00	7.10160E-01	4.72523E 00
248	1.09041E 00	-6.91955E-01	4.72101E 00
249	1.09984E 00	6.74019E-01	4.71681E 00
250	1.10927E 00	-6.56354E-01	4.71262E 00
TRANSDUCER NAME: DATE: JAN 18,	ECOMMT PCQ FAMMING APODI	SIZE FSCM	NO. DRAWING NO.
REF DES: MT2	13/0	A 058	
	ELECTRODE STRIPES: 301	SCALE: NO	

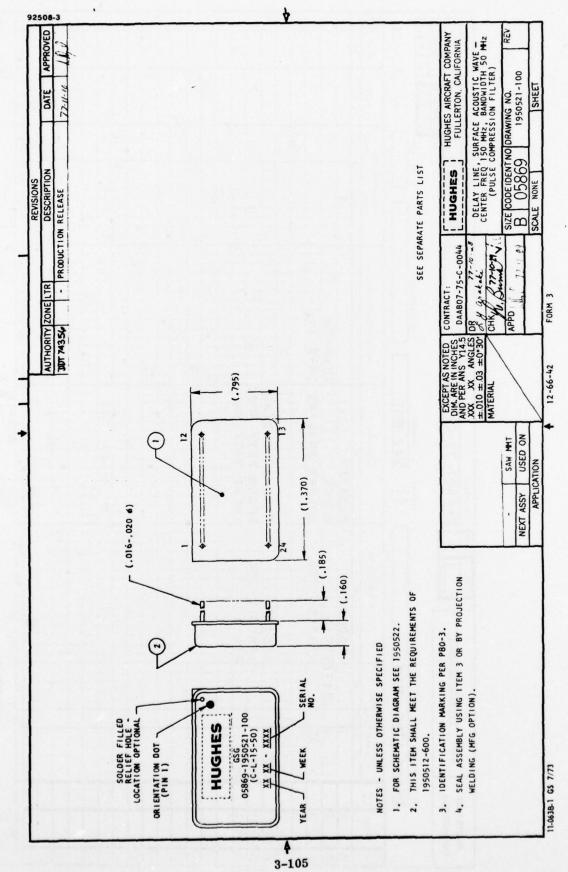
STRIPE NO.	DIM X	DIM Y	DIM S
	STRIPE LOCATION	BREAK LOCATION	STRIPE WIDTH
251	1.11870E 00	6.38964E-01	4.70844E 00
252	1.12811E 00	-6.21858E-01	4.70427E 00
253	1.13751E 00	6.05039E-01	4.70012E 00
254	1.14691E 00	-5.88510E-01	4.69597E 00
255	1.15630E 00	5.72273E-01	4.69184E 00
256	1.16568E 00	-5.56336E-01	4.68771E 00
257	1.17505E 00	5.40699E-01	4.68360E 00
258	1.18441E 00	-5.25370E-01	4.67950E 00
259	1.19376E 00	5.10349E-01	4.67540E 00
260	1.20311E 00	-4.95640E-01	4.67132E 00
261	1.21245E 00	4.81248E-01	4.66725E 00
262	1.22178E 00	-4.67174E-01	4.66319E 00
263	1.23110E 00	4.53422E-01	4.65914E 00
264	1.24042E 00	-4.39994E-01	4.65510E 00
265	1.24972E 00	4.26894E-01	4.65108E 00
266	1.25902E 00	-4.14126E-01	4.64706E 00
267 268 269 270 271 272 273 274 275	1.26831E 00 1.27759E 00 1.28687E 00 1.29613E 00 1.30539E 00 1.31464E 00 1.32388E 00 1.33312E 00 1.34235E 00	4.01690E-01 -3.89589E-01 3.77826E-01 -3.66403E-01 3.55322E-01 -3.44583E-01 3.34191E-01 -3.24145E-01	4.64305E 00 4.63905E 00 4.63507E 00 4.63109E 00 4.62712E 00 4.62317E 00 4.61922E 00 4.61528E 00
276 277 278 279 280 281 282 283	1.34235E 00 1.35156E 00 1.36078E 00 1.36998E 00 1.37917E 00 1.38836E 00 1.39754E 00 1.40671E 00 1.41588E 00	3.14447E-01 -3.05100E-01 2.96103E-01 -2.87460E-01 2.79170E-01 -2.71235E-01 2.63654E-01 -2.56428E-01 2.49559E-01	4.61136E 00 4.60744E 00 4.60354E 00 4.59964E 00 4.59575E 00 4.59188E 00 4.58801E 00 4.58416E 00 4.58031E 00
284 285 286 287 288 289 290 291	1.42504E 00 1.43418E 00 1.44333E 00 1.45246E 00 1.46159E 00 1.47070E 00 1.47982E 00 1.48892E 00 1.49802E 00	-2.43047E-01 2.36892E-01 -2.31093E-01 2.25653E-01 -2.20569E-01 2.15842E-01 -2.11472E-01 2.07458E-01 -2.03800E-01	4.57647E 00 4.57264E 00 4.56882E 00 4.56501E 00 4.56122E 00 4.55743E 00 4.55365E 00 4.54988E 00 4.54611E 00
293	1.50710E 00	2.00498E-01	4.54236E 00
294	1.51618E 00	-1.97549E-01	4.53862E 00
295	1.52526E 00	1.94955E-01	4.53488E 00
296	1.53432E 00	-1.92713E-01	4.53116E 00
297	1.54338E 00	1.90822E-01	4.52745E 00
298	1.55243E 00	-1.89282E-01	4.52374E 00
299	1.56148E 00	1.88091E-01	4.52004E 00
300	1.57051E 00	-1.87248E-01	4.51635E 00

TRANSDUCER NAME: ECOMMT PCQ HAMMING APODIZED TRANSDUCER
DATE: JAN 18, 1978

REF DES: MT2
TOTAL NUMBER OF ELECTRODE STRIPES: 301

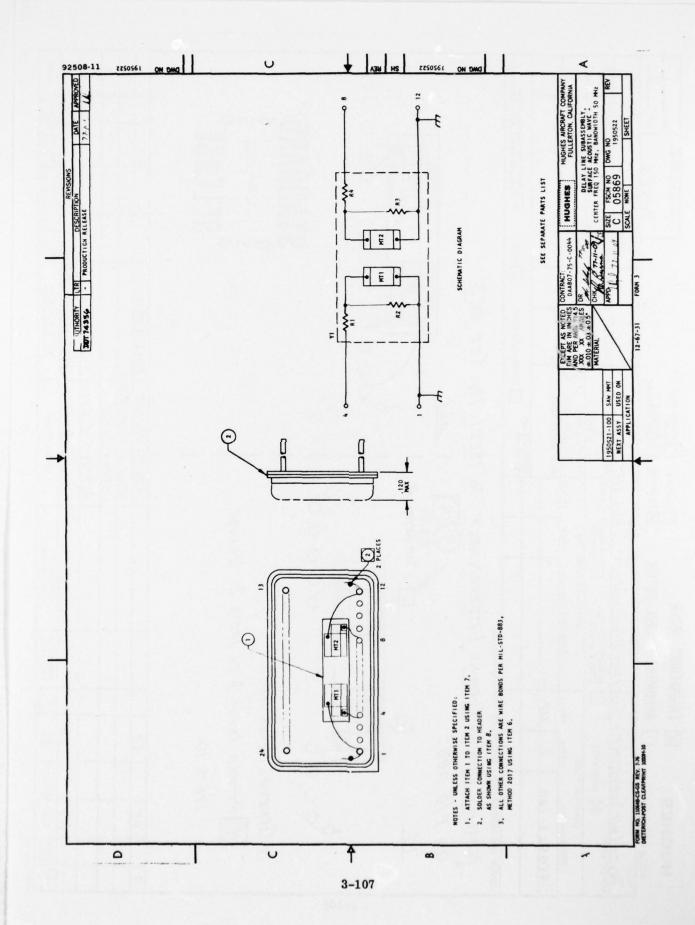
SIZE FSCM NO. DRAWING NO. REV
A 05869 1950520
SCALE: NONE SHEET 19

DIM S STRIPE WIDTH	4.51267E 00	DRAWING NO. 1950520 SHEET
S	4	SIZE FSCM NO. A 05869 SCALE: NONE
CATION	2E-01	SIZE A SCALE:
DIM Y BREAK LOCATION	1.86752E-01	TRANSDUCER
		TRANSDUCER NAME: ECOMMT PCQ HAMMING APODIZED TRANSDUCER DATE: JAN 18, 1978 REF DES: MT2 TOTAL NUMBER OF ELECTRODE STRIPES: 301
DIM X STRIPE LOCATION	1.57954E 00	CQ HAMMING
STRIP	1.5	ECOMMT PO 978 LECTRODE S'
0.	301	ER NAME: JAN 18, 19 MT2 MBER OF EL
STRIPE NO.	3	TRANSDUC DATE: REF DES: TOTAL NU



TRANSMITTAL	HUGHES AIRCRAFT COMPANY FULLERTON, CALIFORNIA	FORNIA	DAABO7-75-C-0044		PL 1950521-100		) Ju
21	12 LIST TITLE			15 REFERENCE NO.	IO PEV AUTH		7,0423
DE	ב		SAW NMT			71116	7 10 1
TEM NO. L'NE	PLANTITY OF CODE IDENT	PART OR IDENT NUMBER	DESCRIPTION	SPECIFICATION OR REFERENCE	REF DESIGNATION	HINY	9,5
	20 21 22	23	24	25	+	2	1:
1		1950512	SUBASSY				
2	1 29172	2917220216	COVER	TEKFORM		-	-
£ 3	AR	966-052775h	SOLDER, SN761W5	QQ- 8-571			
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To Sum	2-5-2			7:1-1	160		-

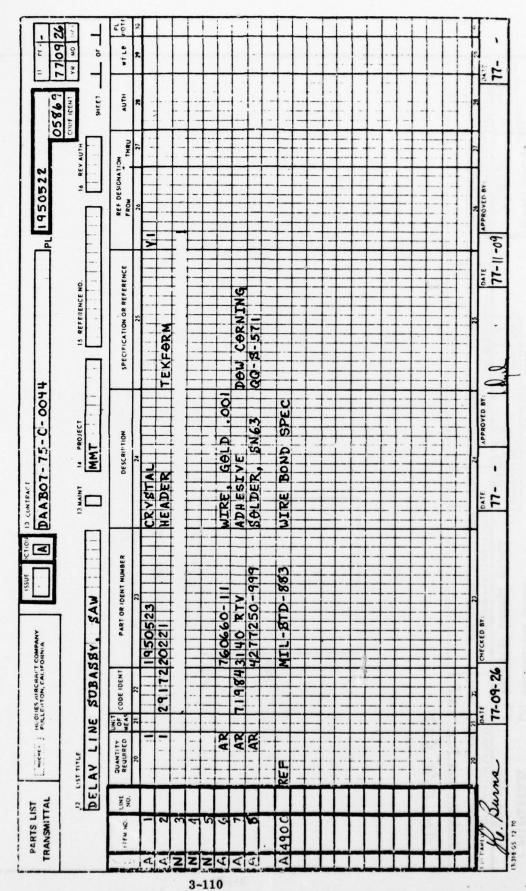
Nº



CHANGE IDENT NO.   SHET	STANDARD  STANDA	FROM THRU WEIGHT P/L. REF. DESIGNATION IN LBS. NOTE
ECP/JPN, ETC.  ORG CODE DATE  12.67-80 01.13  14.66-42 75.01	MEET MIL STD 883.  WAS  OOO D	MILESTICK 36.2 SPECIFICATION OR REFERENCE
CLASS I COMPATIBILITY CLASS II CORRECTION CORRECTION THE MAINTENANCE  CHECKED BY THRU PL MAINTENANCE	<u> </u>	STOCK IRON NKL COBRLT PLLOY RSTEM F/S, CLI COND. PDHESIVE
PROJECT ON THE MANUE	TERCONNECT  2 PLACES  2 PLACES  2 PLACES  2 PLACES  CO O O O O O O O O O	760662 PART OR IDENT NUMBER
HUGHES    ENGINEERING ORDER   TITLE   DOCUMENT CHANGE NOTICE	REASON AND DESCRIPTION - SEE BELOW FOR PLI CHANGES  REASON AND DESCRIPTION - SEE BELOW FOR PLI CHANGES  ON F/D ADD:  15  ON F/D ADD:  15  OO OO  HTEM 10	UNIT MEG CODE
SSEMBLY DATORY FEM FROM T	SobiFY SobiFY Notes CH /TE	BR ATY REG.
HES  1. 05869  1. 05869  MANDATORY  MANDATORY  CONTROL ITEM  NG NO. FROM  1-100	NAME DESCRIPTION - SEE BELOW FOR PLL  ON F/D ADD:  15  15  (4) ATTACH ITEM 9 T  ITEM 10	AR ADD OELETE
HUGHES FSCM NO. 05869 TITLE DELBY   IN/E SUR EFFECTIVITY CONTROL DRAWING NO. 195052 1-100	PEASON AND ON	10 ITEM LINE NO. NO. 6.775, 02. 6.775

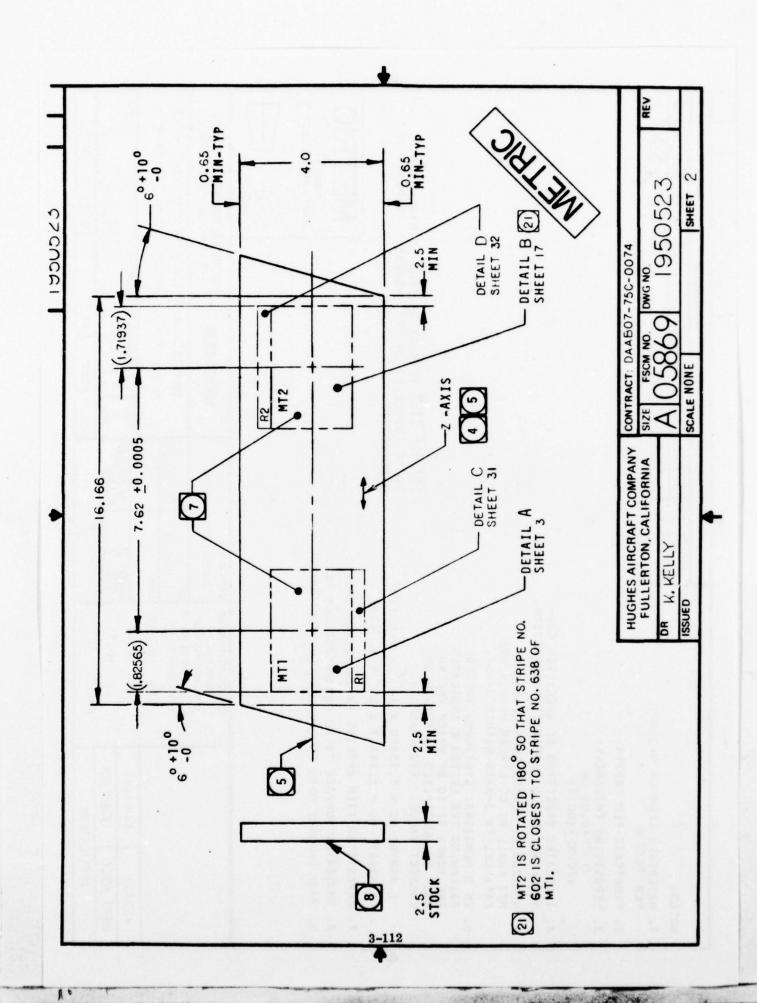
No

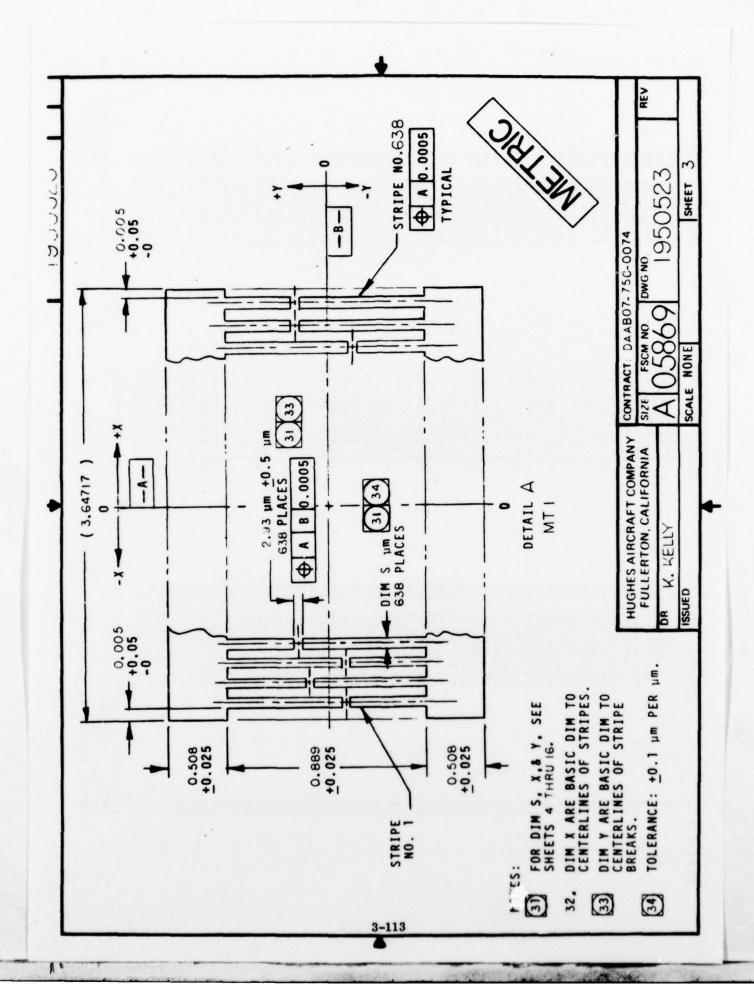
72	VITY		ZONE
SHEET.	FFECTI		P/L NOTE
76420	FION ITEM I		WEIGHT IN LBS.
76420	CONFIGURATION ITEM EFFECTIVITY DRAWING NO. FROM TH		FROM THRU
	THRU		FROM REF. DE
REV. NO.	CONTROL ITEM EFFECTIVITY RAWING NO. FROM TI		SPECIFICATION OR REFERENCE
22	ā		DESCRIPTION SI
	NITEM EFFECTIVITY FROM T	KOWAR PRITERN DETAIL A	PART OR ' D
ENT CHANGE	CONFIGURATION DRAWING NO.		UNIT OF MFG CODE
☐ DOCUMENT	THRU	<b>3</b> →	UNIT OF
	FROM T		YTO
	M EFFE	9.0	DELETE
0. 0586	CONTROL ITEM EFFECTIVITY RAWING NO. FROM	950521-100 1 ON F/0 ADD	ADD
FSCM NO. 05869	CONTROL IT	1950521-100 ON F/0	ITEM LINE



CRYSTAL, SURFACE ACOUSTIC WAVE - PCLN APPROVED REV (AMERICAN) PROJECTION 50 MHz CENTER FREQ., 50 MHz BANDWIDTH HUGHES AIRCRAFT COMPANY OF 32 FULLERTON, CALIFORNIA TO BE INSTALLED IN NEXT ASSEMBLY AT POINT OF FRAGILE ITEM (EASILY DAMAGED BY HANDLING) 950523 78-08-29 DATE SHEET  $\odot$ DWG NO REVISIONS DESCRIPTION PRODUCTION RELEASE 3 HUGHES SCALE NONE MANUFACTURE, SIZE 78-08-25 90-60-81 DAAB07-75C-0074 AUTHORITY DDT 86948 K. KELLY CONTRACT 8. INDICATED SURFACE TO BE CORRUGATED PER P82. BACK SURFACE TO BE ROUGHENED WITH #180 GRIT. DEPOSITION FILM APPLIED IN INDICATED AREA. SH  $1.45870E-02 = 1.45870 \times 10^{-2} = 0.014587$ 1.34567E 00 = 1.34567 x 100 = 1.34567 STALLINE AXIS & PROPAGATION DIRECTION. INDICATES DIRECTION OF SPECIFIED CRY-DIMENSIONS ARE MILLIMETERS & UNLESS OTHERWISE ₹0.002 PER ANSI Y14.5 +20 +0.02 +0.5 HORIZONTAL CENTERLINES OF MT1 & MT2 SHALL BE CO-LINEAR WITHIN AND SPECIFIED PARALLEL TO Z-AXIS WITHIN 0.250. FOLLOWING THE LETTER E INDICATES THE POWER OF 10 BY WHICH THE NO. MUST BE MULTIPLIED TO OBTAIN THE IN DIMENSIONAL LISTINGS, THE NO. ANGLES CORRECT VALUE. FOR EXAMPLE: XXX. ××. × 1. MATERIAL: LITHIUM NIOBATE Z DEPOSITION THICKNESS: 2. FABRICATE PER 780294 USED ON 0.20 +0.01 µm SAW-MMT **APPLICATION** PER 760716 **NEXT ASSY** 950522 NOTES: 5 ;

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		A 4
STRIPE LIDTH	8 M W W & A W W W W W W W W W W W W W W W W	USBED CRAWING NO.
		SIZE A SCALE:
DIM Y BREAK LCCATION	8899441114466411111111111111111111111111	PODIZED TRANSDUCER
STRIPE LOCATION		R NAME: ECOMMT PCLN, UNA AN 18,1978 Wil Per of electrode strifes:
STRIPE NO.	まるでみちらて みらじまえてみちらするちょうるでんちらまるでんちゃく もっちゃりんさんでん ちゃりょうでん しょうしょう しょうしょう はっちゃく まっちゃく しょうしょう しゅうしょう しゅうしゅう しゅうしょう しゅうしょう しゅうしょう しゅうしょう しゅうしゅう しゅうしゅう しゅうしょう しゅうしょう しゅうしょう しゅうしょう しゅうしょう しゅうしゅう しゅう	TRANSDUCE DATE: J. FEF DES: I

		REV;
DIM S STRIPE LIDTH	3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3       3.3.3 <td< td=""><td>SIZE FSCM NO. CRAWING NO. A 05869 1950523 SCALE: NONE SHEET</td></td<>	SIZE FSCM NO. CRAWING NO. A 05869 1950523 SCALE: NONE SHEET
DIM Y BREAK LCCATION		UNAPODIZED TRANSDUCER
STRIPE LOCATION		NSDUCER NAME: ECOMMT PCLN. U. LAN 18,1978 DES: PT1 AL NUMBER OF ELECTRODE STRIFE
STRIPL NO.	- NEWS SE	7 8 0 7 8 8 8 8 8 8 8 8 8 8 8 8 8 8 8 8

		•
STRIPE MIDTH	33.3.3.3.3.3.3.3.3.3.3.3.3.3.3.3.3.3.3	FSCP NO. DRAWING NO. 05869 1950523
BREAK LCCATION	11111111111111111111111111111111111111	IZED TRANSDUCER SIZE
STRIPE LOCATION	11111111111111111111111111111111111111	USDUCER NAME: ECOMMI PCLN, UNAPGD : JAN 18,1978 DES: MT1 AL NUMBER OF ELECTRODE STRIFES:
. 0.4 Jel		TRAN DATE TEF

DIM S STRIPE LIDTH	23.33.33.33.33.33.33.33.33.33.33.33.33.3	SIZE FSCP NO. DRAWING NO. A 05869 1950523 SCALE: NONE SHEET
DIM Y PREAK LOCATION		S: 638
STRIPE LOCATION	1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88. 1.88.	DES: MT1 L NUMBER OF ELECTRODE STRIF
IPE NO.	1 cm 1 4 cm 4 cm 6 cm 2 cm 4	REF

STRIPE WIDTH	24444444444444444444444444444444444444	E FSCP NO. DRAUING NO. 05869 1950523 LE: NONE SHEET
DIP Y BREAK LOCATION	11111111111111111111111111111111111111	SIZ 638 SCA
DIM X STRIPE LOCATION	0.0.0.0.0.0.0.0.0.0.0.0.0.0.0.0.0.0.0.	JAN 14-1978  MA11 MA12 OF ELECTRODE STRIPES:
IPE NG.	よみろみち もてほういよるでんちらてとりのよるでんちらいよるちょうしん ちょうようしょう こうちょう ちょうしゅう しょうきょう しょうしょう しょうしゅう しょう しょうしゅう しょうしゅう しょうしゅう	FEF DES

CIM S STRIPE WIETE	66999999999999999999999999999999999999	SIZE FSCM NO. CRAWING NO. A 05869 1950523 SCALE: NONE SHEET
DIP Y BREAK LCCATION		RIFES: 638
STRIPE LOCATION	20 20 37 44 47 47 47 47 47 47 47 47 47 47 47 47	: JAN 18,1978 DES: MT1 L NUMPFR OF ELECTRODE ST
STRIFF NO.	するまんのもしむの のもらちょうにもりのものなるものもしもらりしょうさんにもしゅうり 氏	DATE REF TCTA

REV.

		RE.
STRIPE WIDTH	22.22.22.22.22.22.22.22.22.22.22.22.22.	IZE FSCM NO. DRAWING NO. A 05869 1950523 CALE: NONE SHEET
BREAK LOCATION	11111111111111111111111111111111111111	UNAPODIZED IMANSDUCER S
STRIPE LOCATION	33 3 3 3 3 3 3 3 3 3 3 3 3 3 3 3 3 3 3	DUCER NATE: ECUMMI PILIN, UNA ES: VT1 NUMBER OF ELECTRODE STRIFF
STRIPE NO.	- コステムに、もて 色りらしるまみきもて色りでするできるとのはなったらい (2)	DATE: DATE: TOTAL

		RE 11
CIM S STRIPE WIDTH	22.77 24.97 25.77 26.99 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77 27.77	SIZE FSCM NO. DRAWING NO. A 05869 1950523 SCALE: NONE SHEET
BREAK LOCATION	11 11 11 11 11 11 11 11 11 11 11 11 11	UNAPODIZED TRANSDUCER ES: 638
STRIPE LOCATION	8 NB NB NB NB NB NB NA 44 44 44 44 44 44 44 44 44 44 44 44 44	DUCER NAME: ECOMMT PCLN. JAN 18,1978 ES: MT1 NUMPFR OF ELECTRODE STRIF
STRIPT NO.	よるちょう もて おっし しょうきょ とし けっしょうちょ とし とういまる ちょし とり しょうきょ とし とり しょう ちょう しゅう しょう しゅう しょう しゅう しょう しゅう しょう しょう しょう しょう しょう しょう しょう しょう しょう しょ	TRANS DATE: REF D TCTAL

CIM S STRIPE WICTH	68103E 0 68103E 0 67839E 0 67839E 0 67575E 0 67313E 0	66 25 9 9 9 9 9 9 9 9 9 9 9 9 9 9 9 9 9 9	22.665 22.665 22.665 22.665 22.665 22.665 22.665 22.665 22.665 22.665 22.665 23.665 23.665 23.665 24.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26.665 26	0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0
DIP Y BREAK LCCATION	.07898E-0 .07898E-0 .07898E-0 .07898E-0 .07898E-0	1.07898E-0 1.07898E-0 1.07898E-0 1.07898E-0 1.07898E-0 1.07898E-0 1.07898E-0 1.07898E-0	11.07898E-01 10.07898E-01 10.07898E-01 10.07898E-01 10.07898E-01 10.07898E-01 10.07898E-01 10.07898E-01	0.7898E-0 0.7898E-0 0.7898E-0 0.7898E-0 0.7898E-0 0.7898E-0 0.7898E-0 0.7898E-0
DIM X STRIPE LOCATION	.05102E-0 .10464E-0 .15824E-0 .21583E-0 .31886F-0		7.2246.8E-01 7.2246.8E-01 7.237468E-01 7.43667E-01 7.43667E-01 7.548961E-01 7.54836E-01 7.54836E-01 7.54836E-01 7.54836E-01 7.54836E-01 7.54836E-01 7.54836E-01 7.54836E-01	01036/E-01 112038E-01 122038E-01 12509E-01 233336E-01 333336E-01 43632E-01 64362E-01 64364E-01 64864E-01 64864E-01
STRIFF NO.	0000000	CC HHHHHHHHHHNN	444444444444444444 100000000000000000	1004444444446491 100444444446491 100444444444444444444444444444444444

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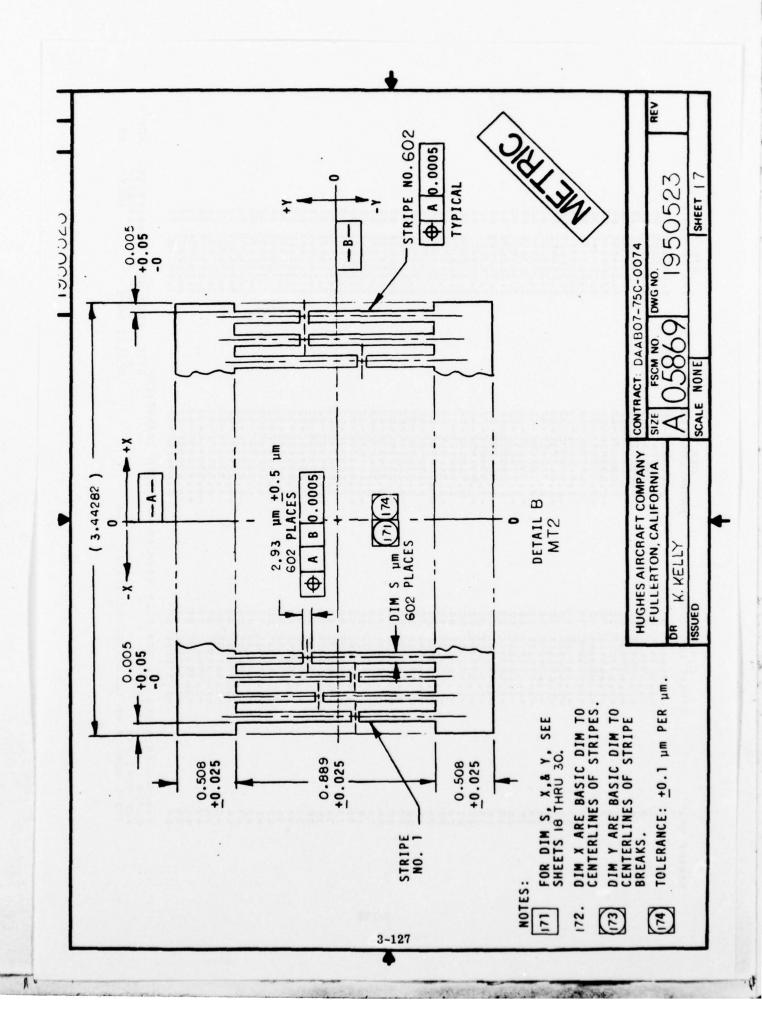
STRIPE WIDTH	2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2	E FSCM NO. DRAW
DIN Y BREAK LCCATION		AFODIZED TRANSDUCE: 636
STRIPE LOCATION	8888888746899999999999999999999999999999	DUCER NAME: ECOMMT PCLN, U JAN 18,1978 ES: MT1 NUMBER OF ELECTRODE STRIPE
STRIPE NO.		- Car

DIM S STRIPE WIDTH	2.5577£E 00	555465	.55546E 0	.55317E 0	.55317E 0	.55089E 0	. 55089E 0	E CACTE O	346 34F	546346	.5440BE 0	.5440PE 0	.54182E 0	.54182E 0	.53957E 0	.53957E 0	.53732E 0	.53732E D	- Dancer	. 53508E G	- 33265F	53062F	.53062E 0	.52840E 0	.52840E 0	.52618E D	.52618E 0	.52397E.0	.52397E 0	. 521/eE G	51956F	SIGNET OF STREET	51737F D	51737F 0	.51518E 0	.51518E 0	.51300E 0	.51300E C	.51082E 0	.51082E C	.53865E 0	.50865E C	.50648E 0	.50648E 0	. 50433E	.50433E 0	NO. DRAWING	ALE: NONE SHEE	
DIF Y BREAK LCCATION	1.07898E-01	1.07898F-0	.07898E-0	.07898E-0	1.07898E-0	.0789RE-0	1.07898E-0	O TROBELLO	1078986	07898F-0	1.07898E-0	.07898E-0	.07898E-0	1.07898E-0	.07898E-0	1.07898E-0	.07898E-0	1.07898E-0	0 1898E-0	1.07898E-0	78985	1.07898F-0	.07898E-0	1.07898E-0	.07898E-0	1.07898E-0	1.07898E-0	.07858E-0	1.07898E-0	0700EF	1.070005	0789850	1.0789PF-0	07898F-0	1.07898E-0	.07898E-0	1.07898E-0	.07898E-0	1.07898E-0	.07898E-0	.07898E-0	.C7898E-0	.07898E-0	1.07898E-0	.07898E-0	.07898E-0	UNAFODIZED TRANSDUCER	PES: 638	
CCATION	1F 00	ے د مال	E O	S	0	٠ س	ت د سال	9 6	) C		1	2	0	0 3	0	0	F	O I	9	O 1	J 6	) C	o o	U	9	9	E	0 i	0 ·	90	20	) C	) C	14	שנ	E	EO	0	3	E	E O	0	E	O (	0 C	E 0	MT PCLN .	ODE STRIF	
STRIPE L	1288	1390	1441	.1492	. 1543	.1594	.1645	1970	1404	1849	1900	1951	.2002	.2053	. 2103	.2154	. 5505	. 2256	. 2306	.2357	2408	25.00	2560	.2610	. 2661	.2711	.2762	. 2812	. 2863	. 2913	1067	4004	3118	3165	3216	. 3266	.3316	.3367	.3417	.3467	.3517	.3567	.3618	.3668	.3718	. 3768	E: ECOM	F ELECTR	
										- ** ** ** ** ** ** ** ** ** ** ** ** **														*																							UCER	AL NUM	
STRIPE NO.	501		C	-	.,		0		-	+-	• -	-	-	-	-	-	-	N	N	0	N	60	10	C	C		m	M	m		0 1	2 1	7 1	: 1	) M	4	4	4	4	4	4	4	4	4	31	E)	TRI	-0	

REV 14

		REV 15
DIM S STRIPE WIDTH	22.22.23.23.23.23.23.23.23.23.23.23.23.2	IZE FSCP NO. DRAWING NO.
DIM Y BREAK LOCATION		NAPODIZED TRANSDUCER S
STRIPE LOCATION	11111111111111111111111111111111111111	DUCER NAME: ECOMMT PCLN. UJAN 18,1978 JAN 18,1978 FS: MTI NUMBER OF ELECTRODE STRIPE
RIPF NO.	こうきょ ちょうりゅう いこうきょ ちらて ちらし こうさんき らり りりょうきょ きっかっしょ こうか しゅうり しゅう しゅうしゅう しょうきょう しょう マック・ロック しゅうしゅう しょうきょう しょうしゅう しゅうしゅう しゅうしゅう しょうしゅう しゅうしゅう しゅうしょう しゅうしゅう しゅう	PANS PATE TOTAL

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STRIPE WIDTH	22 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2	SIZE FSCY NO. DRAWING NO. A 05869 1950523 SCALE: NONE SHEET
DIM Y BREAK LOCATION	11	S: 638
STRIPE LOCATION	1.62947E 1.63497E 1.654947E 1.654947E 1.654947E 1.654946E 1.654946E 1.654946E 1.654946E 1.654946E 1.746698 1.746698 1.746698 1.746698 1.746698 1.746698 1.746698 1.746698 1.746698 1.746698 1.746698 1.746698 1.746698 1.746698 1.746698 1.746698 1.746698 1.746698 1.746698 1.746698 1.746698 1.746698 1.746698 1.746698 1.746698 1.746698	DES: MT1 L NUMPER OF ELECTRODE STRIF
STRIPE NO.	- ここずもできてのららしまるできるとのとのことをもららりには、これをしての のしょうこれ ちょうしゅうしゅう はんしゅうしゅう はんしゅう はんしゅう しょうしゅう しょうしゅう しょうしゅう	DATE DATE TCTA



		REV ,
STRIPE WIDTH	33.22.33.33.33.33.33.33.33.33.33.33.33.3	NG. DRALING NO. 69 1950523 E SHEET
0,	~	FSCP 058 NON
		SIZE SCALE
DIN Y PREAK LOCATION	0.000000000000000000000000000000000000	APUDIZED TRANSD
		PES: 6
NO		STRIP
TRIPE LOCATI		1978 ELECTRODE
S		12 0F
		S CUCER S C CA DES: A
. C.N	よさき 4 に らて おし ひまえち 4 ち らくひまえき 4 ち らてみ らいまえ ち 4 ち ら て み り し まる でん し し まる でん し し まる し も し し まる し も し し し し し し し し し し し し し し し し し	PEFE TOTAL
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		REV ,
STRIPE WIDTH	8 8 8 8 8 8 8 8 8 8 8 8 8 8 8 8 8 8 8	SCM NO. CRAWING NO. 05869 1950523
DIP Y BREAK LOCATION	11 11 11 11 11 11 11 11 11 11 11 11 11	46 APODIZED TRANSDUCER SIZE F 602 SCALE:
STRIPE LOCATION	11111111111111111111111111111111111111	DUCER NAME: ECOMMT PCLN FAMMING JAN 18,1978 ES: MT2 OF ELECTRODE STRIPES:
STRIPE NO.	まる まちに ちらららん ちんんん ちって ファファファファ は のの に ら の の の の の り り り り り り り り り り り り り り	TRANS CATE: RFF D TOTAL

STRIPE LIDTH	888 888 888 888 888 888 888 888 888 88	FSCM NO. DRAWING NO. 05669 1950523 : NONE SHEET
BREAK LOCATION		APODIZED TRANSDLCER SIZE A 602 SCALE
DIM X STRIPE LOCATION	11111111111111111111111111111111111111	CER NAME: ECOMMT PCLN HAMMING JAN 16,1978 : MT2 UMBER OF ELECTRODE STRIPES:
PE NO.	よるさんだらており ひょるぎ みだらて おうじょるぎんちらておりひょるぎんちょうりょうきょんちらしんりじ	TRANSDUC DATE: PEF DES: TCTAL NUI

		REV 21
STRIPE WIDTH	22.00000000000000000000000000000000000	FSCM NO. DRAWING NO. 55869 1950523 : NONE SHEET
DIM Y BREAK LCCATION	10000000000000000000000000000000000000	AMMING APODIZED TRANSDUCER SIZE A A A C A C A C A C A C A C A C E :
STRIPE LOCATION		UCER NAME: ECOMMI PCLN FAMM JAN 18:1978 S: MT2 NUMBER OF ELECTRUDE STRIPES:
STRIPE NO.	ようちょちらておりのよるちょうちゃりょうちょち らてはらしょうちょき ちゃんりゅうこう ちゅうてんりし	TRANSD DATE: REF DE: TOTAL

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STRIPE LIDTH	22.22.22.22.22.22.22.22.22.22.22.22.22.	SCM NO. CRAWING NO. 358E9 1950523 NONE SHEET
BREAK LCCATION	### ### ### ### ### ### ### ### ### ##	APODIZED TRANSDLCER SIZE F A A 602
STRIPE LOCATION		DUCER NAME: ECOMMT PCLN FAMMING JAN 18:1978 ES: MT2 NUMBER OF ELECTRODE STRIPES:
	**************************************	TRANSI DATE: REF DE

		REV.
STRIPE MICTH	\\ A \text{G \te	FSCM NO. DRAWING NO. USBES 1956523 : NONE SHEET
BREAK LCCATION		ING APODIZED TRANSDLCER SIZE 602
STRIPE LOCATION	11111111111111111111111111111111111111	ICER NAME: ECOMMT PCLN FAMMING JAN 18,1978 :: MT2 IUMBER OF ELECTRODE STRIPES:
STRIPF 1:0.	まるまれまもできらいまるまれたもでもまるまないられるようななられるなるなられるならなっていまってです。 ちゃまちらまちもももももももももなってアファファファファファ をあれる ものものものものもの ちゃっと でっと できる はらららららららららららららららららららららららららららららららららららら	TRANSDU CATE: REF DES TCTAL N

		REV 24
STRIPE WIDTH	2.2.2.2.2.2.2.2.2.2.2.2.2.2.2.2.2.2.2.	USE NO. DRAWING NO. USE 1950523 NONE
DIM Y BREAK LOCATION	11111111111111111111111111111111111111	G APODIZED TRANSDICER Size 602 Scale:
STRIPE LOCATION	11.1.1.1.1.1.1.1.1.1.1.1.1.1.1.1.1.1.1	NAME: ECOMMT PCLN FAMMING 1 18,1978 FR OF ELECTRODE STRIPES:
STRIPE NO.		TRANSDUCER DATE: JA REF DES: M TOTAL NUMB

		× ~
STRIPE LIDTH	22.2.2.2.2.2.2.2.2.2.2.2.2.2.2.2.2.2.2	FSCM NO. DRAWING NO. 1950523 SHEET
DIE Y DREAK LCCATION	11111111111111111111111111111111111111	MING APODIZED TRANSDUCER SIZE \$ 602
STRIPE LOCATION	66 66 66 66 66 66 66 66 66 66 66 66 66	UCER NAME: ECOMMI PCLN PAMN JAN 1841978 S: MT2 NUMEER OF ELECTRODE STRIPES:
STRIPL MG.	まるぎゃ ちらてらりひょえきゅうちゃくもえるみちらす めらりょんぎゅ ちらてらりゅうえぎゅ ちらていじょし	TRANSDU DATE: RFF DES

STRIFE LIDTH	2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2	FSCM NO. DRAWING NO. 05869 1950523 :: NONE SHEET
PREAK LCCATION	11111111111111111111111111111111111111	APODIZED TRANSDUCER SIZE A A SCALE
STRIPE LOCATION	6.90 6.90 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00 7.00	CR NAME: ECOMMI PCLN FAMMING JAN 18,1978 MIZ HER OF ELECTRODE STRIPES: 6
IPE NO.	ർ. ർ	TRANSDUCE DATE: JREF DES: TOTAL NUM

		RE 27
STRIPE LIDTH	2 5 5 7 5 7 5 7 5 7 5 7 5 7 5 7 5 7 5 7	FSCM NO. CRAWING NO. 05869 1950523 SHEET
DIM X STRIPE LOCATION BREAK LCCATION	99.533012E=01 99.533012E=01 99.533012E=01 99.5330E=01 10010202 99.5330E=01 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 10010202 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100102 100	MET PLEN FAMMING APODIZED TRANSDOL RODE STRIFES: 602
STRIPE NO.		PATE: JAN 18 REF DES: WTZ TOTAL NUMBER

		REV ,
STRIPE LIDTH	20.00.00.00.00.00.00.00.00.00.00.00.00.0	M NO. DRAWING NO. 869 1950523 NE SHEET
BREAK LCCATION	11 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	APODIZED TRANSDUCER SIZE FSC A DS 02
DIM X STRIPE LOCATION	11.22.000 12.22.000 12.22.000 12.22.000 13.22.000 13.22.000 14.22.000 15.22.000 16.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000 17.22.000	DUCER NAME: ECOMMT PCLN FAMMING JAN 18,1976 ES: MT2 NUMBER OF ELECTRODE STRIPES: 6
STRIPE NO.	はらららららららららららららららららららららららららららららららららららら	TRANSDU DATE: REF DE: TOTAL

		RE 29
STRIPE LIDTH	44444444444444444444444444444444444444	FSCM NO. DRAWING NO. 05869 1950523 NONE SHEET
DIM Y BREAK LCCATION	11 11 11 11 11 11 11 11 11 11 11 11 11	APUDIZED IRANSDULLER SIZE A A A SCALE:
ATICA		F STRIPES: 6
DIM X STRIPE LOCA		UCER NAME: ECOMMI JAN 18,1978 S: MT2 NUMPFR OF ELECTRODE
STRIPE NO.	まるきゅきらてのひのよるきゅきらてのちじょうきゅうらてのちのよるさんちらしょうきゅう しょうきゅう しゃくちょう ちゅうりょう しょうきゅう しゃくりょう はいまく しょうきゅう しょうきゅう しょうきょう しょうきょう しょうきょう しょうきょう しょうきょう しょうしょう しょうしゅう しゅうしょう しゅうしゅう しゅうしゅう しゅうしゅう しゅうしゅう しゅうしゅう しゅうしゅう しょうしょう しゅうしゅう しゅうしょう しゅうしゅう しゅうしゅう しゅうしゅう しゅうしょう しゅうしゅう しゅう	TRANSDU DATE: REF DES TOTAL

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REV
                                                                                                        30
                                                                   TRANSDUCER NAME: ECOMMT PCLN FAMMING APODIZED TRANSDUCEK

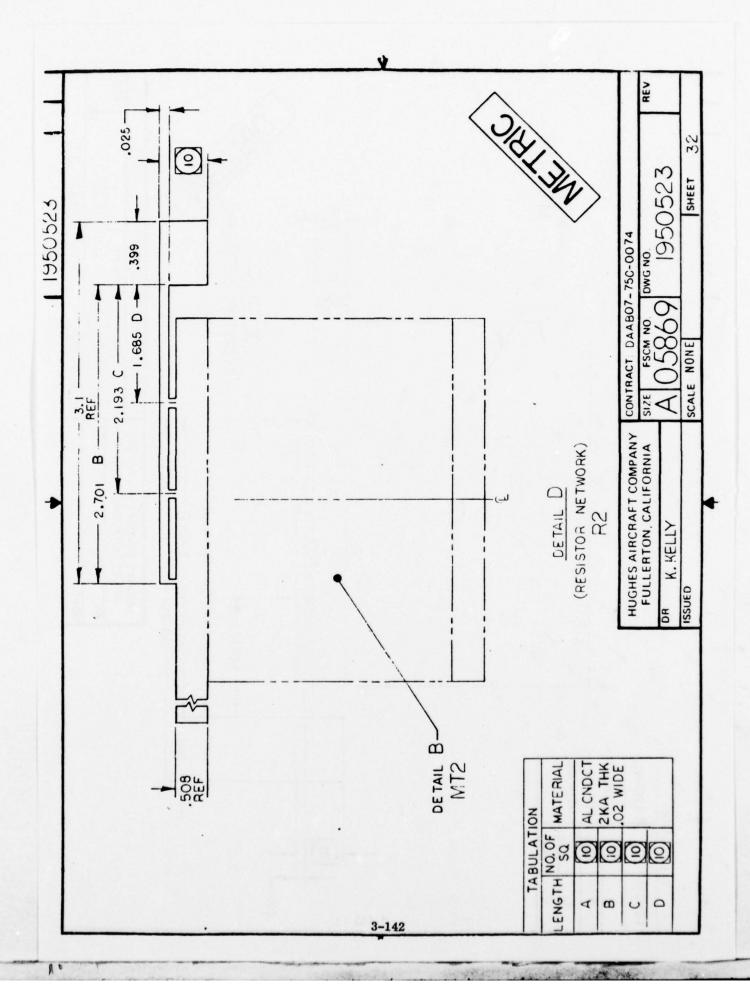
SIZE FSCM NO. DRAWING NO.

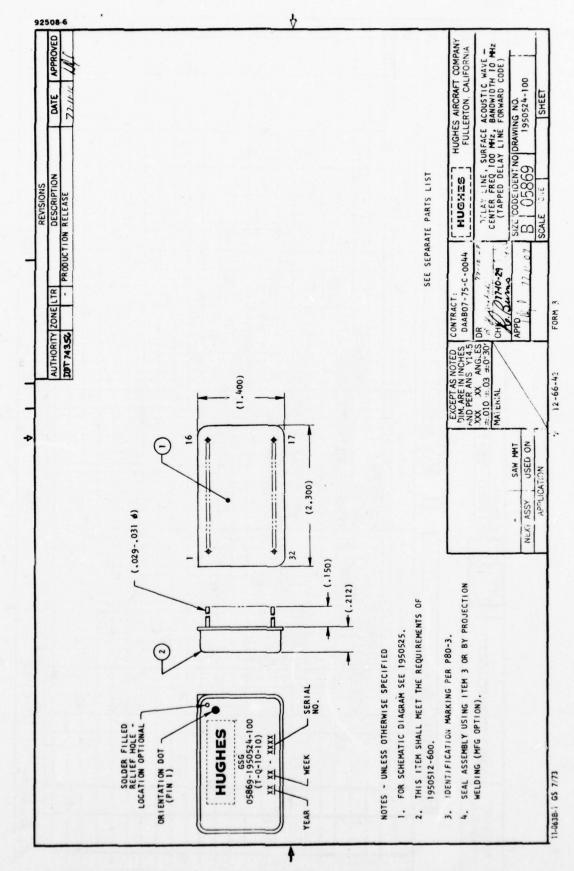
A 05869 1950523

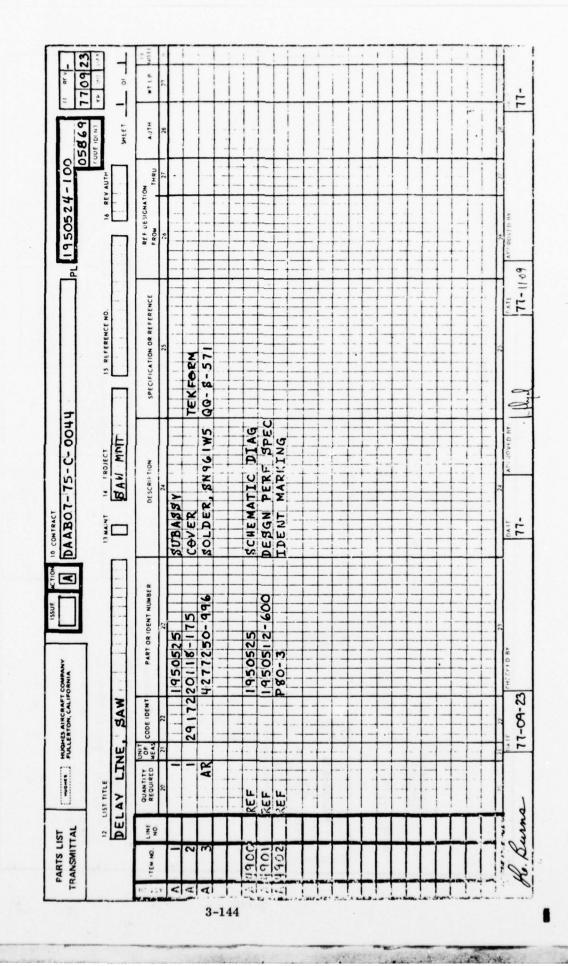
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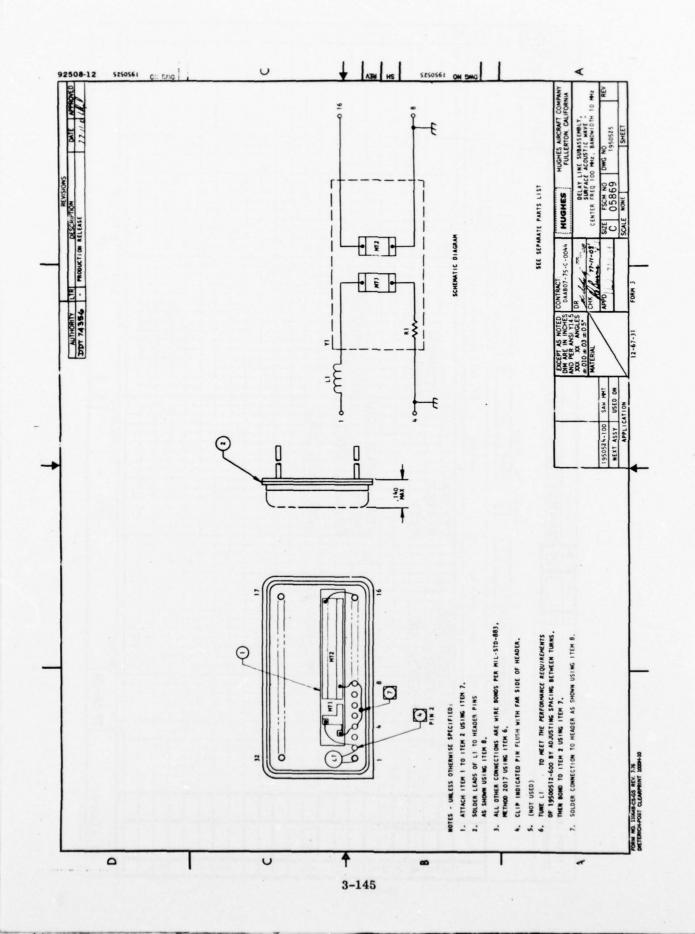
A 05869 1950523

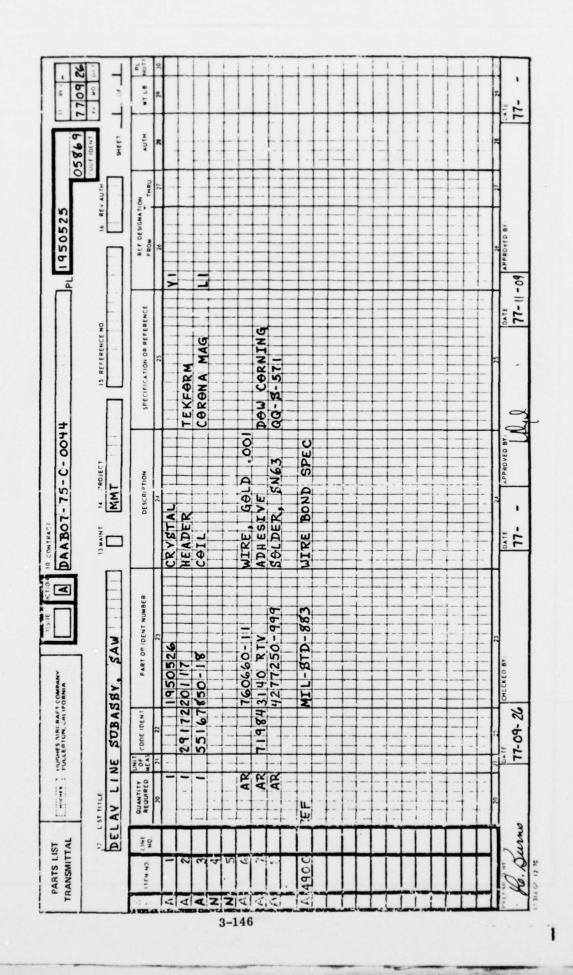
TCTAL NUMBER OF ELECTRODE STRIPES: 602
 STRIPE LIDTH
                                 2.43520E 00
BREAK LCCATION
                                   9.52778E-03
  STRIPE LOCATION
                                  1.70232E 00
1.70719E 00
              STRIPE NO.
```







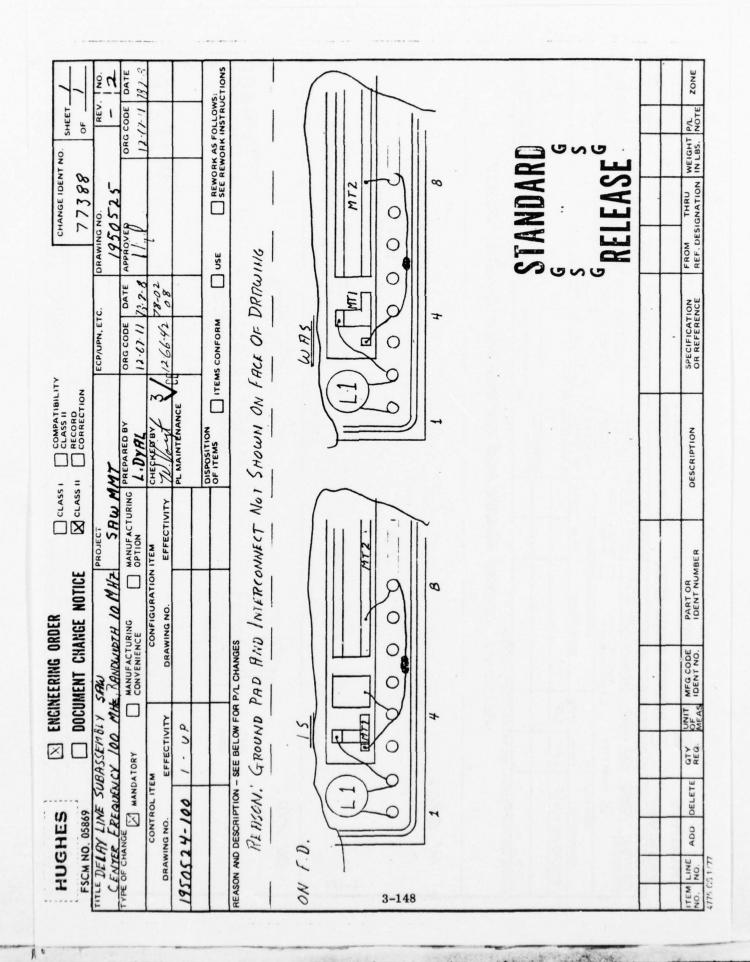




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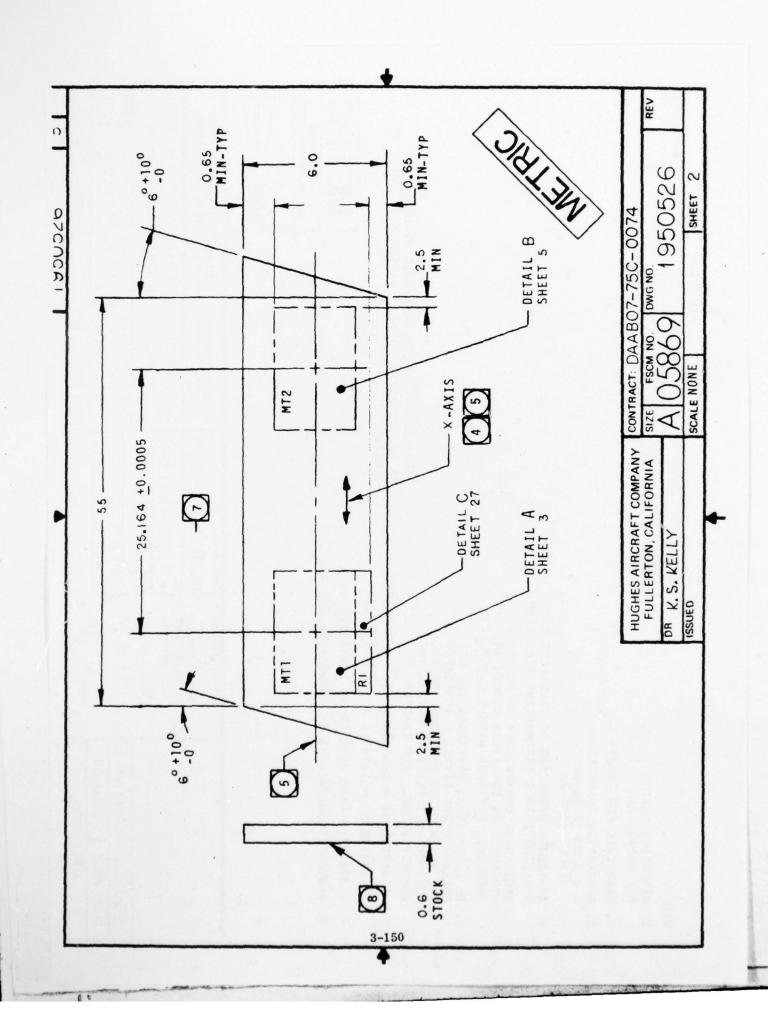
1	REV. NO.	DATE DATE			REWORK AS FOLLOWS:  SEE REWORK INSTRUCTIONS					STANDARD S RELEASE	ZONE
SHEET	a .	ORG CODE 12-67.10			AS FOLL				FLUSH	3 4	HT P/L
JA NO	10				WORK A	100			FL		WEIGHT IN LBS.
75393	NO. 052	grings	0		S.E.	DEN		S	OF HEADER	630 NO	FROM THRU
5	DRAWING NO.	APPROVED			USE	ON SAW DEVICE		W45	SIDE O	$\frac{z}{z}$	FROM REF. DES
٤	TC.	12-67-10 17-12-12	1266-42 77.72		TEMS CONFORM	1 1			CLIP INDICATED WITH FAR SIDE O		SPECIFICATION OR REFERENCE
CLASS II	1 / SAW	PREPARED BY RD YONAN	CHECKED BY 13/	NCE	DISPOSITION OF ITEMS	HEADER PINS NOT REQUIRED			4	WAS	DESCRIPTION
CLASS !	PROJECT RAY THEON	MANUFACTURING OPTION	M THRU	$\vdash$	+	HEADER ,		18	9		
GE NOTICE	_		RATION			CTIPPEO			v USED		PART OR IDENT NUMBER
DOCUMENT CHANGE NOTICE	SUBASSEMBLY, SAW	MANUFACTURING CONVENIENCE	CONFIGU DRAWING NO.			REASON AND DESCRIPTION - SEE BELOW FOR PALCHANGES  REASON AND DESCRIPTION - SEE BELOW FOR PALCHANGES			4. 107		MFG CODE
	SSEM		THRU	3		PEA					TINO
	808A	TORY	FROM	-		SEE BE				<u>S</u>	PEQ.
10 0	40	MANDATORY	CONTROL ITEM			PTION -				`.	DELETE
HUGHES	2		CONTR DRAWING NO.	950514 -100		DESCRI	2/5			ON F/0:	ADD
HUGHES	CENTER DELA	EFFECTIVITY	DRAWI	2025		ON AND	3			3	ITEM NO. NO.
<u> </u>	SE SE	EFFE		16/		REAS			3-147		ITEM NO.

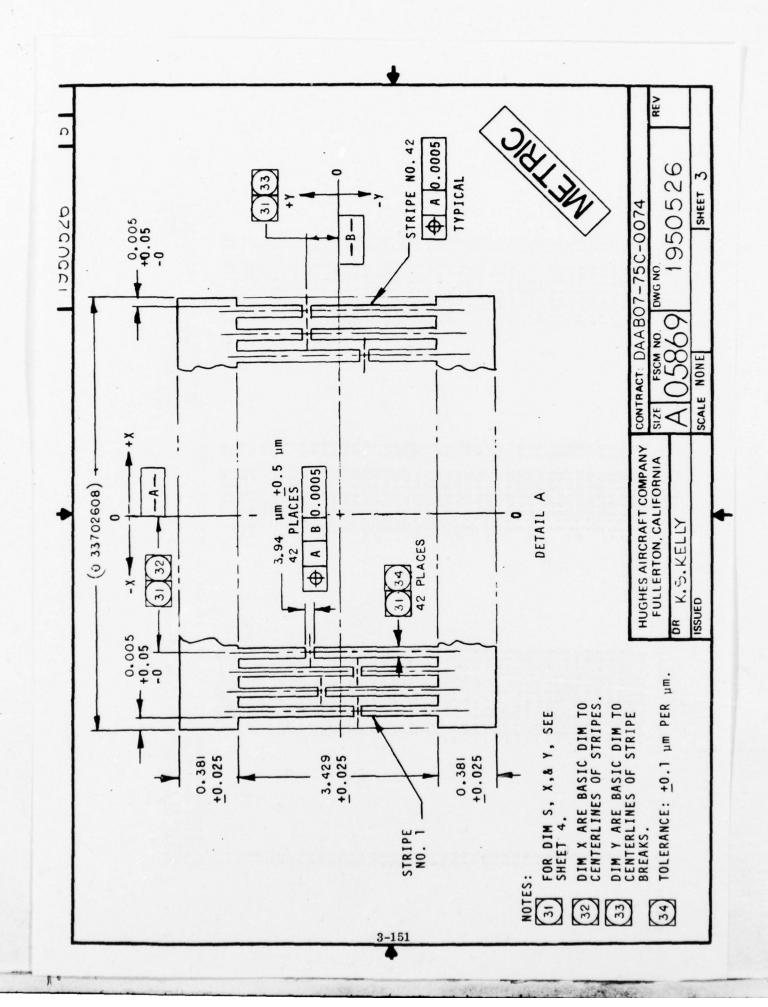
11 "



CRYSTAL, SURFACE ACOUSTIC WAVE- TDL-100 APPROVED THIRD ANGLE (AMERICAN) PROJECTION REV 100 MHz CENTER FREQ., 10 MHz BANDWITH HUGHES AIRCRAFT COMPANY SHEET 1 OF 27 FULLERTON, CALIFORNIA FRAGILE ITEM (EASILY DAMAGED BY HANDLING) -TO BE INSTALLED IN NEXT ASSEMBLY AT POINT OF 950526 DATE DWG NO REVISIONS PRODUCTION RELEASE DESCRIPTION × HUGHES SCALE NONE MANUFACTURE. SIZE DAABO7-75C-0074 K.S. KELLY 78-05-17 AUTHORITY LTR 1 DDT 82255 CONTRACT INDICATED SURFACE TO BE CORRUGATED PER P82 7. DEPOSITION FILM APPLIED IN INDICATED AREA.  $1.45870E-02 = 1.45870 \times 10^{-2} = 0.014587$ 1.34567E 00 = 1.34567 x 10<sup>0</sup> = 1.34567 STALLINE AXIS & PROPAGATION DIRECTION. INDICATES DIRECTION OF SPECIFIED CRY-DIMENSIONS ARE MILLIMETERS & UNLESS OTHERWISE +0.002 PER ANSI Y 14.5 +20 +0.02 +0.5 SPECIFIED HORIZONTAL CENTERLINES OF MT1 & MT2 SHALL BE CO-LINEAR WITHIN AND PARALLEL TO X-AXIS WITHIN 0.250. FOLLOWING THE LETTER E INDICATES THE POWER OF 10 BY WHICH THE NO. MUST BE MULTIPLIED TO OBTAIN THE IN DIMENSIONAL LISTINGS, THE NO. ANGLES XXX. ××. CORRECT VALUE. FOR EXAMPLE: N 2. FABRICATE PER 780294-1. 3. DEPOSITION THICKNESS: SAW/MMT 0.125 +0.01 µm USED ON 1. MATERIAL: QUARTZ PER 760781-100 APPLICATION **NEXT ASSY** 950525 NOTES: \* 5 , 3-149

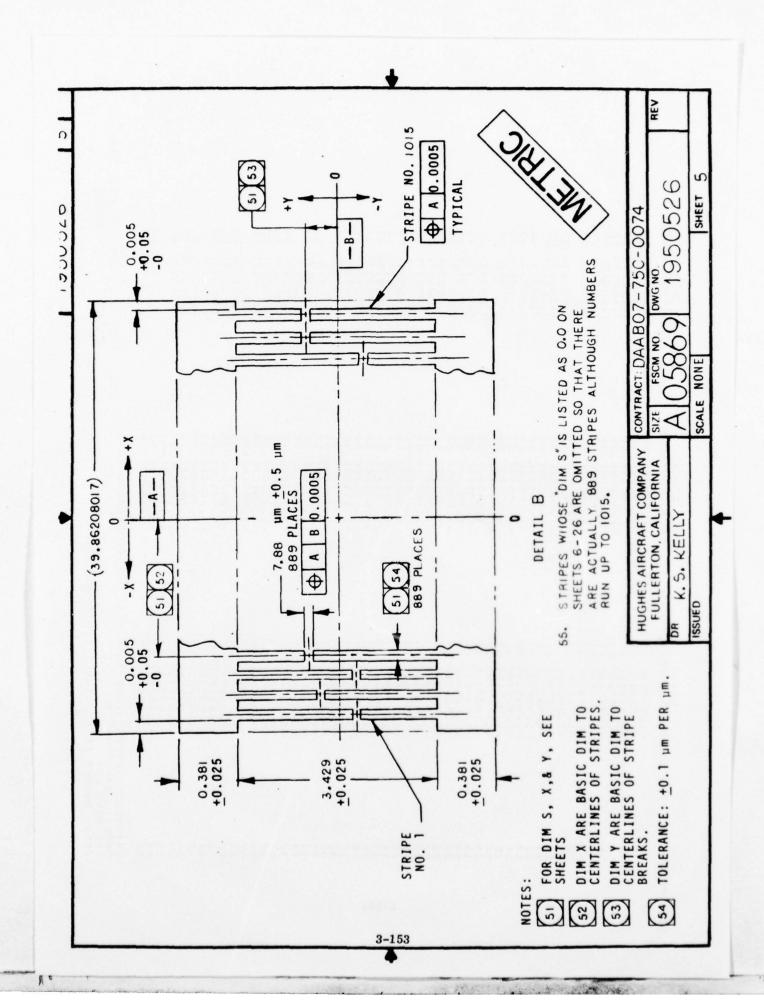
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STAIPE WIDTH	88888888888888888888888888888888888888	IZE FSCM NO. CRAWING NO. A 1950526 CALE: NONE SHEET
DIM Y PRFAK LCCATION		CE PERIODIC XDUCER S 42
STRIPE LOCATION	11111111111111111111111111111111111111	NAME: ECOMMT TDL-196,21 N 23,1978 T1 ER OF ELECTRODE STRIFES:
PF NO.		TRANSDUCER DATE: JA REF DES: P

RE V



		A .
STRIPE LIDTH	7.000 000 000 000 000 000 000 000 000 00	SCM NO. DRAWING NO. 05869 1950526 NONE SHEET
		SIZE F SCALE:
DIM Y ERFAK LCCATION		15
ć		TRIFFS: 1
STRIPE LOCATION		TRODE
F.O.	よるでみたらてらららまるちゃだらてみららまるちゃちゃともらちゃまらでもとうとうとでもとらてもなっている。 2.2.2.2.2.2.2.2.2.2.2.2.2.2.2.2.2.2.2.	E: JAN DES: PT2 AL NUMPER
STRIPE NO	3–154	

STRIPE LIDTH	.88017E 0	86017	ANDIZE O	20000	1000	111000		986175	•	SECTION OF	HH017F 0	A8017E 0	88017E C	0.	.8 E C 17 E 3	.88617C 0	.88017E 0	. 88017E 0		.88017E	.880172 0	0 35.000	0 111	ARDITE D		.88017E 0	.88017E 0	. 88617E 3	.0	.88017E 0	.88017E 0	. 88017E	211000	271700			.88017E 0	.88017E 0	.88017E 0	.880171 0	.88017E 0	7.880176 00	.880176 0		0 2111	SAMOITE O			CF NO. CRAUING N	A 05869 1	ONE
PREAK LCCATION	5 9000F C	C 363098	200000	100000	200000	T.S. JOOGE	. 169 ERE -4	1.59000F 0	-59000E	200000	2 40000	33008	0 700084	.06968E-4	1.59000E 0	. 59000E S.	1.59000E 0	\$ 300065.	1.5900CE G	. 59000E	100065.1	2.06968E-4	1.0900E	L SOUDE D	590006	1.59000E 0	1.59300E G	1.59000E 0	2.06968E-4	1.59000E G	1.59000E	1.59060E	1.59000E	1.00000		4-14-640 C	1.590006	1.59000F C	1.59000E 0	.59000E G	1.59000E C	-1.59000E 00	1.59000E 0	.06968E-4	1.590000	100000	390008		TEANSDUCER		w)
ATICA	C	, (	, (	> 0	0	٠	٥	0	0	,,	2 6		00	0	0	(3	0	0	C	0	0	0	30	2	3 6	0	1)	0	0	0	0	0	0	0	20	, c		0	0	0	0	01	3	C	0	ى د	2 0	•	TDL-100 TAPPED		DE STRIPES: 101
STRIPE LOC	1 79977	2000	10000	70001	1. 19554	1.19347	1.78242	1.77138	1.76980	1. 76863	20001.1	1000101	76197	1.75088	1.73963	1.73825	1.73668	1.73510	1.73353	1.73195	1.73037	1.71933	1.70828	1.00/11	1.70356	1.76198	1.70040	1.69883	1.68778	1.67673	1.67516	1.67358	1.67201	1.6/043	1.65888	1.65623	1.64519	1.64361	1.64204	1.64046	1.63888	-1.63731E	1.63573	1.62469	1.61364	1.61207	1.60001	1,000.1	R NAME: ECOMMI	12	FR OF ELECTRO
.E NO.				יי	10	u.,	26	5.7	a	50		1	7.	34		9	67	49	69	20	73	72	27	***	34	11	7.6	79	80	r a	35	80	48	× .	w.r.	000	υ <b>σ</b>	00	9.1	26	9.6	*6	u)	96	16	x 0	101	301	TRANSDUCE DATE:	FF DES:	CTAL NUM

		A S
STRIPE WIDTH	7	SIZC FSCM NO. DRAWING NO. 4 05869 1950526 SCALE: NONE SHEET
PREAK LCCATION		APPED TRANSDUCER
STRIPE LOCATION	11111111111111111111111111111111111111	CER NAME: ECOMMI TDL-100 T JAN 23,1978 : MT2 UMBER OF ELECTRODE STRIFES:
.04	よろさみちもてれらいよるちゃちもではらりまるさんちもてはりむよろうみちもでんらじまんさんきらてはらむ	TRANSDU DATE: REF DES TCTAL N

		œ
STRIPE WIDTH	7.68 017 E 00 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0	SIZE FSCP NO. DRAWING NO. A 05869 1950526 SCALE: NONE SHEET
DIP Y BREAK LOCATION		TAPPED TRANSDUCER
STRIPE LOCATION	11111111111111111111111111111111111111	ER NAME: ECOMMT TDL-160 JAN 23,1978 MT2 MBER OF ELECTRODE STRIFE
STRIPE NO.	าณทรถพาธ์ขอาณทรมพาธ์ขอาดทรถพาธ์ขอาดทรมพาธ์ขอาดทรมพาธ์ขอ ชั้นชั้นชั้นชั้นชั้นชั้นชั้นชั้น การการการการสี่ อาการการการการการการการการการการการการการ	TRANSDUCT DATE: PFF DES: TCTAL NUI

CIM S STRIPE WIDTH	7.688017E 000 7.886017E 000	SIZE FSCP NO. DRAWING NO. A 05869 1950526 SCALE: NONE SHEET
DIN Y HREAK LCCATION		RIFES: 1015
STRIPE LOCATION		E: JAN 23,1978 DES: MT2 AL NUMBER OF FLECTRODE ST
STRIPE NO.	HUNGENTERSTONES OF THE PROPERTY OF THE PROPERT	PREF

STRIPE MIDTH	7.88 8 8 0 1 7 E 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0	SIZE FSCM NO. CRAWING NO.
DIN Y FREAK LCCATION		ES: 1015
STRIPE LOCATION		AN 23,1978
STRIPE NO.	Note that the contraction of the	DATE:

CIM S STRIPE LIDTH	7.6886017E 000 7.6886017E 000	P NO. CRAWING NO. R 869 1950526 NE SHEET 1
DIM Y BREAK LCCATION		ED TRANSDUCER SIZE FSC A DS A 05
DIM X STRIPE LOCATION	11.1.1.1.1.1.1.1.1.1.1.1.1.1.1.1.1.1.1	AAKE: ECOMMT TEL-166 TAEP 23,1978 2 R OF ELECTRODE STRIPES: 1
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DIM S STRIPE LICTE	7.66 to 17 E	SIZE FSCM NO. DRAWING NO.
DIM Y TION FREAK LCCATION		DL-100 TAPPED TRANSDUCER STRIFES: 1015
DIK X STRIPE LOCAT	$ \begin{array}{c} -4484884 - 349 - 44848 - 4484 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 489 - 48$	TRANSDUCER NAME: ECOMMT T DATE: JAN 22,1978 REF DFS: MT2 TCTAL NUMBER OF ELECTRODE
STRIPE	3-161	

		REV 14
CIM S STRIPE WICTH	77.888800117E 000 000 000 000 000 000 000 000 000 0	SIZE FSCM NO. DRAWING NO. A 05869 1950526 SCALE: NONE SHEET
DIP Y RREAK LCCATION		1015
STRIPE LOCATION	44444448888888888888888888888888888888	AN 93,1978 MAN 93,1978 MAN 93,1978 MAN 93,1978
STRIPE NO.		PATE: DATE: TOTAL NUM

		R L
CIM S STRIPE WIDTH	7.888017E 000	SIZE FSCM NO. DRAWING NO. 05869 1950526 SCALE: NONE SHEET
PREAK LCCATION		TAPFED TRANSDUCERS: 1015
STRIPE LOCATION	11111111111111111111111111111111111111	CER NAME: ECOMMT TDL-156 JAN 23,1978 : MT2 UMBFR OF ELECTRODE STRIFE
PF NO.		TRANSDUC DATE: RFF DES TCTAL MU

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   STRIPE LOCATION
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                                                            RANSDUCER NAME:
ATE: JAN 23,197
EF DES: MT2
CTAL NUMBER CF EL
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		REV 17
STRIPE LIDTH		-88017E 0 -88017E 0 -88017E 0
DIM Y BREAK LOCATION		
DIM X STRIPE LOCATION	$\begin{array}{c} \text{1} \\ \text{1} \\ \text{2} \\ \text{3} \\ \text{4} \\ \text{2} \\ \text{3} \\ \text{4} \\ \text{3} \\ \text{4} \\ \text{5} \\ \text{5} \\ \text{6} \\ \text{6} \\ \text{6} \\ \text{7} \\ \text{6} \\ \text{6} \\ \text{7} \\ \text{6} \\ \text{6} \\ \text{7} \\ \text{6} \\ $	3.47020E 00 3.48596E 00 3.51749E 00 3.51749E 00 3.62794E 00 AN 23.1976 AN 23.1976 AN 23.1976 AN 23.1976
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	SIZE FS
	PPED TRANSDUCER
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$\begin{array}{c} NUMNMMWA4444444444444444444444444444444444$	1978 F ELECTRODE
	ATE: JAN 23 ATE: JAN 23 EF DES: MT2 OTAL NUMBER C
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DIM S STRIPE LIDIT	7.888017E 00 7.888017E 00	SIZE FSCP NO. DRAWING NC. A 05869 1950526 SCALE: NONE SHEET
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STRIPE LOCATION	7. 7. 7. 7. 7. 7. 7. 7. 7. 7. 7. 7. 7. 7	SDUCER NAPE: ECOMMI IDE-15 . JAN 23,1978 DES: PT2 L NUMBER OF ELECTRODE STRIPE
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STRIPE LIDTH	7. *** ********************************	SIZE FSCM NO. DRAWING NO. A 1950526 SCALE: NONE SHEET
DIM Y BREAK LOCATION		13 TAPPED TRANSDUCER ES: 1015
STRIPE LOCATION		UCER NAVE: ECOMMT TDL-10 JAN 23,1978 S: PT2 S: PT2 NUMBER OF ELECTRODE STRIF
STRIPE NO.	3-169	TRANSD DATE: AFF DE TCTAL

		RE 22
DIM S STRIPE LIDIT	7.5880117E 000 7.5880117E 000	SIZE FSCM NO. CRAWING NO. A 05869 1950526 SCALE: NONE SHEET
DIM Y BREAK LOCATION	######################################	1015
STRIPE LOCATION	11.166425 11.166425 11.166425 11.166425 11.166425 11.19436405 11.194365 11.204365 11.204365 11.204365 11.204365 11.204365 11.204365 11.204365 11.204365 11.204365 11.204365 11.204365 11.204365 11.204365 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665 11.304665	AN 23,1978 MT2 BFR OF ELECTRODE STRIPES:
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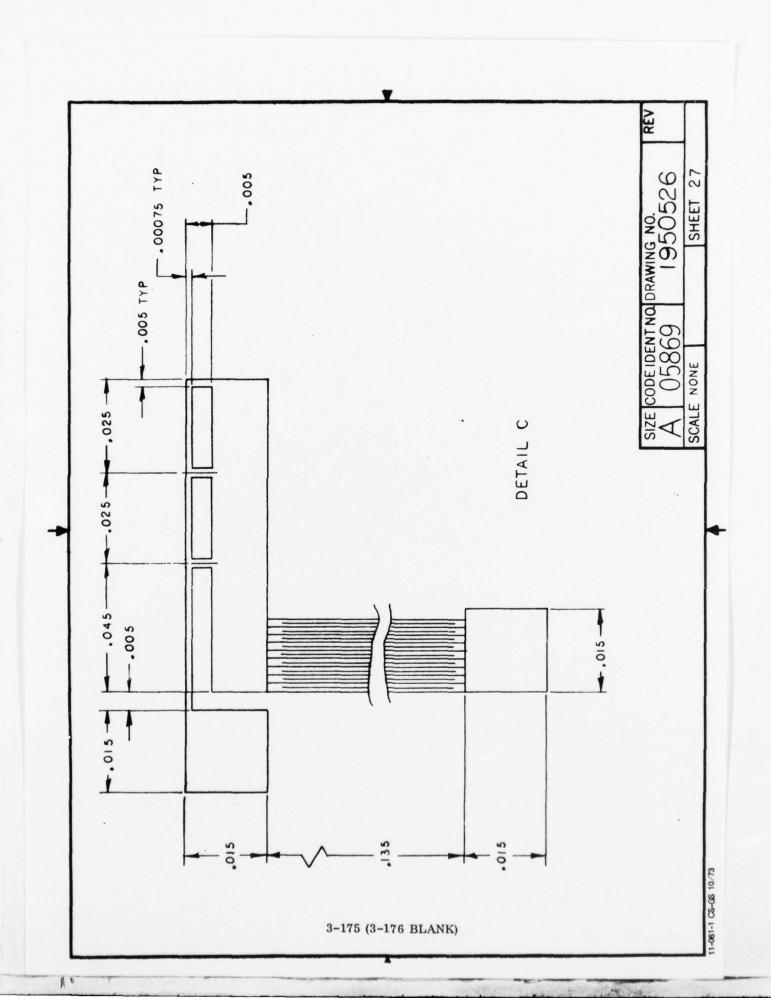
DIM S STRIPE LIDIF	7.68 0117E	SIZE FSCM NO. DRAWING NO. A 05869 1950526 SCALE: NONE SHEET
DIM Y BREAK LCCATION		0 TAPPED TRANSDUCER ES: 1615
STRIPE LOCATION	11. 1. 1. 1. 1. 1. 1. 1. 1. 1. 1. 1. 1.	SEDUCER NAME: ECOMMT TDL-10: JAN 23,1978 DES: MT2 L NUMBER OF ELECTRODE STRIP
STRIPE NO.	$-\alpha n_1 + n_2 + n_3 + n_4 + n$	TRANSDI DATE: RFF DES

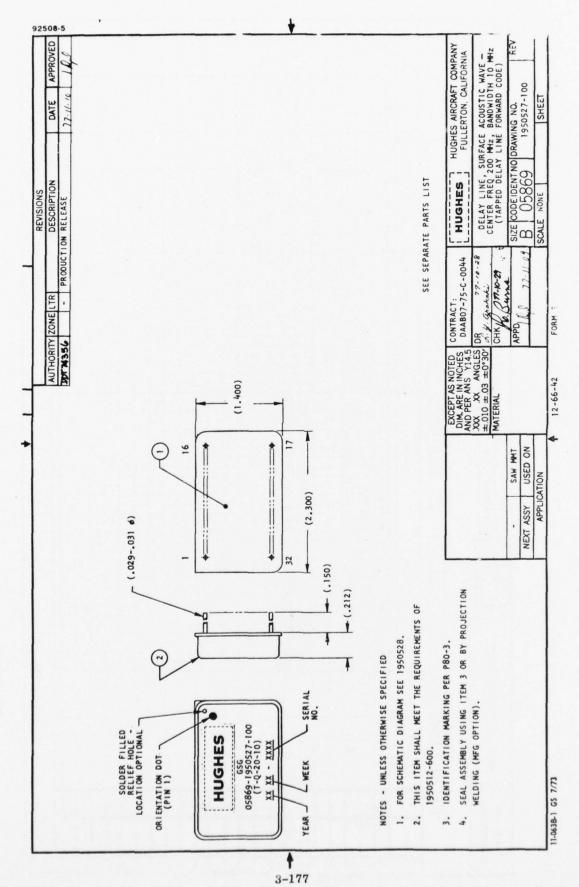
		REV 24
DIM S STRIPE WIDTH	7.888017E 00 7.888017E 00 7.886017E 00	SIZE FSCM NO. DRAWING NO. A 05869 1950526 SCALE: NONE SHEET
DIP Y BREAK LOCATION		TAPPED TRANSDUCERS: 1615
STRIPE LOCATION	11.55.69.90.11 11.55.69.90.11 11.55.69.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.75.90.11 11.55.90.11 11.55.90.11 11.55.90.11 11.55.90.11 11.55.90.11 11.55.	ER NAME: ECOMMI TDL-100 JAN 23,1978 MT2 MER OF ELECTRODE STRIFE
STRIPE NO.	まえちゅうとてはりりまえちゅきらすのまえきよちらすのまられるちゃらまるとうまえでみまらすらり	TRANSDUC DATE: REF DES: TCTAL NU

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STRIPE LIDTH	7.68 8017 E 00	IZE FSCM NO. CRAMING NO. A 05869 1950526 Cale: None Sheet
DIP Y BREAK LOCATION	11 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	TAPPED TRANSDUCER S
STRIPE LOCATION	11	NAME: ECOMMT TDL-100 N 23,1978 T2 FR OF ELECTRODE STRIPE
FE NO.	まっちょう ちゅうりゅう ちゅう ちゅう ちゅう ちゅう ちゅう ちゅう ちゅう ちゅう ちゅう ち	TRANSDUCER DATE: JA REF DES: T

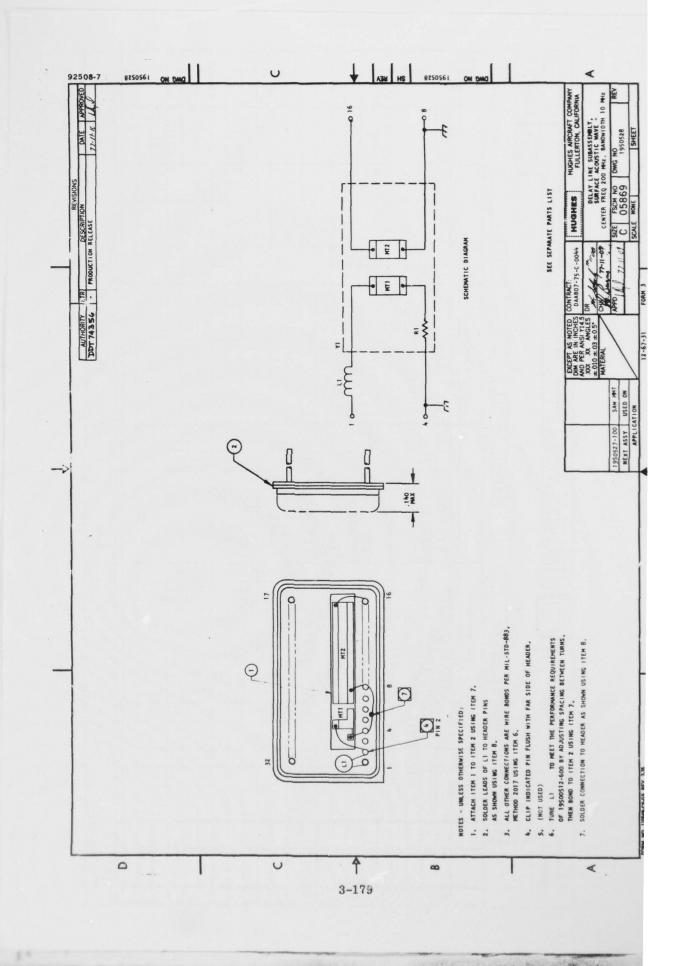
		REV	56
E LIDTH	175 175 175 175 175 175 175 175 175 175	CRAWING NO.	SHEET
STRIPE	77.77.77.77.77.77.77.77.77.77.77.77.77.	FSCH NO.	. NONE
		SIZE	SCALES
BREAK LCCATION	11. 1. 1. 1. 1. 1. 1. 1. 1. 1. 1. 1. 1.	TRANSDUCER	
<b>a</b>		TAPPED	: 1015
1110A		TDL-100 TAPPED	STRIPES
STRIPE LUCATION	1.951221 1.955221 1.955236 1.955366 1.955536 1.955536 1.955936 1.955936 1.95636	23,1978	R OF ELECTRODE STRIPES:
. ON		TRANSDUCER DATE: JAN	OTAL NUMBE

STRIPE





1 770923 \*1 . 4 95869 13.45 AUTH PL 1950527 - 100 HEF DESIGNATION 60-11-22 SPECIFICATION OR REFERENCE 15 REFERENCE NO. GO-8-571 DAABO7-75-C-0044 SCHEMATIC DIAG DESGN PERF SPEC IDENT MARKING COVER SOLDER, SN96 1W5 SAW MMT DESCRIPT ON SUBABBY TAMAINT V PART OR IDENT NUMBER 1950512-600 P80-3 2917220118-175 4277250-996 1950528 HUGHES AIRCRAFT COMPANY FULLERTON, CALIFORNIA 77-09-23 DELAY LINE, SAW CODE IDENT UNIT MOR PADDAL S AR QUANTITY REQUINED Ho. Surna TRANSMITTAL PARTS LIST 0064 1061



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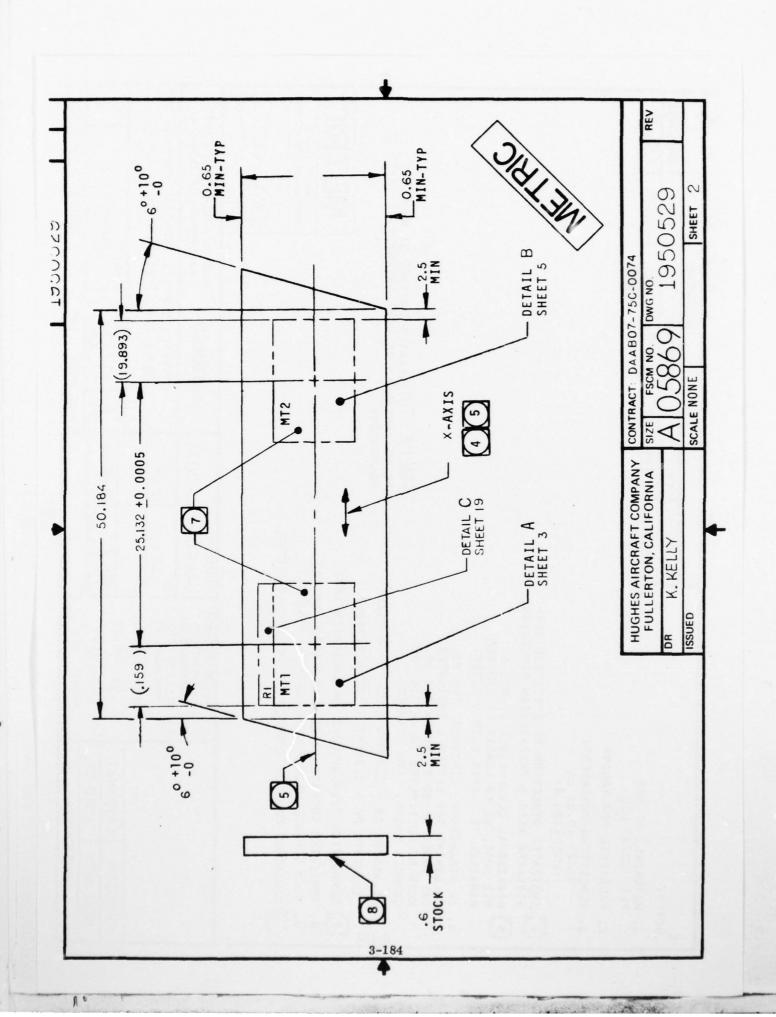
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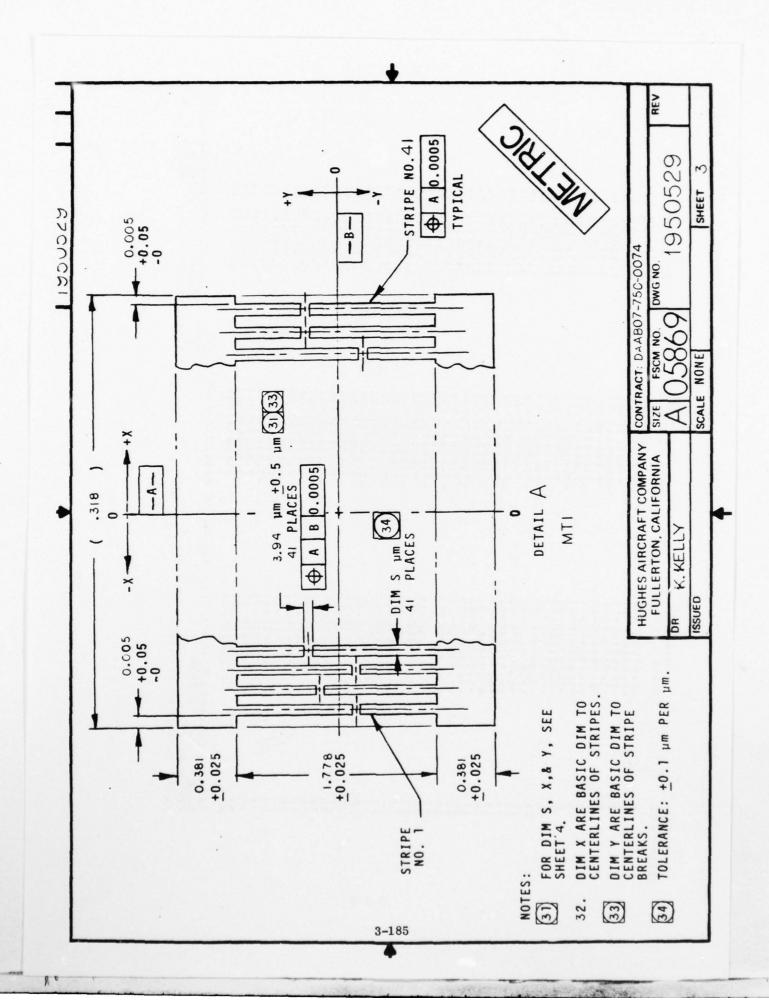
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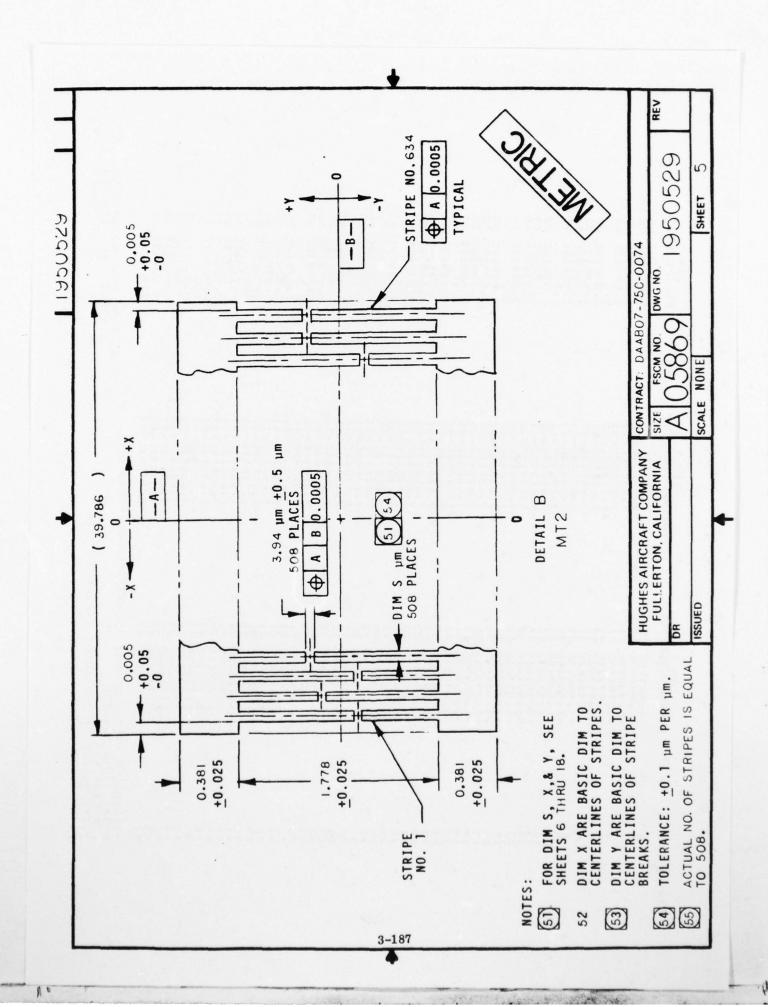
CRYSTAL, SURFACE ACOUSTIC WAVE-TDL 200 APPROVED THIRD ANGLE (AMERICAN) PROJECTION REV METRIC HUGHES AIRCRAFT COMPANY OF 19 - 200 MHz CENTER FREQ., IOMHZ BANDWIDTH FULLERTON, CALIFORNIA TO BE INSTALLED IN NEXT ASSEMBLY AT POINT OF FRAGILE ITEM (EASILY DAMAGED BY HANDLING) 1950529 SHEET 1 78-08-29 DATE REVISIONS PRODUCTION RELEASE DESCRIPTION ž HUGHES SCALE NONE MANUFACTURE. SIZE DAAB07-75C-0074 78-08-29 18.09.06 1 AUTHORITY **DDT86948** DIMENSION TO BE DETERMINED AT TIME OF FABRICATION. K. KELLY CONTRACT INDICATED SURFACE TO BE CORRUGATED PER P82. DEPOSITION FILM APPLIED IN INDICATED AREA. BACK SURFACE TO BE ROUGHENED WITH #180 GRIT. CHK  $1.45870E-02 = 1.45870 \times 10^{-2} = 0.014587$ 1.34567E 00 = 1.34567 x 10<sup>0</sup> = 1.34567 STALLINE AXIS & PROPAGATION DIRECTION. INDICATES DIRECTION OF SPECIFIED CRY-MILLIMETERS & UNLESS OTHERWISE +0.002 **DIMENSIONS ARE** +0.02 +20 PER ANSI Y14.5 +0.5 SPECIFIED HORIZONTAL CENTERLINES OF MT1 & MT2 SHALL BE CO-LINEAR WITHIN AND FOLLOWING THE LETTER E INDICATES -AXIS WITHIN 0.250. THE POWER OF 10 BY WHICH THE NO. MUST BE MULTIPLIED TO OBTAIN THE IN DIMENSIONAL LISTINGS, THE NO. ANGLES ××. XXX. FOR EXAMPLE: Z DEPOSITION THICKNESS: 2. FABRICATE PER 780294 0.125 +0.01 µm USED ON SAWMMT MATERIAL: QUARTZ CORRECT VALUE. PER 760781-100 APPLICATION PARALLEL TO **NEXT ASSY** 1950528 NOTES: 800 ; ë. • (v) . 9

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STRIPE WIDTH		FSCM NO. DRALING NO. 05869 1950529 NONE SHEET
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DIM X STRIPE LOCATION	11111111111111111111111111111111111111	R NAME: ECOMMT TOL-200, 41 An 23,1978 MT1 BFR OF ELECTRODE STRIPES:
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IPE NO. STHIPE LOCA	151 152 -1.04172E 153	55 -1.04014	-1.01095 57 -1.01016	11.00250	79.79.79.79.79.79.79.79.79.79.79.79.79.7	-9.77818	-9.62435	67 -9.47838	-9.46263	76 -9.33879	71 -9.16283	-9.14708	18,99324	-8.84728	77 78 78	-8.82365	-R-67769	- R - 52485	78.515.97	-8-36214 85	86 -8.21618	1800000	85 -8.19255	18.04659	-7.89275	-7.88487	94 -7.81699	94	97 -7-57719	-7.56144	-7-41548	CER	CTAL NUM

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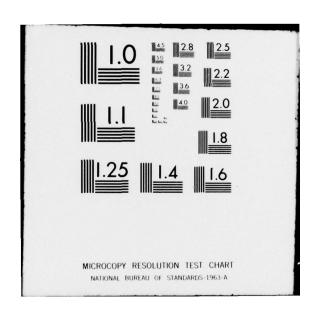
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HUGHES AIRCRAFT CO FULLERTON CALIF GROUND SYSTEMS GROUP F/6 9/5
PHOTOLITHOGRAPHIC TECHNIQUES FOR SURFACE ACOUSTIC WAVE (SAW) DE--ETC(U)
DEC 78 A W DOZIER

PR-79-12-40-VOL-1

DELET-TR-75-0044-F-VOL-1

NL AD-A064 197 UNCLASSIFIED 4 OF 4 AD A064197 END DATE FILMED 4 -79



STRIPE LIDTH	00000000000000000000000000000000000000		SIZE FSCM NO. DRAWING NO. A 05869 1950529 SCALE: NONE SHEET
TION BREAK LOCATION		トレンシー・	CL-2CO, TAPPED TRANSDUCER STRIFES: 634
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STRIPE LOCATION	. 58471E-0	.50595F-0	-42719F-C	. 34843E-0	. 88881E-	• 42919E - 5	936456	100001	74429F-0	273675-0	106961	11614E-6	.03738E-0	-57776E-C	.18144E-0	.93812E-0	.93812E-0	181446-0	.57776E0	11646	100000	27367F-G	73396-6	6.19290E-01	.27167E-0	.35043E-0	-42919E-C	. 88881E-0	34843E-0	50595F-0	58471E-C	10443E 0	.25039F 0	.25827E 0	.26615E 0	.27402E C	.41998E C	. 56595E	. 57382E 3	. 58170E 0	58958E C	.73554E C	. 88150E C	. 88938E	.89725E 0	. 90513E 0	. 05109F	NAPE: ECOMMI TEL-200.	23,197	
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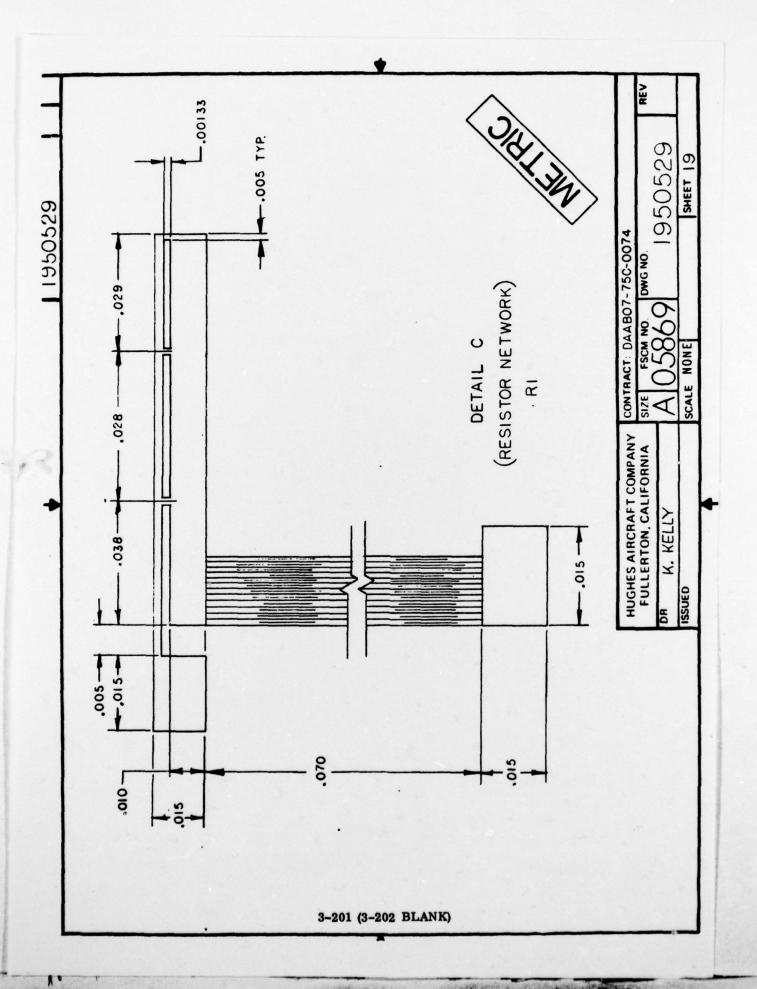
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NO. STRIPE LOCATION	5.35258E 0	404 494 5.37620E 0	5.52217E 0	0 30,976.0E	5.69176F 0	10 E.83772E 0	0.983688	13 5.99943E 0	14 6.00731E 0	15 6.15327E 0	17 6.30711E 0	18 6.31499E 0	15 6.52286E U	21 6.61479E 0	6.62266E 0	24 6.63841F C	2E 6.78438E 0	6.93034E 0	0.93821E 0	25 6.95397E 0	30 7.09993E 0	31 7.24589E 0	7.25377E 0	7.269525 0	35 7.41548E 0	7.56144E 0	7.56932E 0	7.585076	4r 7.73103E 0	7.87699E G	7.854872 0	7.900625	0 3629E 0	46 8.19255E 0	8.20042E C	8.20830E 0	50 8.36214E 0	CER NAVE: ECOMMT T	EF DES: MT2 CTAL NUMPFR OF ELECTRODE
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STRIPE LICTH			S TARRET TO CO	00000000000000000000000000000000000000	FSCP NO. DRABING NO. 05869 1950529 SHEET
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